

RL78/G14

**RENESAS MCU** 

R01DS0053EJ0360 Rev. 3.60 Mar 29, 2024

True low-power platform (66  $\mu$ A/MHz, and 0.60  $\mu$ A for operation with only RTC and LVD) for the general-purpose applications, with 1.6-V to 5.5-V operation, 16- to 512-Kbyte code flash memory, and 44 DMIPS at 32 MHz

### 1. OUTLINE

#### 1.1 Features

#### **Ultra-Low Power Consumption Technology**

- V<sub>DD</sub> = single power supply voltage of 1.6 to 5.5 V which can operate a 1.8 V device at a low voltage
- HALT mode
- STOP mode
- SNOOZE mode

#### **RL78 CPU Core**

- · CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 μs: @ 32 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 μs: @ 32.768 kHz operation with subsystem clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- · Address space: 1 MB
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 2.5 to 48 KB

#### **Code Flash Memory**

- · Code flash memory: 16 to 512 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming with boot swapping and flash shield window

#### **Data Flash Memory**

- Data flash memory: 4 KB and 8 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

#### **High-speed On-chip Oscillator**

- Select from 64 MHz, 48 MHz, 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy:  $\pm 1.0\%$  (V<sub>DD</sub> = 1.8 to 5.5 V, T<sub>A</sub> = -20 to +85°C)

#### **Operating Ambient Temperature**

- T<sub>A</sub> = -40 to +85°C (A: Consumer applications,
   D: Industrial applications)
- T<sub>A</sub> = -40 to +105°C (G: Industrial applications)

#### **Power Management and Reset Function**

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

#### **Data Transfer Controller (DTC)**

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- · Activation sources: Activated by interrupt sources.
- Chain transfer function

#### **Event Link Controller (ELC)**

• Event signals of 19 to 26 types can be linked to the specified peripheral function.

#### **Serial Interfaces**

- Simplified SPI (CSI Note): 3 to 8 channels
- UART/UART (LIN-bus supported): 3 or 4 channels
- I2C/simplified I2C: 4 to 10 channels

#### Timer

- 16-bit timer: 8 to 12 channels (Timer Array Unit (TAU): 4 to 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)
- 12-bit interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years, alarm function, and clock correction function)
- Watchdog timer: 1 channel (operable with the dedicated low-speed on-chip oscillator)

#### A/D Converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)
- · Analog input: 8 to 20 channels
- Internal reference voltage (1.45 V) and temperature sensor

#### D/A Converter

- 8-bit resolution D/A converter (VDD = 1.6 to 5.5 V)
- · Analog output: None or up to two channels
- Output voltage: 0 V to VDD
- Real-time output function

#### Comparator

- None or up to two channels
- Operating modes: Comparator high-speed mode, comparator low-speed mode, window mode
- The external reference voltage or internal reference voltage can be selected as the reference voltage.

# I/O Port

- I/O port: 26 to 92 (N-ch open drain I/O [withstand voltage of 6 V]: 2 to 4, N-ch open drain I/O [VDD withstand voltage/EVDD withstand voltage]: 10 to 28)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3
   V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

#### Others

• On-chip BCD (binary-coded decimal) correction circuit

**Note** Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

Remark The functions mounted depend on the product.

See 1.6 Outline of Functions.



#### O ROM, RAM capacities

Flash ROM	Data flash	Data flash RAM	RL78/G14				
riasii NOW	Data ilasii	IXAIVI	30 pins	32 pins	36 pins	40 pins	
192 KB	8 KB	20 KB	_	_	_	R5F104EH	
128 KB	8 KB	16 KB	R5F104AG	R5F104BG	R5F104CG	R5F104EG	
96 KB	8 KB	12 KB	R5F104AF	R5F104BF	R5F104CF	R5F104EF	
64 KB	4 KB	5.5 KB Note	R5F104AE	R5F104BE	R5F104CE	R5F104EE	
48 KB	4 KB	5.5 KB Note	R5F104AD	R5F104BD	R5F104CD	R5F104ED	
32 KB	4 KB	4 KB	R5F104AC	R5F104BC	R5F104CC	R5F104EC	
16 KB	4 KB	2.5 KB	R5F104AA	R5F104BA	R5F104CA	R5F104EA	

Flash ROM	Data flash	RAM	RL78/G14				
T IdSIT NOW	Data ilasii	IVAIVI	44 pins	48 pins	52 pins	64 pins	
512 KB	8 KB	48 KB Note	_	R5F104GL	_	R5F104LL	
384 KB	8 KB	32 KB	_	R5F104GK	_	R5F104LK	
256 KB	8 KB	24 KB Note	R5F104FJ	R5F104GJ	R5F104JJ	R5F104LJ	
192 KB	8 KB	20 KB	R5F104FH	R5F104GH	R5F104JH	R5F104LH	
128 KB	8 KB	16 KB	R5F104FG	R5F104GG	R5F104JG	R5F104LG	
96 KB	8 KB	12 KB	R5F104FF	R5F104GF	R5F104JF	R5F104LF	
64 KB	4 KB	5.5 KB Note	R5F104FE	R5F104GE	R5F104JE	R5F104LE	
48 KB	4 KB	5.5 KB Note	R5F104FD	R5F104GD	R5F104JD	R5F104LD	
32 KB	4 KB	4 KB	R5F104FC	R5F104GC	R5F104JC	R5F104LC	
16 KB	4 KB	2.5 KB	R5F104FA	R5F104GA	_	_	

Flash ROM Data flash	Data flach	RAM	RL78/G14		
	KAW	80 pins	100 pins		
512 KB	8 KB	48 KB Note	R5F104ML	R5F104PL	
384 KB	8 KB	32 KB	R5F104MK	R5F104PK	
256 KB	8 KB	24 KB Note	R5F104MJ	R5F104PJ	
192 KB	8 KB	20 KB	R5F104MH	R5F104PH	
128 KB	8 KB	16 KB	R5F104MG	R5F104PG	
96 KB	8 KB	12 KB	R5F104MF	R5F104PF	

**Note** The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H R5F104xE (x = A to C, E to G, J, L): Start address FE900H R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

## 1.2 Ordering Information

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Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14

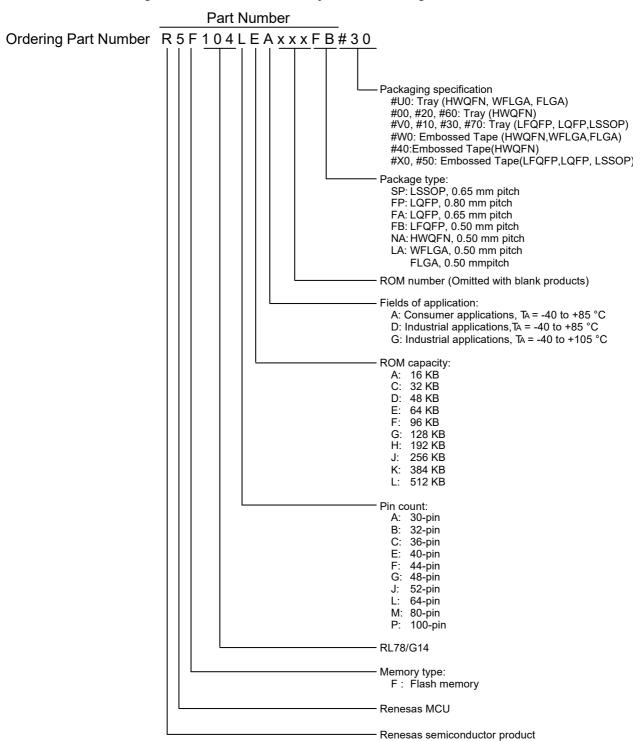


Table 1 - 1 List of Ordering Part Numbers (1/4)

Pin	Package	Fields of	Ordering Part Number		RENESAS Code	
count		Application Note	Part Number	Packaging specification		
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	А	R5F104AAASP, R5F104ACASP, R5F104ADASP, R5F104AEASP, R5F104AFASP, R5F104AGASP	#V0, #10, #30, #X0, #50, #70	PLSP0030JB-B	
		D	R5F104AADSP, R5F104ACDSP, R5F104ADDSP, R5F104AEDSP, R5F104AFDSP, R5F104AGDSP			
		G	R5F104AAGSP, R5F104ACGSP, R5F104AGGSP, R5F104AEGSP, R5F104AFGSP, R5F104AGGSP			
32 pins	32-pin plastic HWQFN	Α	R5F104BAANA, R5F104BCANA, R5F104BDANA,	#U0, #W0	PWQN0032KB-A	
	(5 × 5 mm, 0.5 mm pitch)		R5F104BEANA, R5F104BFANA, R5F104BGANA	#00, #20, #40, #60	PWQN0032KE-A PWQN0032KG-A	
		D	R5F104BADNA, R5F104BCDNA, R5F104BDNA, R5F104BEDNA, R5F104BFDNA, R5F104BGDNA	#U0, #W0	PWQN0032KB-A	
		G			PWQN0032KB-A	
			R5F104BEGNA, R5F104BFGNA, R5F104BGGNA	#00, #20, #40, #60	PWQN0032KE-A PWQN0032KG-A	
	32-pin plastic LQFP (7 × 7, 0.8 mm pitch)	Α	R5F104BAAFP, R5F104BCAFP, R5F104BDAFP,	#V0, #30, #X0	PLQP0032GB-A	
	( <i>t</i> × <i>t</i> , 0.8 mm pical)		R5F104BEAFP, R5F104BGAFP	#10, #50, #70	PLQP0032GB-A PLQP0032GE-A	
		D	R5F104BADFP, R5F104BCDFP, R5F104BBDFP, R5F104BBDFP, R5F104BFDFP, R5F104BGDFP	#V0, #10, #30, #X0, #50, #70	PLQP0032GB-A	
		G	R5F104BAGFP, R5F104BCGFP, R5F104BCGFP,	#V0, #30, #X0	PLQP0032GB-A	
			R5F104BEGFP, R5F104BFGFP, R5F104BGGFP	#10, #50, #70	PLQP0032GB-A PLQP0032GE-A	
	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Α	R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA	#U0, #W0	PWLG0036KA-A	
		G	R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA			
40 pins		• •	Α	R5F104EAANA, R5F104ECANA, R5F104EDANA,	#U0, #W0	PWQN0040KC-A
	(6 × 6 mm, 0.5 mm pitch)		R5F104EEANA, R5F104EFANA, R5F104EGANA, R5F104EHANA	#00, #20, #40, #60	PWQN0040KD-A PWQN0040KE-A	
		D	R5F104EADNA, R5F104ECDNA, R5F104EDDNA, R5F104EEDNA, R5F104EFDNA, R5F104EGDNA, R5F104EHDNA	#U0, #W0	PWQN0040KC-A	
		G	R5F104EAGNA, R5F104EDGNA, R5F10	#U0, #W0	PWQN0040KC-A	
			R5F104EEGNA, R5F104EFGNA, R5F104EGGNA, R5F104EHGNA	#00, #20, #40, #60	PWQN0040KD-A PWQN0040KE-A	
44 pins	44-pin plastic LQFP	Α	R5F104FAAFP, R5F104FCAFP, R5F104FDAFP,	#V0, #X0	PLQP0044GC-A	
	(10 × 10, 0.8 mm pitch)		R5F104FEAFP, R5F104FFAFP, R5F104FGAFP, R5F104FHAFP, R5F104FJAFP	#10, #50, #70	PLQP0044GC-A PLQP0044GC-D PLQP0044GE-A	
				#30	PLQP0044GC-A PLQP0044GC-D	
		D	R5F104FADFP, R5F104FCDFP, R5F104FDDFP,	#V0, #X0	PLQP0044GC-A	
			R5F104FEDFP, R5F104FFDFP, R5F104FGDFP, R5F104FHDFP, R5F104FJDFP	#10, #30, #50, #70	PLQP0044GC-A PLQP0044GC-D	
		G	R5F104FAGFP, R5F104FCGFP, R5F104FGGFP,	#V0, #X0	PLQP0044GC-A	
			R5F104FEGFP, R5F104FFGFP, R5F104FGGFP, R5F104FHGFP, R5F104FJGFP	#10, #50, #70	PLQP0044GC-A PLQP0044GC-D PLQP0044GE-A	
				#30	PLQP0044GC-A PLQP0044GC-D	

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



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Table 1 - 1 List of Ordering Part Numbers (2/4)

	Pin	Package	Fields of	Ordering Part Number		RENESAS Code	
	count		Application Note	Part Number	Packaging specification	-	
<r></r>	48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	A	R5F104GKAFB, R5F104GLAFB	#10, #50, #70	PLQP0048KB-B PLQP0048KL-A	
					#30	PLQP0048KB-B	
				R5F104GAAFB, R5F104GCAFB, R5F104GDAFB,	#V0, #X0	PLQP0048KF-A	
<r></r>				R5F104GEAFB, R5F104GFAFB, R5F104GGAFB, R5F104GHAFB, R5F104GJAFB	#10, #50, #70	PLQP0048KB-B PLQP0048KL-A	
					#30	PLQP0048KB-B	
			D	R5F104GADFB, R5F104GCDFB, R5F104GDDFB,	#V0, #X0	PLQP0048KF-A	
<r></r>				R5F104GEDFB, R5F104GFDFB, R5F104GGDFB, R5F104GHDFB, R5F104GJDFB	#10, #30, #50, #70	PLQP0048KB-B	
<r></r>			G	R5F104GKGFB, R5F104GLGFB	#10, #50, #70	PLQP0048KB-B PLQP0048KL-A	
					#30	PLQP0048KB-B	
_				R5F104GAGFB, R5F104GCGFB, R5F104GDGFB,	#V0, #X0	PLQP0048KF-A	
<r></r>				R5F104GEGFB, R5F104GFGFB, R5F104GGGFB, R5F104GHGFB, R5F104GJGFB	#10, #50, #70	PLQP0048KB-B PLQP0048KL-A	
					#30	PLQP0048KB-B	
		48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	Α	R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA,	#U0, #W0	PWQN0048KB-A	
<r></r>	<b>?&gt;</b>	(/ ^ / mm, o.s mm piteri)	R5	R5F104GHANA, R5F104GJANA, R5F104GKANA, R5F104GLANA	#00, #20, #40, #60	PWQN0048KE-A PWQN0048KG-A	
				D	R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA, R5F104GHDNA, R5F104GJDNA	#U0, #W0	PWQN0048KB-A
			G	R5F104GAGNA, R5F104GCGNA, R5F104GDGNA,	#U0, #W0	PWQN0048KB-A	
<r></r>				R5F104GEGNA, R5F104GFGNA, R5F104GGGNA, R5F104GHGNA, R5F104GHGNA, R5F104GLGNA, R5F104GLGNA	#00, #20, #40, #60	PWQN0048KE-A PWQN0048KG-A	
	52 pins	52-pin plastic LQFP	Α	R5F104JCAFA, R5F104JDAFA, R5F104JEAFA,	#V0, #X0	PLQP0052JA-A	
<r></r>		(10 × 10 mm, 0.65 mm pitch)		R5F104JFAFA, R5F104JGAFA, R5F104JHAFA, R5F104JJAFA	#10, #30, #50, #70	PLQP0052JA-A PLQP0052JD-B	
<r></r>			D	R5F104JCDFA, R5F104JDDFA, R5F104JEDFA, R5F104JFDFA, R5F104JGDFA, R5F104JHDFA, R5F104JJDFA	#V0, #10, #30, #X0, #50, #70	PLQP0052JA-A	
			G	R5F104JCGFA, R5F104JDGFA, R5F104JEGFA,	#V0, #X0	PLQP0052JA-A	
<r></r>				R5F104JFGFA, R5F104JGGFA, R5F104JHGFA, R5F104JJGFA	#10, #30, #50, #70	PLQP0052JA-A PLQP0052JD-B	
<r></r>	64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)	A	R5F104LKAFA, R5F104LLAFA	#10, #30, #50, #70	PLQP0064JA-A PLQP0064JB-A	
				R5F104LCAFA, R5F104LDAFA, R5F104LEAFA,	#V0, #X0	PLQP0064JA-A	
<r></r>				R5F104LFAFA, R5F104LGAFA, R5F104LHAFA, R5F104LJAFA	#10, #30, #50, #70	PLQP0064JA-A PLQP0064JB-A	
<r></r>			D	R5F104LCDFA, R5F104LDDFA, R5F104LEDFA, R5F104LFDFA, R5F104LFDFA, R5F104LJDFA	#V0, #10, #30, #X0, #50, #70	PLQP0064JA-A	
<r></r>			G	R5F104LKGFA, R5F104LLGFA	#10, #30, #50, #70	PLQP0064JA-A PLQP0064JB-A	
			1	R5F104LCGFA, R5F104LDGFA, R5F104LEGFA,	#V0, #X0	PLQP0064JA-A	
<r></r>				R5F104LFGFA, R5F104LGGFA, R5F104LHGFA, R5F104LJGFA	#10, #30, #50, #70	PLQP0064JA-A PLQP0064JB-A	

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

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Table 1 - 1 List of Ordering Part Numbers (3/4)

		1	Fields of	Ordering Part Number		
	Pin count	Package	Fields of Application Note	Part Number	Packaging specification	RENESAS Code
<r></r>	64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	A	R5F104LKAFB, R5F104LLAFB	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
					#30	PLQP0064KB-C
				R5F104LCAFB, R5F104LDAFB, R5F104LEAFB,	#V0, #X0	PLQP0064KF-A
<r></r>				R5F104LFAFB, R5F104LGAFB, R5F104LHAFB, R5F104LJAFB	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
					#30	PLQP0064KB-C
			D	R5F104LCDFB, R5F104LDDFB, R5F104LEDFB,	#V0, #X0	PLQP0064KF-A
<r></r>				R5F104LFDFB, R5F104LGDFB, R5F104LHDFB, R5F104LJDFB	#10, #30, #50, #70	PLQP0064KB-C
<r></r>			G	R5F104LKGFB, R5F104LLGFB	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
					#30	PLQP0064KB-C
				R5F104LCGFB, R5F104LDGFB, R5F104LEGFB,	#V0, #X0	PLQP0064KF-A
<r></r>				R5F104LFGFB, R5F104LGGFB, R5F104LHGFB, R5F104LJGFB	#10, #50, #70	PLQP0064KB-C PLQP0064KL-A
					#30	PLQP0064KB-C
		64-pin plastic FLGA (5 × 5 mm, 0.5 mm pitch)	A	R5F104LCALA, R5F104LDALA, R5F104LEALA, R5F104LFALA, R5F104LGALA, R5F104LHALA, R5F104LJALA, R5F104LKALA, R5F104LLALA	#U0, #W0	PWLG0064KA-A
			G	R5F104LCGLA, R5F104LDGLA, R5F104LEGLA, R5F104LFGLA, R5F104LGGLA, R5F104LHGLA, R5F104LJGLA, R5F104LKGLA, R5F104LLGLA		
<r></r>		64-pin plastic LQFP (14 × 14 mm, 0.8 mm pitch)	A	R5F104LCAFP, R5F104LDAFP, R5F104LEAFP, R5F104LFAFP, R5F104LGAFP, R5F104LHAFP, R5F104LJAFP	#V0, #10, #30, #X0, #50, #70	PLQP0064GA-A
			D	R5F104LCDFP, R5F104LDDFP, R5F104LEDFP, R5F104LFDFP, R5F104LFDFP, R5F104LJDFP, R5F104LJDFP		
			G	R5F104LCGFP, R5F104LDGFP, R5F104LEGFP, R5F104LFGFP, R5F104LGGFP, R5F104LJGFP, R5F104LJGFP	-	
<r></r>	80 pins	80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)	A	R5F104MKAFB, R5F104MLAFB	#10, #50, #70	PLQP0080KB-B PLQP0080KJ-A
					#30	PLQP0080KB-B
				R5F104MFAFB, R5F104MGAFB, R5F104MHAFB,	#V0, #X0	PLQP0080KE-A
<r></r>				R5F104MJAFB	#10, #50, #70	PLQP0080KB-B PLQP0080KJ-A
					#30	PLQP0080KB-B
			D	R5F104MFDFB, R5F104MGDFB, R5F104MHDFB,	#V0, #X0	PLQP0080KE-A
<r></r>				R5F104MJDFB	#10, #30, #50, #70	PLQP0080KB-B
<r></r>			G	R5F104MKGFB, R5F104MLGFB	#10, #50, #70	PLQP0080KB-B PLQP0080KJ-A
					#30	PLQP0080KB-B
_				R5F104MFGFB, R5F104MGGFB, R5F104MHGFB,	#V0, #X0	PLQP0080KE-A
<r></r>				R5F104MJGFB	#10, #50, #70	PLQP0080KB-B PLQP0080KJ-A
					#30	PLQP0080KB-B

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

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Table 1 - 1 List of Ordering Part Numbers (4/4)

Б.		Fields of	Ordering Part Number			
Pin count	Package	Application Note	Part Number	Packaging specification	RENESAS Code	
80 pins	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	А	R5F104MKAFA, R5F104MLAFA	#10, #30, #50, #70	PLQP0080JB-E	
			R5F104MFAFA, R5F104MGAFA, R5F104MHAFA, R5F104MJAFA	#V0, #10, #30, #X0, #50, #70	PLQP0080JB-E	
		D	R5F104MFDFA, R5F104MGDFA, R5F104MHDFA, R5F104MJDFA	#V0, #10, #30, #X0, #50, #70	PLQP0080JB-E	
		G	R5F104MKGFA, R5F104MLGFA	#10, #30, #50, #70	PLQP0080JB-E	
			R5F104MFGFA, R5F104MGGFA, R5F104MHGFA, R5F104MJGFA	#V0, #10, #30, #X0, #50, #70	PLQP0080JB-E	
100 pins	100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)	A	R5F104PKAFB, R5F104PLAFB	#10, #50, #70	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
			R5F104PFAFB, R5F104PGAFB, R5F104PHAFB,	#V0, #X0	PLQP0100KE-A	
			R5F104PJAFB #10, #		PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
		D	R5F104PFDFB, R5F104PGDFB, R5F104PHDFB,	#V0, #X0	PLQP0100KE-A	
			R5F104PJDFB	#10, #30, #50, #70	PLQP0100KB-B	
		G	R5F104PKGFB, R5F104PLGFB	#10, #50, #70	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
			R5F104PFGFB, R5F104PGGFB, R5F104PHGFB,	#V0, #X0	PLQP0100KE-A	
			R5F104PJGFB	#10, #50, #70	PLQP0100KB-B PLQP0100KP-A	
				#30	PLQP0100KB-B	
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	А	R5F104PKAFA, R5F104PLAFA	#10, #30, #50, #70	PLQP0100JC-A	
			R5F104PFAFA, R5F104PGAFA, R5F104PHAFA, R5F104PJAFA	#V0, #10, #30, #X0, #50, #70	PLQP0100JC-A	
		D	R5F104PFDFA, R5F104PGDFA, R5F104PHDFA, R5F104PJDFA	#V0, #10, #30, #X0, #50, #70	PLQP0100JC-A	
		G	R5F104PKGFA, R5F104PLGFA	#10, #30, #50, #70	PLQP0100JC-A	
			R5F104PFGFA, R5F104PGGFA, R5F104PHGFA, R5F104PJGFA	#V0, #10, #30, #X0, #50, #70	PLQP0100JC-A	

Note For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

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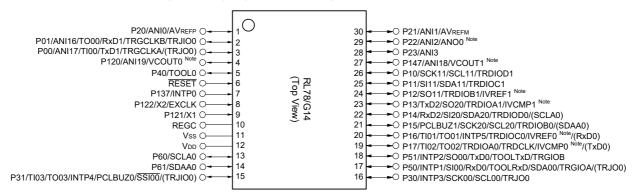
<R>

<R>

# 1.3 Pin Configuration (Top View)

# 1.3.1 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

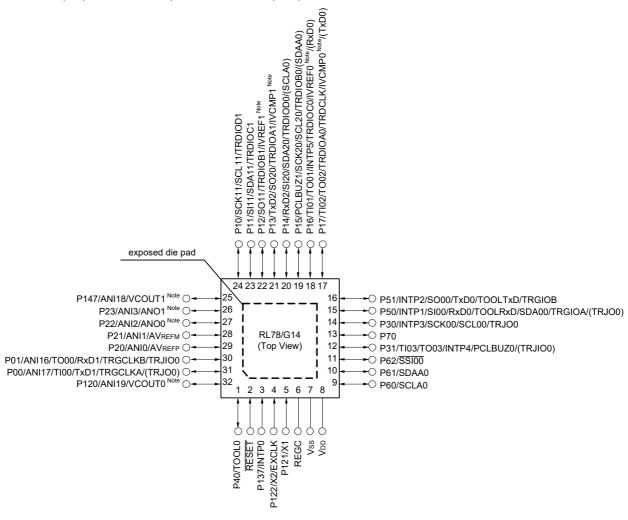
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

# **1.3.2 32-pin products**

• 32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)

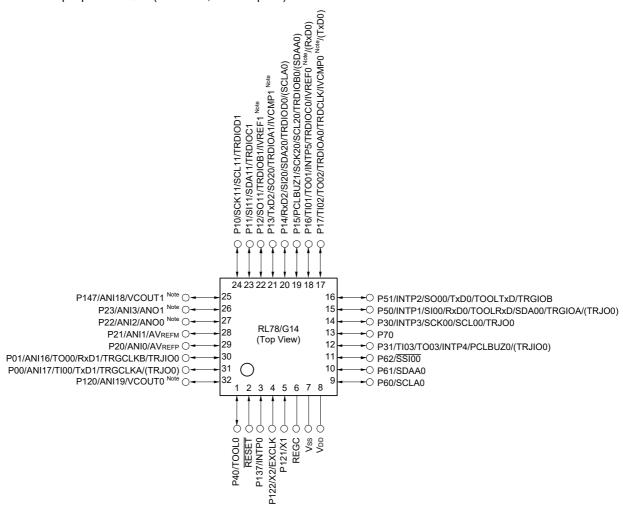


**Note** Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).
- Remark 3. It is recommended to connect an exposed die pad to Vss.

• 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



**Note** Mounted on the 96 KB or more code flash memory products.

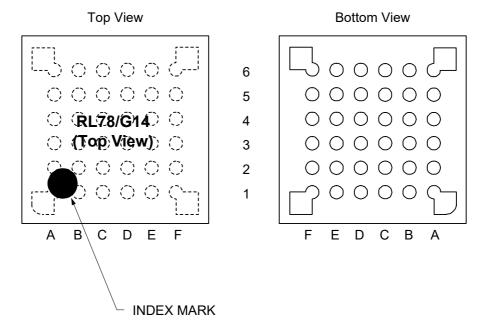
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

# **1.3.3 36-pin products**

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	Α	В	С	D	E	F	
6	P60/SCLA0	VDD	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62/SSI00	P61/SDAA0	Vss	REGC	RESET	P120/ANI19/ VCOUT0 Note	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/TRDIOD0/ (SCLA0)	P31/TI03/TO03/ INTP4/PCLBUZ0/ (TRJIO0)	P00/TI00/TxD1/ TRGCLKA/ (TRJO0)	P01/TO00/ RxD1/TRGCLKB/ TRJIO0	4
3	P50/INTP1/ SI00/RxD0/ TOOLRxD/ SDA00/TRGIOA/ (TRJO0)	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ TRDIOB0/ (SDAA0)	P22/ANI2/ ANO0 Note	P20/ANI0/ AVREFP	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK00/SCL00/ TRJO0	P16/TI01/TO01/ INTP5/TRDIOC0/ IVREF0 Note/ (RXD0)	P12/SO11/ TRDIOB1/ IVREF1 Note	P11/SI11/ SDA11/ TRDIOC1	P24/ANI4	P23/ANI3/ ANO1 <sup>Note</sup>	2
1	P51/INTP2/ SO00/TxD0/ TOOLTxD/ TRGIOB	P17/TI02/TO02/ TRDIOA0/ TRDCLK/ IVCMP0 Note/ (TxD0)	P13/TxD2/ SO20/TRDIOA1/ IVCMP1 Note	P10/SCK11/ SCL11/ TRDIOD1	P147/ANI18/ VCOUT1 Note	P25/ANI5	1
	Α	В	С	D	E	F	

**Note** Mounted on the 96 KB or more code flash memory products.

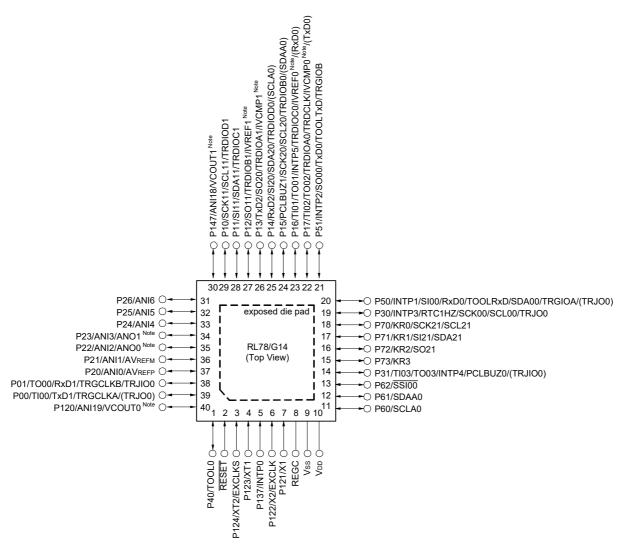
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

## 1.3.4 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

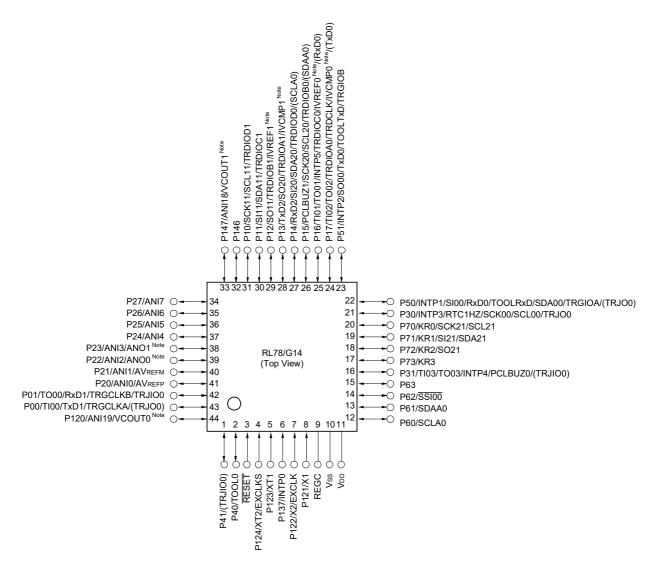
Remark 1. For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

Remark 3. It is recommended to connect an exposed die pad to Vss.

## 1.3.5 44-pin products

• 44-pin plastic LQFP (10 × 10 mm, 0.8 mm pitch)



Note Mounted on the 96 KB or more code flash memory products.

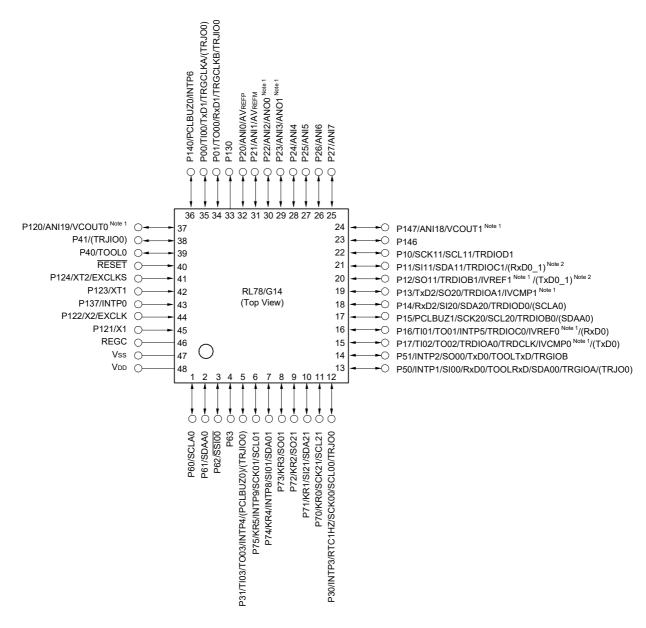
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

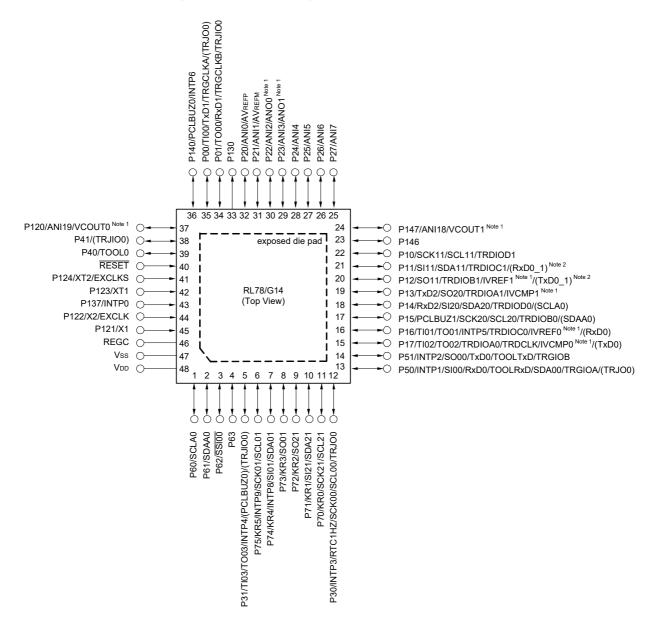
## **1.3.6 48-pin products**

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



- **Note 1.** Mounted on the 96 KB or more code flash memory products.
- Note 2. Mounted on the 384 KB or more code flash memory products.
- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

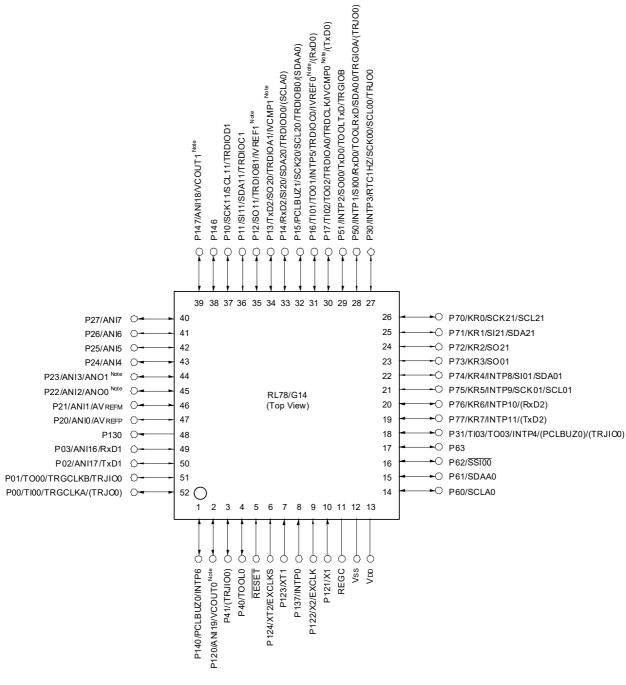
• 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



- Note 1. Mounted on the 96 KB or more code flash memory products.
- **Note 2.** Mounted on the 384 KB or more code flash memory products.
- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).
- Remark 3. It is recommended to connect an exposed die pad to Vss.

# 1.3.7 **52-pin products**

• 52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)



**Note** Mounted on the 96 KB or more code flash memory products.

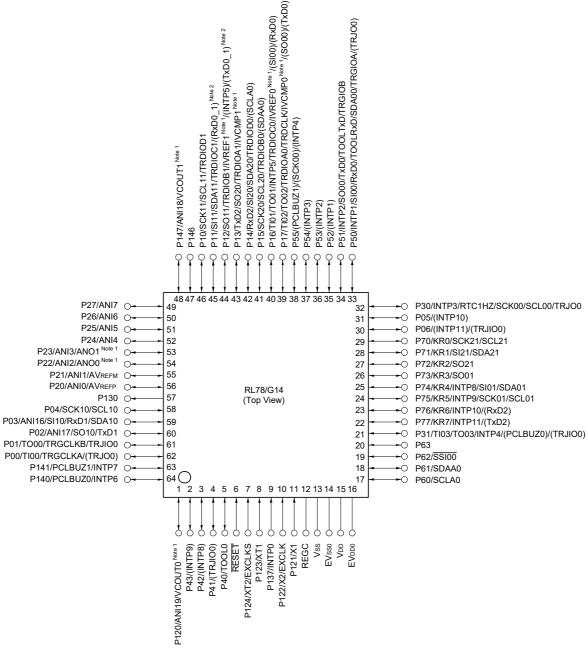
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

**Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

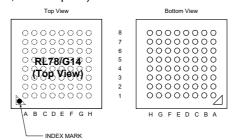
## 1.3.8 64-pin products

- 64-pin plastic LQFP (14 × 14 mm, 0.8 mm pitch)
- 64-pin plastic LQFP (12 × 12 mm, 0.65 mm pitch)
- 64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)



- Note 1. Mounted on the 96 KB or more code flash memory products.
- Note 2. Mounted on the 384 KB or more code flash memory products.
- Caution 1. Make EVsso pin the same potential as Vss pin.
- Caution 2. Make VDD pin the same potential as EVDD0 pin, or the potential that is higher than the EVDD0 pin.
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

• 64-pin plastic FLGA (5 × 5 mm, 0.5 mm pitch)

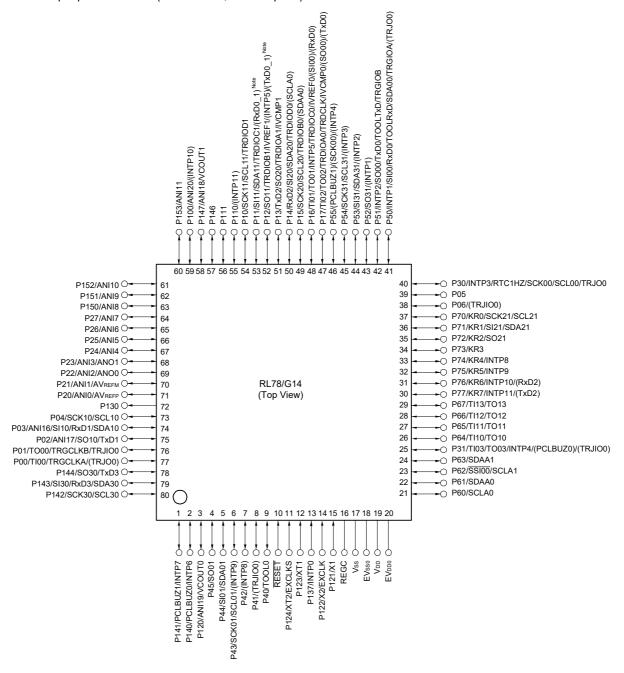


	Α	В	С	D	E	F	G	Н
8	EV <sub>DD0</sub>	EVsso	P121/X1	P122/X2/ EXCLK	P137/INTP0	P123/XT1	P124/XT2/ EXCLKS	P120/ANI19/ VCOUT0 Note 1
7	P60/SCLA0	VDD	Vss	REGC	RESET	P01/TO00/ TRGCLKB/ TRJIO0	P00/TI00/ TRGCLKA/ (TRJO0)	P140/ PCLBUZ0/ INTP6
6	P61/SDAA0	P62/SSI00	P63	P40/TOOL0	P41/(TRJIO0)	P43/(INTP9)	P02/ANI17/ SO10/TxD1	P141/ PCLBUZ1/ INTP7
5	P77/KR7/ INTP11/(TxD2)	P31/TI03/ T003/INTP4/ (PCLBUZ0)/ (TRJI00)	P53/(INTP2)	P42/(INTP8)	P03/ANI16/ SI10/RxD1/ SDA10	P04/SCK10/ SCL10	P130	P20/ANI0/ AVREFP
4	P75/KR5/ INTP9/ SCK01/ SCL01	P76/KR6/ INTP10/ (RxD2)	P52/(INTP1)	P54/(INTP3)	P16/TI01/ TO01/INTP5/ TRDIOC0/ IVREF0 Note 1/ (SI00)/(RxD0)	P21/ANI1/ AVREFM	P22/ANI2/ ANO0 Note 1	P23/ANI3/ ANO1 Note 1
3	P70/KR0/ SCK21/ SCL21	P73/KR3/ S001	P74/KR4/ INTP8/SI01/ SDA01	P17/TI02/TO02/ TRDIOA0/ TRDCLK/ IVCMP0 Note 1/ (SO00)/(TxD0)	P15/SCK20/ SCL20/ TRDIOB0/ (SDAA0)	P12/SO11/ TRDIOB1/ IVREF1 Note 1/ (INTP5)/ (TxD0_1) Note 2	P24/ANI4	P26/ANI6
2	P30/INTP3/ RTC1HZ/ SCK00/ SCL00/TRJO0	P72/KR2/ SO21	P71/KR1/ SI21/SDA21	P06/(INTP11)/ (TRJIO0)	P14/RxD2/ SI20/SDA20/ TRDIOD0/ (SCLA0)	P11/SI11/ SDA11/ TRDIOC1/ (RxD0_1) Note 2	P25/ANI5	P27/ANI7
1	P05/(INTP10)	P50/INTP1/ SI00/RxD0/ TOOLRxD/ SDA00/ TRGIOA/ (TRJO0)	P51/INTP2/ SO00/TxD0/ TOOLTxD/ TRGIOB	P55/ (PCLBUZ1)/ (SCK00)/ (INTP4)	P13/TxD2/ SO20/ TRDIOA1/ IVCMP1 Note 1	P10/SCK11/ SCL11/ TRDIOD1	P146	P147/ANI18/ VCOUT1 Note 1
	A	В	С	D	E	F	G	Н

- Note 1. Mounted on the 96 KB or more code flash memory products.
- **Note 2.** Mounted on the 384 KB or more code flash memory products.
- Caution 1. Make EVsso pin the same potential as Vss pin.
- Caution 2. Make VDD pin the same potential as EVDD0 pin, or the potential that is higher than the EVDD0 pin.
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu F$ ).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

## 1.3.9 80-pin products

- 80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)
- 80-pin plastic LFQFP (12 × 12 mm, 0.5 mm pitch)

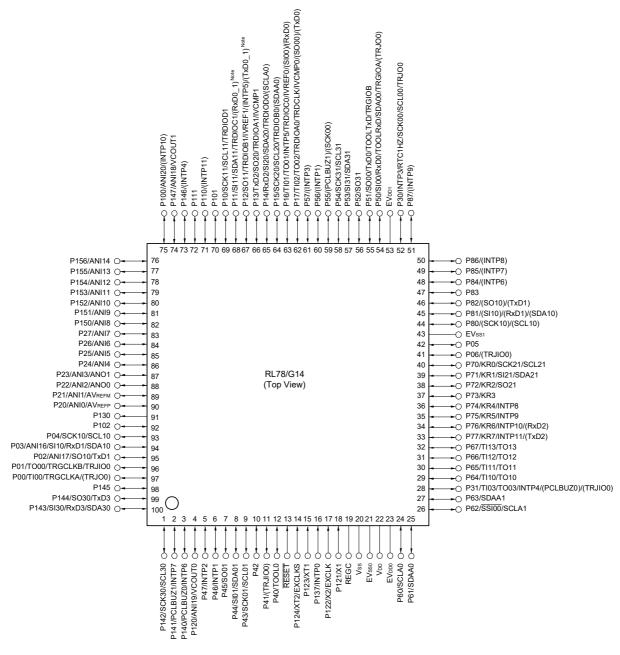


Note Mounted on the 384 KB or more code flash memory products.

- Caution 1. Make EVsso pin the same potential as Vss pin.
- Caution 2. Make VDD pin the same potential as EVDD0 pin, or the potential that is higher than the EVDD0 pin.
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD and EVDD0 pins and connect the Vss and EVss0 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

# 1.3.10 100-pin products

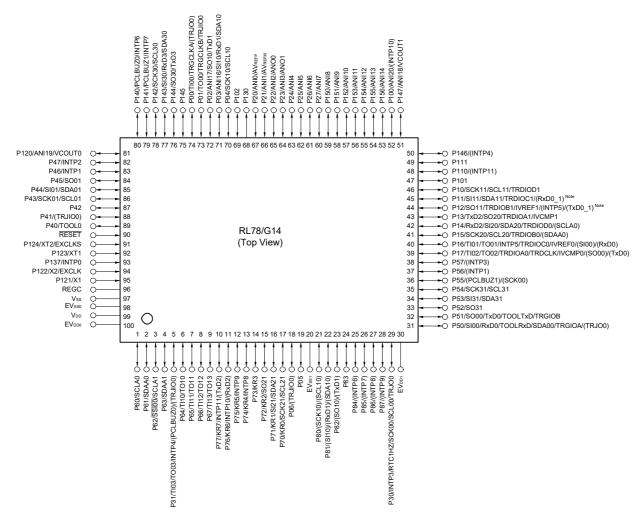
• 100-pin plastic LFQFP (14 × 14 mm, 0.5 mm pitch)



Note Mounted on the 384 KB or more code flash memory products.

- Caution 1. Make EVsso, EVss1 pins the same potential as Vss pin.
- Caution 2. Make VDD pin the same potential as EVDD0, EVDD1 pins, or the potential that is higher than the EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu\text{F}).$
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- Remark 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

• 100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)



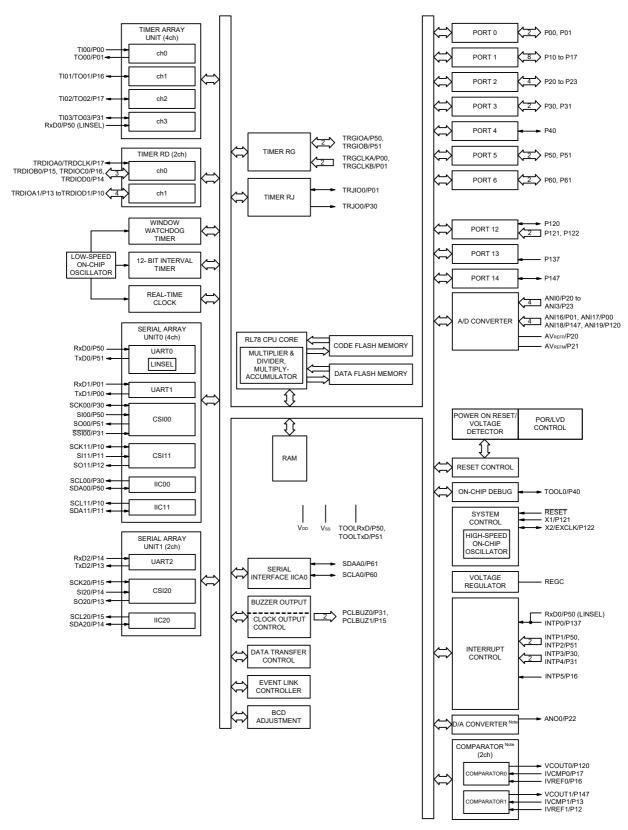
- Note Mounted on the 384 KB or more code flash memory products.
- Caution 1. Make EVsso, EVss1 pins the same potential as Vss pin.
- Caution 2. Make VDD pin the same potential as EVDD0, EVDD1 pins, or the potential that is higher than the EVDD0, EVDD1 pins (EVDD0 = EVDD1).
- Caution 3. Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu F$ ).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVss0 and EVss1 pins to separate ground lines.
- **Remark 3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

#### 1.4 Pin Identification

ANI0 to ANI14, RxD0 to RxD3: Receive data ANI16 to ANI20: Analog output SCK00, SCK01, SCK10, ANO0, ANO1: SCK11, SCK20, SCK21, Analog output AVREFM: A/D converter reference SCK30, SCK31, voltage minus SCLA0, SCLA1: Serial clock input/output A/D converter reference SCL00, SCL01, SCL10, SCL11, AVREFP: voltage plus SCL20, SCL21, SCL30, EVDD0, EVDD1: Power supply for port SCL31: Serial clock output EVsso, EVss1: Ground for port SDAA0, SDAA1, SDA00, EXCLK: External clock input SDA01, SDA10, SDA11, (main system clock) SDA20, SDA21, SDA30, EXCLKS: External clock input SDA31: Serial data input/output (subsystem clock) SI00, SI01, SI10, SI11, INTP0 to INTP11: External interrupt input SI20, SI21, SI30, SI31: Serial data input IVCMP0, IVCMP1: Comparator input SO00, SO01, SO10, IVREF0, IVREF1: Comparator reference input SO11, SO20, SO21, KR0 to KR7: SO30, SO31: Key return Serial data output P00 to P06: Port 0 SSI00: Serial interface chip select input P10 to P17: Port 1 TI00 to TI03, P20 to P27: Port 2 TI10 to TI13: Timer input P30, P31: Port 3 TO00 to TO03. P40 to P47: Port 4 TO10 to TO13, TRJO0: Timer output P50 to P57: Port 5 TOOL0: Data input/output for tool P60 to P67: Port 6 TOOLRxD, TOOLTxD: Data input/output for external device P70 to P77: Port 7 TRDCLK, TRGCLKA, P80 to P87: Port 8 TRGCLKB: Timer external input clock P100 to P102: Port 10 TRDIOA0, TRDIOB0, P110, P111: Port 11 TRDIOCO, TRDIODO, P120 to P124: Port 12 TRDIOA1, TRDIOB1, P130, P137: Port 13 TRDIOC1, TRDIOD1, P140 to P147: Port 14 TRGIOA, TRGIOB, TRJIO0: Timer input/output P150 to P156: Port 15 TxD0 to TxD3: Transmit data PCLBUZ0, PCLBUZ1: Programmable clock VCOUT0, VCOUT1: Comparator output output/buzzer output VDD. Power supply REGC: Vss: Ground Regulator capacitance RESET: X1, X2: Crystal oscillator (main system clock) RTC1HZ: Real-time clock correction XT1. XT2: Crystal oscillator (subsystem clock) clock (1 Hz) output

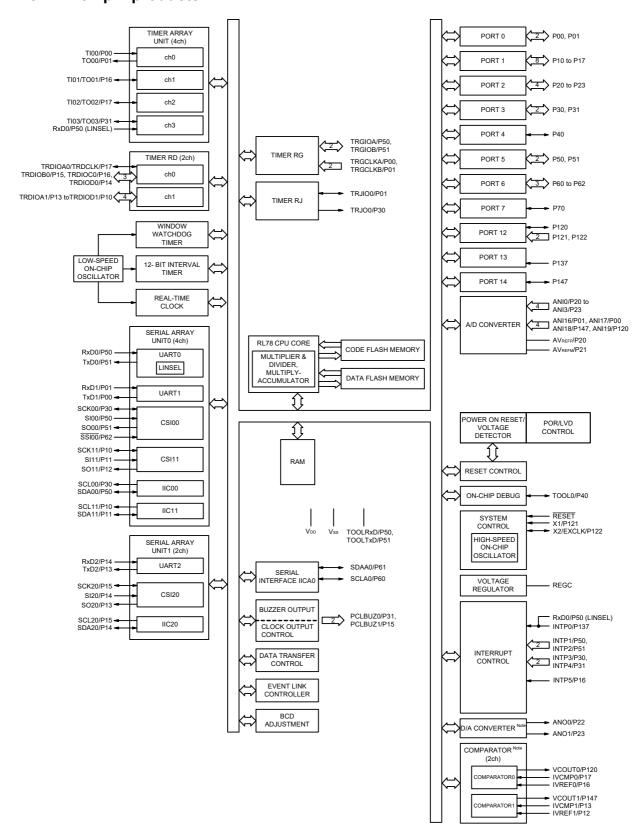
## 1.5 Block Diagram

# **1.5.1 30-pin products**



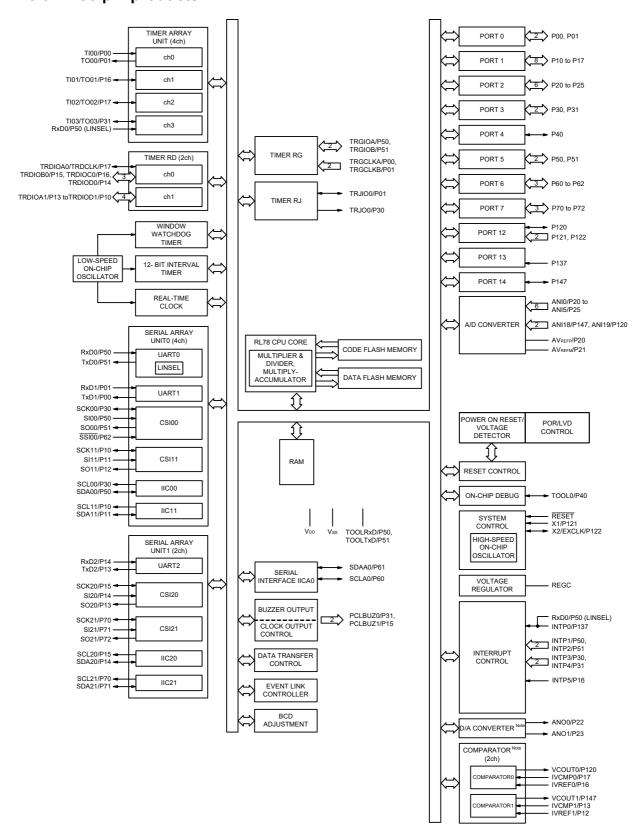
**Note** Mounted on the 96 KB or more code flash memory products.

### **1.5.2 32-pin products**



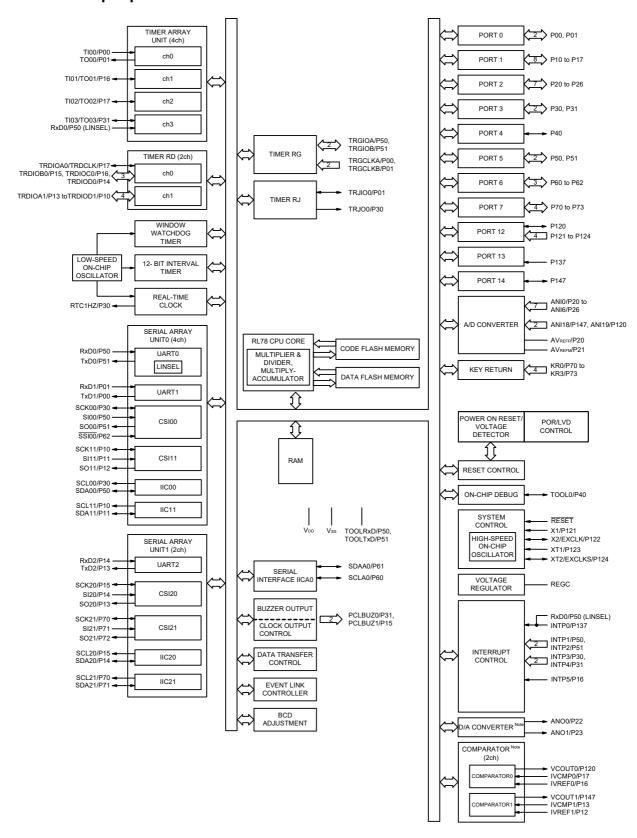
**Note** Mounted on the 96 KB or more code flash memory products.

### **1.5.3 36-pin products**



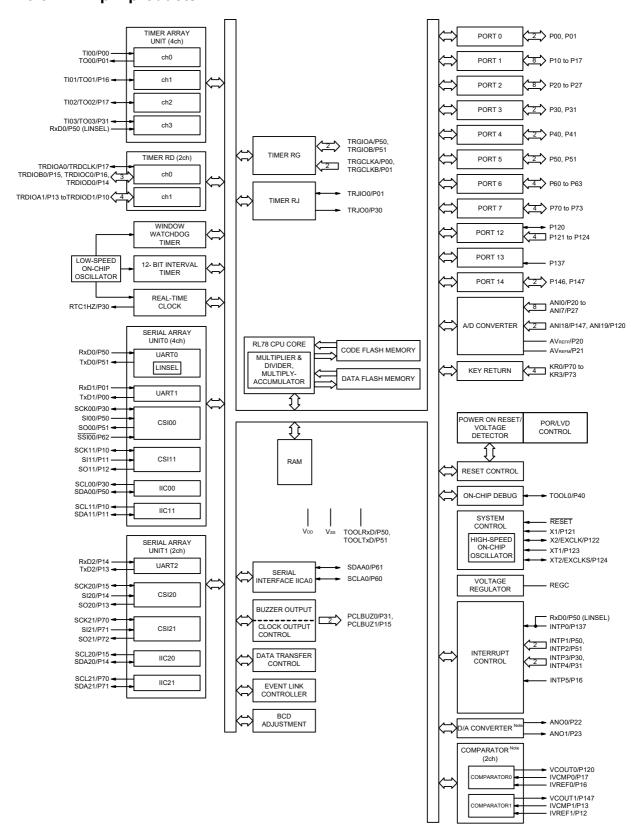
**Note** Mounted on the 96 KB or more code flash memory products.

## 1.5.4 40-pin products



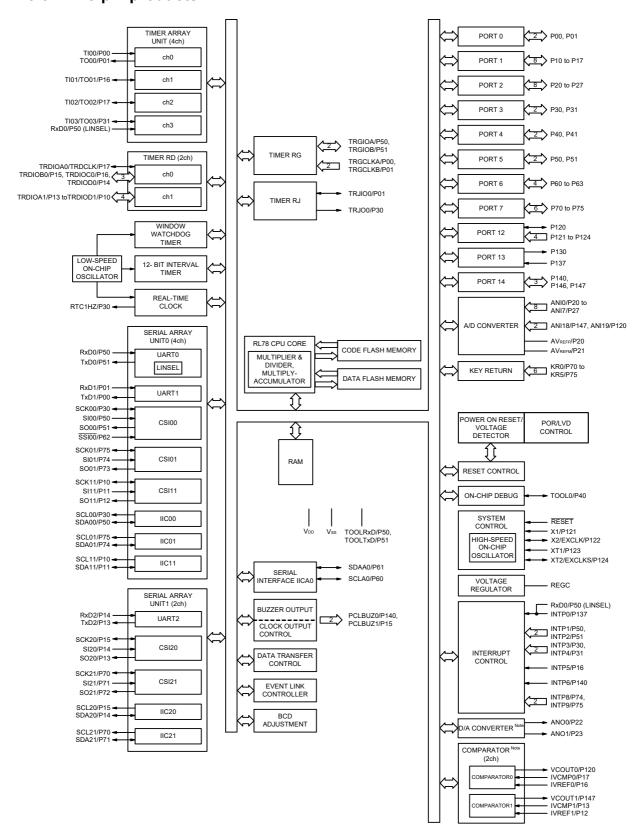
**Note** Mounted on the 96 KB or more code flash memory products.

### **1.5.5 44-pin products**



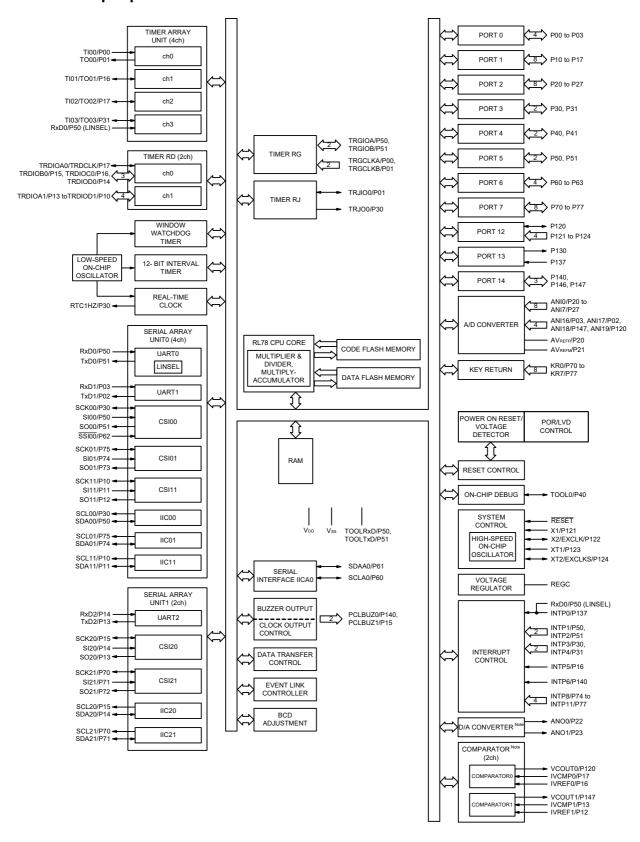
**Note** Mounted on the 96 KB or more code flash memory products.

### **1.5.6 48-pin products**



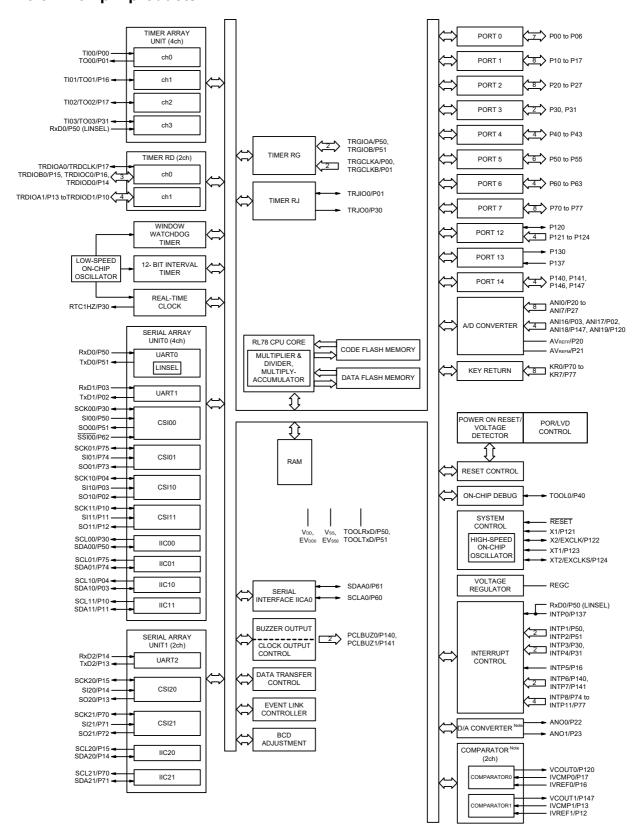
**Note** Mounted on the 96 KB or more code flash memory products.

## **1.5.7 52-pin products**



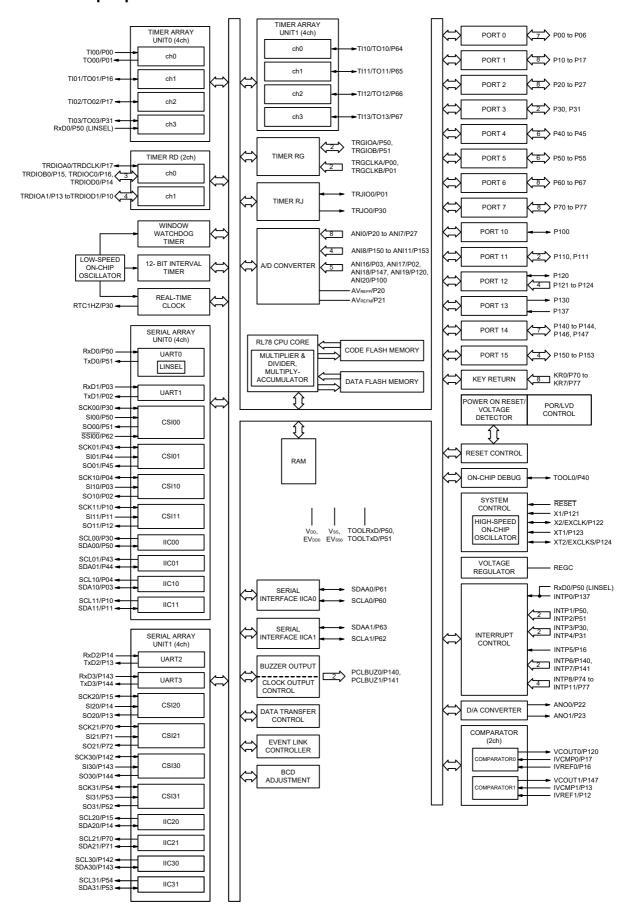
**Note** Mounted on the 96 KB or more code flash memory products.

### **1.5.8 64-pin products**

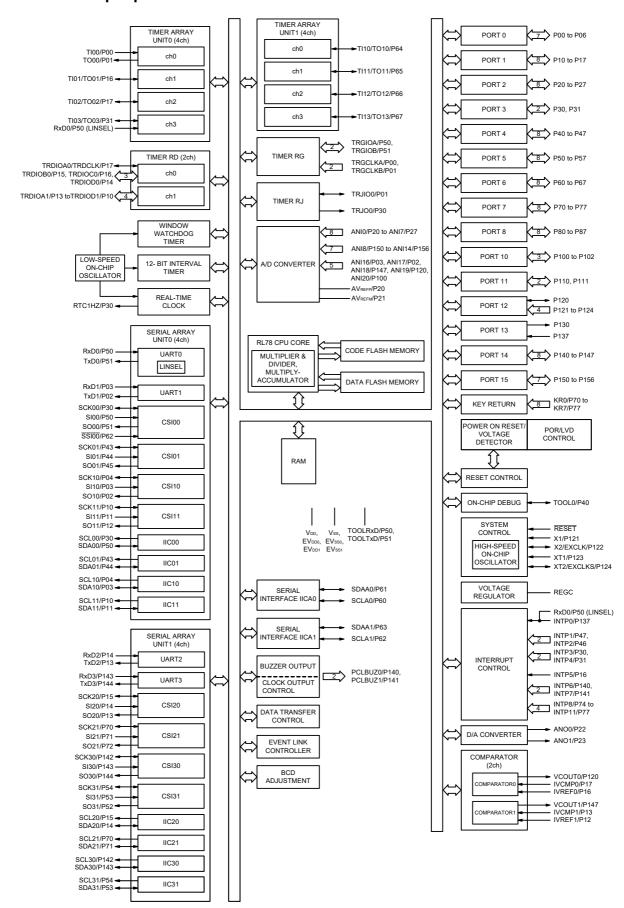


**Note** Mounted on the 96 KB or more code flash memory products.

## 1.5.9 80-pin products



## 1.5.10 100-pin products



### 1.6 Outline of Functions

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

					(1/2)			
		30-pin	32-pin	36-pin	40-pin			
	Item	R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)			
Code flash men	nory (KB)	16 to 64	16 to 64	16 to 64	16 to 64			
Data flash mem	nory (KB)	4	4	4	4			
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note			
Address space		1 MB		l	·			
Main system clock	High-speed system clock  High-speed on-chip oscillator clock (fiH)	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)  HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)						
Subsystem cloc	k	, 3 ,			XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-	chip oscillator clock	15 kHz (TYP.): VDD = 1.6	to 5.5 V		<u> </u>			
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)						
Minimum instru	ction execution time	0.03125 µs (High-speed on-chip oscillator clock: fін = 32 MHz operation)						
		0.05 μs (High-speed syste	em clock: fмx = 20 MHz op	eration)				
		— 30.5 μs (Subsystem clock: fsuB = 32.768 kHz operation)						
Instruction set		<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits)</li> <li>Multiplication and Accumulation (16 bits × 16 bits + 32 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>						
I/O port	Total	26	28	32	36			
	CMOS I/O	21	22	26	28			
	CMOS input	3	3	3	5			
	CMOS output	_	_	_	_			
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer F	RJ: 1 channel, Timer RD: 2	channels, Timer RG: 1 c	hannel)			
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 channel						
	RTC output		-		1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)			

(Note is listed on the next page.)

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H R5F104xE (x = A to C, E to G, J, L): Start address FE900H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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					•			
		30-pin	32-pin	36-pin	40-pin			
It	tem	R5F104Ax	R5F104Bx	R5F104Cx	R5F104Ex			
		(x = A, C  to  E)	(x = A, C to E)	(x = A, C  to  E)	(x = A, C  to  E)			
Clock output/buzzer	output	2	2	2	2			
			6 kHz, 1.25 MHz, 2.5 MH IN = 20 MHz operation) 6 kHz, 1.25 MHz, 2.5 MH IN = 20 MHz operation)		32.768 kHz			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels			
Serial interface		<ul> <li>Simplified SPI (CSI): 1</li> <li>Simplified SPI (CSI): 1</li> <li>[36-pin, 40-pin products]</li> <li>Simplified SPI (CSI): 1</li> </ul>	<ul> <li>Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified l<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified l<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified l<sup>2</sup>C: 1 channel</li> <li>[36-pin, 40-pin products]</li> <li>Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified l<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified l<sup>2</sup>C: 1 channel</li> </ul>					
	I <sup>2</sup> C bus	1 channel	1 channel	1 channel	1 channel			
Data transfer control	ller (DTC)	28 sources	32 sources	31 sources	29 sources			
Event link controller	(ELC)	Event input: 19 Event trigger output: 7						
Vectored interrupt	Internal	24	24	24	24			
sources	External	6	6	6	7			
Key interrupt		_	_	_	4			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access						
Power-on-reset circuit  Voltage detector  On-chip debug function		• Power-down-reset: 1.	<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C) 1.51 ±0.06 V (TA = -40 to +105°C)</li> <li>Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C) 1.50 ±0.06 V (TA = -40 to +105°C)</li> </ul>					
		1.63 V to 4.06 V (14 stag	es)					
		Provided						
Power supply voltage		V <sub>DD</sub> = 1.6 to 5.5 V (T <sub>A</sub> = - V <sub>DD</sub> = 2.4 to 5.5 V (T <sub>A</sub> = -	,					
Operating ambient temperature		TA = -40 to +85°C (A: Consumer applications, D: Industrial applications), TA = -40 to +105°C (G: Industrial applications)						

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

		<u> </u>			(.,			
		30-pin	32-pin	36-pin	40-pin			
	Item	R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)			
Code flash mer	mory (KB)	96 to 128	96 to 128	(X = F, G) 96 to 128	96 to 192			
Data flash mem		8	8	8	8			
RAM (KB)	, ()	12 to 16 Note	12 to 16 Note	12 to 16 Note	12 to 20 Note			
Address space		1 MB						
Main system	High-speed system	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK)						
clock	Clock  High-speed on-chip oscillator clock (fiн)	HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)  HS (high-speed main) mode: 1 to 32 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V),						
	,	LS (low-speed main) mod	le: 1 to 8 MHz (V <sub>DD</sub> = 1.8 de: 1 to 4 MHz (V <sub>DD</sub> = 1.6	to 5.5 V),				
Subsystem cloc	 ck	Lv (low-voltage main) mo	——————————————————————————————————————		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz			
Low-speed on-	chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V						
General-purpos	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)						
Minimum instru	ction execution time	0.03125 μs (High-speed o	on-chip oscillator clock: fiн	= 32 MHz operation)				
		0.05 μs (High-speed syste	em clock: fмx = 20 MHz op	eration)				
		— 30.5 μs (Subsystem clock: fsub = 32.768 kHz operation)						
Instruction set		Data transfer (8/16 bits)  Adder and subtractor/logical operation (8/16 bits)  Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits)  Multiplication and Accumulation (16 bits × 16 bits + 32 bits)  Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.						
I/O port	Total	26	28	32	36			
	CMOS I/O	21	22	26	28			
	CMOS input	3	3	3	5			
	CMOS output	_	_	_	_			
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3			
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer F	RJ: 1 channel, Timer RD: 2	channels, Timer RG: 1 cl	hannel)			
	Watchdog timer	1 channel						
	Real-time clock (RTC)	1 channel						
	12-bit interval timer	1 channel						
	Timer output	Timer outputs: 13 channel						
	RTC output	PWM outputs: 9 channels						

(Note is listed on the next page.)

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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					(2/2)		
		30-pin	32-pin	36-pin	40-pin		
ľ	tem	R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)		
Clock output/buzzer	output	2	2	2	2		
		[30-pin, 32-pin, 36-pin pro • 2.44 kHz, 4.88 kHz, 9.7 (Main system clock: fMA [40-pin products] • 2.44 kHz, 4.88 kHz, 9.7 (Main system clock: fMA • 256 Hz, 512 Hz, 1.024 (Subsystem clock: fsub	6 kHz, 1.25 MHz, 2.5 MH IN = 20 MHz operation) 6 kHz, 1.25 MHz, 2.5 MH IN = 20 MHz operation)	z, 5 MHz, 10 MHz	., 32.768 kHz		
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels		
D/A converter		1 channel	2 channels				
Comparator		2 channels					
Serial interface		<ul> <li>Simplified SPI (CSI): 1</li> <li>Simplified SPI (CSI): 1</li> <li>[36-pin, 40-pin products]</li> <li>Simplified SPI (CSI): 1</li> <li>Simplified SPI (CSI): 1</li> </ul>	<ul> <li>Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I<sup>2</sup>C: 1 channel</li> </ul>				
	I <sup>2</sup> C bus	1 channel	1 channel	1 channel	1 channel		
Data transfer contro	ller (DTC)	30 sources	•		31 sources		
Event link controller	(ELC)	Event input: 21 Event trigger output: 8	Event input: 21, Event trigger output: 9		Event input: 22 Event trigger output: 9		
Vectored interrupt	Internal	24	24	24	24		
sources	External	6	6	6	7		
Key interrupt	•	_	_	_	4		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access					
Power-on-reset circuit		• Power-down-reset: 1.	<ul> <li>Power-on-reset: 1.51 ±0.04 V (T<sub>A</sub> = -40 to +85°C)         <ul> <li>1.51 ±0.06 V (T<sub>A</sub> = -40 to +105°C)</li> </ul> </li> <li>Power-down-reset: 1.50 ±0.04 V (T<sub>A</sub> = -40 to +85°C)         <ul> <li>1.50 ±0.06 V (T<sub>A</sub> = -40 to +105°C)</li> </ul> </li> </ul>				
Voltage detector		1.63 V to 4.06 V (14 stag	es)				
On-chip debug func	tion	Provided					
Power supply voltag	е	VDD = 1.6 to 5.5 V (TA = - VDD = 2.4 to 5.5 V (TA = -	•				
Operating ambient to	emperature	$T_A = -40 \text{ to } +85^{\circ}\text{C (A: Co}$ $T_A = -40 \text{ to } +105^{\circ}\text{C (G: Ir}$	• • • • • • • • • • • • • • • • • • • •	ndustrial applications),			

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

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					(172)
		44-pin	48-pin	52-pin	64-pin
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx
		(x = A, C  to  E)	(x = A, C  to  E)	(x = C  to  E)	(x = C to E)
Code flash me	mory (KB)	16 to 64	16 to 64	32 to 64	32 to 64
Data flash mer	mory (KB)	4	4	4	4
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	4 to 5.5 Note	4 to 5.5 Note
Address space	<b>;</b>	1 MB			
Main system clock	High-speed system clock	HS (high-speed main) HS (high-speed main) LS (low-speed main) n	scillation, external main mode: 1 to 20 MHz (V mode: 1 to 16 MHz (V node: 1 to 8 MHz (VD mode: 1 to 4 MHz (VD	DD = 2.7 to 5.5 V), DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),	(CLK)
	High-speed on-chip oscillator clock (fін)	HS (high-speed main)	mode: 1 to 32 MHz (V mode: 1 to 16 MHz (V node: 1 to 8 MHz (VD mode: 1 to 4 MHz (VD	DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),	
Subsystem clock XT1 (crystal) oscillation, external subsystem				lock input (EXCLKS) 3	2.768 kHz
Low-speed on-	-chip oscillator clock	15 kHz (TYP.): VDD = 1	I.6 to 5.5 V		
General-purpose register 8 bits × 32 registers (8 bits × 8 registers × 4 banks)					
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: fιн = 32 MHz operation)			
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)			
		30.5 μs (Subsystem clock: fsub = 32.768 kHz operation)			
<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32</li> <li>Multiplication and Accumulation (16 bits × 16 bits + 32 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation)</li> </ul>					
I/O port	Total	40	44	48	58
	CMOS I/O	31	34	38	48
	CMOS input	5	5	5	5
	CMOS output	_	1	1	1
	N-ch open-drain I/O (6 V tolerance)	4	4	4	4
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 13 char PWM outputs: 9 chann			
	RTC output	1 • 1 Hz (subsystem clock: fsuB = 32.768 kHz)			

(Note is listed on the next page.)

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H R5F104xE (x = A to C, E to G, J, L): Start address FE900H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.



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		+	T	ı	(2/2			
		44-pin	48-pin	52-pin	64-pin			
It	em	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx			
		(x = A, C to E)	(x = A, C  to  E)	(x = C to E)	(x = C to E)			
Clock output/buzz	er output	2	2	2	2			
		<ul> <li>• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation)</li> <li>• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: fsub = 32.768 kHz operation)</li> </ul>						
8/10-bit resolution A/D converter		10 channels	10 channels	12 channels	12 channels			
Serial interface		[44-pin products]  • Simplified SPI (CSI): 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I <sup>2</sup> C: 1 channel  • Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels  [48-pin, 52-pin products]  • Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels  [64-pin products]  • Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I <sup>2</sup> C: 2 channels						
		• Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels						
	I <sup>2</sup> C bus	1 channel	1 channel	1 channel	1 channel			
Data transfer cont	roller (DTC)	29 sources	30 sources		31 sources			
Event link controlle	er (ELC)	Event input: 20 Event trigger output: 7						
Vectored	Internal	24	24	24	24			
interrupt sources	External	7	10	12	13			
Key interrupt	•	4	6	8	8			
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access						
Power-on-reset ci	Power-on-reset circuit		<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)</li></ul>					
Voltage detector		1.63 V to 4.06 V (14 s	tages)					
On-chip debug fur	nction	Provided						
Power supply volt	age	VDD = 1.6 to 5.5 V (TA VDD = 2.4 to 5.5 V (TA	•					
Operating ambien	t temperature				$T_A = -40 \text{ to } +85^{\circ}\text{C}$ (A: Consumer applications, D: Industrial applications), $T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications)			

Note

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

		44-pin	48-pin	52-pin	64-pin	
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx	
		(x = F  to  H, J)	(x = F  to  H, J)	(x = F to H, J)	(x = F  to  H, J)	
Code flash m	nemory (KB)	96 to 256	96 to 256	96 to 256	96 to 256	
Data flash m	emory (KB)	8	8	8	8	
RAM (KB)		12 to 24 <sup>Note</sup>	12 to 24 Note	12 to 24 Note	12 to 24 Note	
Address space	ce	1 MB				
Main system clock	clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)				
	High-speed on-chip oscillator clock (fін)	HS (high-speed main) LS (low-speed main) n	mode: 1 to 32 MHz (V mode: 1 to 16 MHz (V node: 1 to 8 MHz (V mode: 1 to 4 MHz (V	'DD = 2.4 to 5.5 V), DD = 1.8 to 5.5 V),		
Subsystem c	lock	XT1 (crystal) oscillatio	n, external subsystem o	clock input (EXCLKS) 3	2.768 kHz	
Low-speed o	n-chip oscillator clock	15 kHz (TYP.): V <sub>DD</sub> = 1	I.6 to 5.5 V			
General-purp	oose register	8 bits × 32 registers (8	bits × 8 registers × 4 ba	anks)		
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)				
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)				
		30.5 μs (Subsystem clock: fsuв = 32.768 kHz operation)				
Multiplication (8 bits     Multiplication and A		its)				
IIISUUCUON SE	91	Adder and subtractor     Multiplication (8 bits     Multiplication and Act	cumulation (16 bits × 16	s), Division (16 bits ÷ 16		
I/O port	Total	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac	$\times$ 8 bits, 16 bits $\times$ 16 bit cumulation (16 bits $\times$ 10	s), Division (16 bits ÷ 16 6 bits + 32 bits)		
		Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a	× 8 bits, 16 bits × 16 bit cumulation (16 bits × 10 and bit manipulation (Se	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole	ean operation), etc.	
	Total	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a	× 8 bits, 16 bits × 16 bit cumulation (16 bits × 10 nd bit manipulation (Se	s), Division (16 bits ÷ 16 6 bits + 32 bits) et, reset, test, and Boole	ean operation), etc.	
	Total CMOS I/O	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a     40     31	× 8 bits, 16 bits × 16 bit cumulation (16 bits × 10 nd bit manipulation (Se 44 34	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38	ean operation), etc. 58 48	
	Total CMOS I/O CMOS input	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a     40     31	× 8 bits, 16 bits × 16 bit cumulation (16 bits × 10 nd bit manipulation (Se 44 34 5	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38	58 48 5	
	Total CMOS I/O CMOS input CMOS output N-ch open-drain I/O	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a     40     31     5     —     4  8 channels	× 8 bits, 16 bits × 16 bits cumulation (16 bits × 10 nd bit manipulation (Set 44 34 5 1	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38 5	58 48 5 1	
I/O port	Total CMOS I/O CMOS input CMOS output N-ch open-drain I/O (6 V tolerance)	Adder and subtractor     Multiplication (8 bits     Multiplication and Ac     Rotate, barrel shift, a     40     31     5     —     4  8 channels	× 8 bits, 16 bits × 16 bits cumulation (16 bits × 10 nd bit manipulation (Set 44 34 5 1	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38 5 1	58 48 5 1	
I/O port	Total  CMOS I/O  CMOS input  CMOS output  N-ch open-drain I/O  (6 V tolerance)  16-bit timer	Adder and subtractor Multiplication (8 bits Multiplication and Ac Rotate, barrel shift, a  40  31  5  4  8 channels (TAU: 4 channels, Tim	× 8 bits, 16 bits × 16 bits cumulation (16 bits × 10 nd bit manipulation (Set 44 34 5 1	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38 5 1	58 48 5 1	
I/O port	Total  CMOS I/O  CMOS input  CMOS output  N-ch open-drain I/O  (6 V tolerance)  16-bit timer  Watchdog timer  Real-time clock	Adder and subtractor Multiplication (8 bits Multiplication and Ac Rotate, barrel shift, a  40  31  5  — 4  8 channels (TAU: 4 channels, Tim 1 channel	× 8 bits, 16 bits × 16 bits cumulation (16 bits × 10 nd bit manipulation (Set 44 34 5 1	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38 5 1	58 48 5 1	
I/O port	Total  CMOS I/O  CMOS input  CMOS output  N-ch open-drain I/O (6 V tolerance)  16-bit timer  Watchdog timer  Real-time clock (RTC)	Adder and subtractor Multiplication (8 bits Multiplication and Ac Rotate, barrel shift, a  40  31  5  — 4  8 channels (TAU: 4 channels, Tim 1 channel  1 channel	× 8 bits, 16 bits × 16 bits cumulation (16 bits × 10 and bit manipulation (Set 44 34 5 1 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	s), Division (16 bits ÷ 16 bits + 32 bits) et, reset, test, and Boole 48 38 5 1	58 48 5 1	

(Note is listed on the next page.)

Note

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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		44-pin	48-pin	52-pin	64-pin		
It	em	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx		
	Citi	(x = F to H, J)	(x = F to H, J)	(x = F to H, J)	(x = F to H, J)		
Clock output/buzz	er output	2	2	2	2		
Olook Gutput Buzz	or output		<del>-</del>		_		
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: fmain = 20 MHz operation)					
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz					
			(Subsystem clock: fsub = 32.768 kHz operation)				
8/10-bit resolution A/D converter D/A converter Comparator		10 channels	10 channels	12 channels	12 channels		
		2 channels			•		
		2 channels					
Serial interface		l <sup>2</sup> C: 1 channel • Simplified SPI (CSI):	1 channel/UART (UAR 1 channel/UART: 1 channels/UART: 1 ch	annel/simplified I <sup>2</sup> C: 1	channel		
		<ul> <li>[48-pin, 52-pin produc</li> <li>Simplified SPI (CSI):</li> <li>I<sup>2</sup>C: 2 channels</li> <li>Simplified SPI (CSI):</li> </ul>	<ul> <li>Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I<sup>2</sup>C: 2 channels [48-pin, 52-pin products]</li> <li>Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I<sup>2</sup>C: 2 channels</li> <li>Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I<sup>2</sup>C: 1 channel</li> <li>Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I<sup>2</sup>C: 2 channels</li> </ul>				
		<ul> <li>[64-pin products]</li> <li>Simplified SPI (CSI):</li> <li>I<sup>2</sup>C: 2 channels</li> <li>Simplified SPI (CSI):</li> </ul>	2 channels/UART (UA 2 channels/UART: 1 cl 2 channels/UART: 1 cl	RT supporting LIN-bus	s): 1 channel/simplifie 2 channels		
	I <sup>2</sup> C bus	1 channel	1 channel	1 channel	1 channel		
Data transfer cont			32 sources	1 chamici	33 sources		
Event link controll	, ,	31 sources 32 sources 33 sources  Event input: 22  Event trigger output: 9					
Vectored	Internal	24	24	24	24		
interrupt sources	External	7	10	12	13		
Key interrupt	<u> </u>	4	6	8	8		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access					
Power-on-reset ci	rcuit	<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.51 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> <li>Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.50 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> </ul>					
Voltage detector		1.63 V to 4.06 V (14 s	tages)				
On-chip debug fur	nction	Provided					
Power supply volt		VDD = 1.6 to 5.5 V (TA VDD = 2.4 to 5.5 V (TA	•				
Operating ambien	t temperature	T <sub>A</sub> = -40 to +85°C (A:	Consumer applications  3: Industrial applications		tions),		

Note

The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.



[48-pin, 64-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

			(1/2		
		48-pin	64-pin		
	Item	R5F104Gx	R5F104Lx		
		(x = K, L)	(x = K, L)		
Code flash memory	(KB)	384 to 512	384 to 512		
Data flash memory	(KB)	8 8			
RAM (KB)		32 to 48 <sup>Note</sup>	32 to 48 <sup>Note</sup>		
Address space		1 MB			
Main system clock High-speed system clock		X1 (crystal/ceramic) oscillation, external m HS (high-speed main) mode: 1 to 20 MHz HS (high-speed main) mode: 1 to 16 MHz LS (low-speed main) mode: 1 to 8 MHz LV (low-voltage main) mode: 1 to 4 MHz	t (VDD = 2.7 to 5.5 V), t (VDD = 2.4 to 5.5 V), (VDD = 1.8 to 5.5 V),		
	High-speed on-chip oscillator clock (fih)	HS (high-speed main) mode: 1 to 32 MHz HS (high-speed main) mode: 1 to 16 MHz LS (low-speed main) mode: 1 to 8 MHz LV (low-voltage main) mode: 1 to 4 MHz	(VDD = 2.4 to 5.5 V), (VDD = 1.8 to 5.5 V),		
Subsystem clock		XT1 (crystal) oscillation, external subsyste	m clock input (EXCLKS) 32.768 kHz		
Low-speed on-chip oscillator clock		15 kHz (TYP.): VDD = 1.6 to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4	4 banks)		
Minimum instruction	n execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)			
		0.05 μs (High-speed system clock: fмx = 2	0 MHz operation)		
		30.5 μs (Subsystem clock: fsub = 32.768 k	Hz operation)		
Instruction set		<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8</li> <li>Multiplication (8 bits × 8 bits, 16 bits × 16 32 bits)</li> <li>Multiplication and Accumulation (16 bits and Rotate, barrel shift, and bit manipulation etc.</li> </ul>	bits), Division (16 bits ÷ 16 bits, 32 bits ÷  < 16 bits + 32 bits)		
I/O port	Total	44	58		
	CMOS I/O	34	48		
	CMOS input	5	5		
	CMOS output	1	1		
	N-ch open-drain I/O (6 V tolerance)	4	4		
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Tir	ner RD: 2 channels, Timer RG: 1 channel)		
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 14 channels PWM outputs: 9 channels			
	RTC output	1 • 1 Hz (subsystem clock: fsub = 32.768 kH	z)		

(Note is listed on the next page.)

**Note** The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(2/2)

		<del> </del>	` '	
		48-pin	64-pin	
Item		R5F104Gx	R5F104Lx	
		(x = K, L)	= K, L) $(x = K, L)$	
Clock output/buzzer output		2	2	
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.	5 MHz, 5 MHz, 10 MHz	
		(Main system clock: fmain = 20 MHz operation	on)	
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09		
		(Subsystem clock: fsub = 32.768 kHz opera	tion)	
8/10-bit resolution A/D	converter	10 channels	12 channels	
D/A converter 2 channels				
Comparator		2 channels		
Serial interface  [48-pin products]  • Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channels  I <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 1 channel/UART: 1 channel/simplified I <sup>2</sup> C: 1 channel  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels		annel/simplified I <sup>2</sup> C: 1 channel		
		<ul> <li>[64-pin products]</li> <li>Simplified SPI (CSI): 2 channels/UART (UAI2C: 2 channels</li> <li>Simplified SPI (CSI): 2 channels/UART: 1 ch</li> <li>Simplified SPI (CSI): 2 channels/UART: 1 ch</li> </ul>	nannel/simplified l <sup>2</sup> C: 2 channels	
	I <sup>2</sup> C bus	1 channel	1 channel	
Data transfer controller	· (DTC)	32 sources	33 sources	
Event link controller (E	LC)	Event input: 22		
,	,	Event trigger output: 9		
Vectored interrupt	Internal	24	24	
sources	External	10	13	
Key interrupt		6	8	
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Internal reset by RAM parity error Internal reset by illegal-memory access		
Power-on-reset circuit		<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)</li></ul>		
Voltage detector		1.63 V to 4.06 V (14 stages)		
On-chip debug function	າ	Provided		
Power supply voltage		V <sub>DD</sub> = 1.6 to 5.5 V (T <sub>A</sub> = -40 to +85°C) V <sub>DD</sub> = 2.4 to 5.5 V (T <sub>A</sub> = -40 to +105°C)		
Operating ambient tem	perature	TA = -40 to +85°C (A: Consumer applications TA = -40 to +105°C (G: Industrial applications		

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (code flash memory 96 KB to 256 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

			(1/2)	
		80-pin	100-pin	
	Item	R5F104Mx	R5F104Px	
		(x = F to H, J)	(x = F  to  H, J)	
Code flash me	mory (KB)	96 to 256	96 to 256	
Data flash mer	mory (KB)	8	8	
RAM (KB)		12 to 24 Note	12 to 24 Note	
Address space 1 MB		1 MB		
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)		
	High-speed on-chip oscillator clock (fін)	HS (high-speed main) mode: 1 to 32 MHz (VI HS (high-speed main) mode: 1 to 16 MHz (VI LS (low-speed main) mode: 1 to 8 MHz (VDI LV (low-voltage main) mode: 1 to 4 MHz (VDI	DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),	
Subsystem clo	ck	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz		
Low-speed on-	-chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V		
General-purpo	se register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)		
Minimum instru	uction execution time	0.03125 µs (High-speed on-chip oscillator clock: fін = 32 MHz operation)		
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)		
		30.5 μs (Subsystem clock: fsub = 32.768 kHz operation)		
Instruction set		<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits)</li> <li>Multiplication and Accumulation (16 bits × 16 bits + 32 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>		
I/O port	Total	74	92	
	CMOS I/O	64	82	
	CMOS input	5	5	
	CMOS output	1	1	
	N-ch open-drain I/O (6 V tolerance)	4	4	
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)		
	Watchdog timer	1 channel		
	Real-time clock (RTC)	1 channel		
	12-bit interval timer	1 channel		
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels		
	RTC output	1 • 1 Hz (subsystem clock: fsuB = 32.768 kHz)		
	1	1 ,		

**Note** In the case of the 24 KB, this is about 23 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(2/2)

		80-pin	100-pin	
It	em	R5F104Mx	R5F104Px	
		(x = F to H, J)	(x = F  to  H, J)	
Clock output/buzz	er output	2	2	
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.	5 MHz, 5 MHz, 10 MHz	
		(Main system clock: fmain = 20 MHz operation	,	
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09		
		(Subsystem clock: fsub = 32.768 kHz opera		
8/10-bit resolution	A/D converter	17 channels	20 channels	
D/A converter		2 channels	2 channels	
Comparator		2 channels	2 channels	
Serial interface  [80-pin, 100-pin products]  • Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channel l <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified l <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified l <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified l <sup>2</sup> C: 2 channels		nannel/simplified I <sup>2</sup> C: 2 channels nannel/simplified I <sup>2</sup> C: 2 channels		
	I <sup>2</sup> C bus	2 channels	2 channels	
Data transfer controller (DTC) 39 sources 39 sources		39 sources		
Event link controll	er (ELC)	Event input: 26 Event trigger output: 9		
Vectored	Internal	32	32	
interrupt sources	External	13	13	
Key interrupt	<u> </u>	8	8	
Reset  Reset by RESET pin  Internal reset by watchdog timer  Internal reset by power-on-reset  Internal reset by voltage detector  Internal reset by illegal instruction execution Note  Internal reset by RAM parity error  Internal reset by illegal-memory access		n Note		
Power-on-reset circuit		<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.51 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> <li>Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.50 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> </ul>		
Voltage detector		1.63 V to 4.06 V (14 stages)		
On-chip debug fur	nction	Provided		
Power supply volt	age	V <sub>DD</sub> = 1.6 to 5.5 V (T <sub>A</sub> = -40 to +85°C) V <sub>DD</sub> = 2.4 to 5.5 V (T <sub>A</sub> = -40 to +105°C)		
Operating ambien	t temperature	$T_A = -40 \text{ to } +85^{\circ}\text{C}$ (A: Consumer applications $T_A = -40 \text{ to } +105^{\circ}\text{C}$ (G: Industrial applications	, ,	

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin products (code flash memory 384 KB to 512 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

			(1/2)	
		80-pin	100-pin	
	Item	R5F104Mx	R5F104Px	
		(x = K, L)	(x = K, L)	
Code flash me	mory (KB)	384 to 512	384 to 512	
Data flash mer	mory (KB)	8	8	
RAM (KB)		32 to 48 <sup>Note</sup>	32 to 48 Note	
Address space	<b>;</b>	1 MB		
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz (VDD = 2.7 to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz (VDD = 2.4 to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz (VDD = 1.8 to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz (VDD = 1.6 to 5.5 V)		
	High-speed on-chip oscillator clock (fiн)	HS (high-speed main) mode: 1 to 16 MHz (VLS (low-speed main) mode: 1 to 8 MHz (VD	(DD = 2.7 to 5.5 V), (DD = 2.4 to 5.5 V), (DD = 1.8 to 5.5 V), (DD = 1.6 to 5.5 V)	
Subsystem clo	ck	XT1 (crystal) oscillation, external subsystem c	lock input (EXCLKS) 32.768 kHz	
Low-speed on-	-chip oscillator clock	15 kHz (TYP.): VDD = 1.6 to 5.5 V		
General-purpo	se register	8 bits × 32 registers (8 bits × 8 registers × 4 ba	nks)	
Minimum instru	uction execution time	0.03125 µs (High-speed on-chip oscillator clock: fін = 32 MHz operation)		
		0.05 μs (High-speed system clock: fмx = 20 MHz operation)		
		30.5 μs (Subsystem clock: fsub = 32.768 kHz operation)		
Instruction set		<ul> <li>Data transfer (8/16 bits)</li> <li>Adder and subtractor/logical operation (8/16 bits)</li> <li>Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits)</li> <li>Multiplication and Accumulation (16 bits × 16 bits + 32 bits)</li> <li>Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.</li> </ul>		
I/O port	Total	74	92	
•	CMOS I/O	64	82	
	CMOS input	5	5	
	CMOS output	1	1	
	N-ch open-drain I/O (6 V tolerance)	4	4	
Timer	16-bit timer	12 channels (TAU: 8 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)		
	Watchdog timer	1 channel		
	Real-time clock (RTC)	1 channel		
	12-bit interval timer	1 channel		
	Timer output	Timer outputs: 18 channels PWM outputs: 12 channels		
	RTC output	1 • 1 Hz (subsystem clock: fsub = 32.768 kHz)		

**Note** In the case of the 48 KB, this is about 47 KB when the self-programming function and data flash function are used (For details, see **CHAPTER 3** in the RL78/G14 User's Manual).

(2/2)

		<u> </u>		
		80-pin	100-pin	
It	em	R5F104Mx	R5F104Px	
		(x = K, L)	(x = K, L)	
Clock output/buzz	er output	2	2	
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.	5 MHz, 5 MHz, 10 MHz	
		(Main system clock: fmain = 20 MHz operation	,	
		• 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.09		
		(Subsystem clock: fsub = 32.768 kHz opera	tion)	
8/10-bit resolution	A/D converter	17 channels	20 channels	
D/A converter		2 channels	2 channels	
Comparator		2 channels	2 channels	
Serial interface  [80-pin, 100-pin products]  • Simplified SPI (CSI): 2 channels/UART (UART supporting LIN-bus): 1 channels/C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels  • Simplified SPI (CSI): 2 channels/UART: 1 channel/simplified I <sup>2</sup> C: 2 channels		nannel/simplified I <sup>2</sup> C: 2 channels nannel/simplified I <sup>2</sup> C: 2 channels		
	I <sup>2</sup> C bus	2 channels	2 channels	
Data transfer controller (DTC) 39 sources 39 sources		39 sources		
Event link controll	er (ELC)	Event input: 26 Event trigger output: 9		
Vectored	Internal	32	32	
interrupt sources	External	13	13	
Key interrupt		8	8	
Reset  Reset by Internal Internal Internal Internal Internal Internal Internal		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Internal reset by RAM parity error Internal reset by illegal-memory access	n Note	
Power-on-reset circuit		<ul> <li>Power-on-reset: 1.51 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.51 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> <li>Power-down-reset: 1.50 ±0.04 V (TA = -40 to +85°C)         <ul> <li>1.50 ±0.06 V (TA = -40 to +105°C)</li> </ul> </li> </ul>		
Voltage detector		1.63 V to 4.06 V (14 stages)		
On-chip debug fur	nction	Provided		
Power supply volt	age	V <sub>DD</sub> = 1.6 to 5.5 V (T <sub>A</sub> = -40 to +85°C) V <sub>DD</sub> = 2.4 to 5.5 V (T <sub>A</sub> = -40 to +105°C)		
Operating ambien	t temperature	$T_A = -40$ to +85°C (A: Consumer applications $T_A = -40$ to +105°C (G: Industrial applications	, ,	

**Note** The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

# 2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications TA = -40 to +85°C R5F104xxAxx

- D: Industrial applications T<sub>A</sub> = -40 to +85°C R5F104xxDxx
- G: Industrial applications when TA = -40 to +105°C products is used in the range of TA = -40 to +85°C R5F104xxGxx
- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.

## 2.1 Absolute Maximum Ratings

#### **Absolute Maximum Ratings**

(1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVss0 = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V <sub>DD</sub> +0.3 Note 1	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P47, P50 to P57, P64 to P67,	and -0.3 to V <sub>DD</sub> +0.3 Note 2	
		P70 to P77, P80 to P87, P100 to P102,		
		P110, P111, P120, P140 to P147		
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vıз	P20 to P27, P121 to P124, P137,	-0.3 to V <sub>DD</sub> +0.3 Note 2	V
		P150 to P156, EXCLK, EXCLKS, RESET		
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P47, P50 to P57, P60 to P67,	and -0.3 to V <sub>DD</sub> +0.3 Note 2	
		P70 to P77, P80 to P87, P100 to P102,		
		P110, P111, P120, P130, P140 to P147		
	Vo2	P20 to P27, P150 to P156	-0.3 to V <sub>DD</sub> +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI20	-0.3 to EVDD0 +0.3	
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI14	-0.3 to V <sub>DD</sub> +0.3	V
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- **Note 3.** Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

#### **Absolute Maximum Ratings**

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
		-170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	Юн2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	ow IoL1 Per pin		P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
		170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal c	pperation mode	-40 to +85	°C
temperature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

#### 2.2 Oscillator Characteristics

### 2.2.1 X1, XT1 characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$ 

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	2.4 V ≤ V <sub>DD</sub> < 2.7 V	1.0		16.0	
		1.8 V ≤ V <sub>DD</sub> < 2.4 V	1.0		8.0	
		1.6 V ≤ V <sub>DD</sub> < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G14 User's Manual.

### 2.2.2 On-chip oscillator characteristics

(TA = -40 to +85°C, 1.6 V  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

Oscillators	Parameters	C	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator clock frequency		-20 to +85°C	$1.8 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	-1.0		+1.0	%
accuracy			1.6 V ≤ VDD < 1.8 V	-5.0		+5.0	%
		-40 to -20°C	1.8 V ≤ VDD < 5.5 V	-1.5		+1.5	%
			1.6 V ≤ VDD < 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

**Note 1.** High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

#### 2.3 DC Characteristics

#### 2.3.1 Pin characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

(1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	1.6 V ≤ EVDD0 ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$			-55.0	mA
		(When duty ≤ 70% Note 3)  1.  1.  1.  1.  1.  1.  1.  1.  1.  1	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			-10.0	mA
			$1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-5.0	mA
	Іон2		1.6 V ≤ EVDD0 < 1.8 V			-2.5	mA
			$4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}$			-80.0	mA
			2.7 V ≤ EVDD0 < 4.0 V			-19.0	mA
			1.8 V ≤ EVDD0 < 2.7 V			-10.0	mA
		P111, P146, P147 (When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	1.6 V ≤ EVDD0 ≤ 5.5 V			-135.0 Note 4	mA
			1.6 V ≤ VDD ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ VDD ≤ 5.5 V			-1.5	mA

**Note 1.** Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, EVDD1, VDD pins to an output pin.

**Note 3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH  $\times$  0.7)/(n  $\times$  0.01) <Example> Where n = 80% and IoH = -10.0 mA Total output current of pins = (-10.0  $\times$  0.7)/(80  $\times$  0.01)  $\approx$  -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Note 4. -100 mA for industrial applications (R5F104xxDxx, R5F104xxGxx).

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Note 2. Do not exceed the total current value.

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V			70.0	mA
		P102, P120, P130, P140 to P145	2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			15.0	mA
		(When duty ≤ 70% Note 3)	1.8 V ≤ EV <sub>DD0</sub> < 2.7 V			9.0	mA
		1.0	1.6 V ≤ EVDD0 < 1.8 V			4.5	mA
		Total of P05, P06, P10 to P17, 4.	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			80.0	mA
		P30, P31, P50 to P57,	2.7 V ≤ EVDD0 < 4.0 V			35.0	mA
		P60 to P67, P70 to P77, P80 to P87, P100, P101, P110,	1.8 V ≤ EVDD0 < 2.7 V			20.0	mA
		P111, P146, P147 (When duty ≤ 70% Note 3)	1.6 V ≤ EVDD0 < 1.8 V			10.0	mA
	lo <sub>L2</sub>	Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )				150.0	mA
		Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	1.6 V ≤ VDD ≤ 5.5 V			5.0	mA

- **Note 1.** Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoL × 0.7)/(n × 0.01)

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$ 

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

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Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVDD0		EVDD0	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EV <sub>DD0</sub>	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV <sub>DD0</sub>	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EV <sub>DD0</sub>	V
	VIH3	P20 to P27, P150 to P156	0.7 Vdd		VDD	V	
	VIH4	P60 to P63		0.7 EVDD0		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0.8 Vdd		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156	1	0		0.3 VDD	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 VDD	V

Caution The maximum value of ViH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

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Items	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IOH1 = -10.0 mA	EVDD0 - 1.5			V
		P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P111, P120, P130, P140 to P147	1.8 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -1.5 mA	EVDD0 - 0.5			V
			1.6 V ≤ EVDD0 < 1.8 V, IOH1 = -1.0 mA	EVDD0 - 0.5			٧
	VOH2	P20 to P27, P150 to P156	1.6 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA	VDD - 0.5			٧
Output voltage, low	Vol1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IOL1} = 20.0 \text{ mA}$			1.3	٧
	1	P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 8.5 mA			0.7	٧
		P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{IoL1} = 1.5 \text{ mA}$			0.4	V
			$1.8 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V},$ $10L1 = 0.6 \text{ mA}$			0.4	٧
			1.6 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 0.3 mA			0.4	V
	VOL2	P20 to P27, P150 to P156	$1.6 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ $10L2 = 400  \mu\text{A}$			0.4	٧
	VOL3	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA			2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 5.0 mA			0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA			0.4	V
			1.8 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 2.0 mA			0.4	V
		1.6 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 1.0 mA			0.4	V	

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(5/5)

Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVDDO	)			1	μА
	ILIH2	P20 to P27, P137, P150 to P156, RESET	VI = VDD				1	μA
	Ішнз	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μA
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVsso	, In input port	10	20	100	kΩ

# 2.3.2 Supply current characteristics

## (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.4		mA
current Note 1		mode	mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.4		
Note 1				fносо = 32 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.1		
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.1		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.1	8.7	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.1	8.7	
				fHOCO = 32 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.8	8.1	
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.8	8.1	
				fHOCO = 48 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.0	6.9	
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.0	6.9	
				fHOCO = 24 MHz,	Normal	V <sub>DD</sub> = 5.0 V		3.8	6.3	
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		3.8	6.3	
				fносо = 16 MHz,	Normal	V <sub>DD</sub> = 5.0 V		2.8	4.6	
				fih = 16 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.8	4.6	
			LS (low-speed main)	fносо = 8 MHz,	Normal	V <sub>DD</sub> = 3.0 V		1.3	2.0	mA
			mode Note 5	fih = 8 MHz Note 3	operation	V <sub>DD</sub> = 2.0 V		1.3	2.0	
			LV (low-voltage main)	fносо = 4 MHz,	Normal	V <sub>DD</sub> = 3.0 V		1.3	1.8	mA
	mode Note 5	mode Note 5	fiH = 4 MHz Note 3	operation	V <sub>DD</sub> = 2.0 V		1.3	1.8		
		HS (high-speed main)	Ver = F 0 V	Normal	Square wave input		3.3	5.3	mA	
		mode Note 5		Resonator connection		3.4	5.5			
				f <sub>MX</sub> = 20 MHz Note 2,	Normal	Square wave input		3.3	5.3	
			V <sub>DD</sub> = 3.0 V	V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.4	5.5	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.1	
				V <sub>DD</sub> = 5.0 V	operation	Resonator connection		2.1	3.2	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.1	
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.1	3.2	
			LS (low-speed main)	f <sub>MX</sub> = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	mA
			mode Note 5	V <sub>DD</sub> = 3.0 V	operation	Resonator connection		1.2	2.0	
				f <sub>MX</sub> = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	
				V <sub>DD</sub> = 2.0 V	operation	Resonator connection		1.2	2.0	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μA
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				TA = +25°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	
			TA = +50°C	operation	Resonator connection		4.8	6.7	1	
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	┤	
				T <sub>A</sub> = +70°C	operation	Resonator connection		4.8	7.5	1
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	1	
				T <sub>A</sub> = +85°C	operation	Resonator connection		5.4	8.9	1

(Notes and Remarks are listed on the next page.)

- **Note 1.** Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode:  $1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 8 MHz LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
  Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)
  Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

# (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	I <sub>DD2</sub>	HALT mode	HS (high-speed main)	fhoco = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.80	3.09	mA
Note 1	Note 2		mode Note 6	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.80	3.09	
				fносо = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.49	2.40	
				fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.49	2.40	
				fносо = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.62	2.40	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.62	2.40	
				fHOCO = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.4	1.83	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.4	1.83	
				fHOCO = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.37	1.38	
				fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.37	1.38	
			LS (low-speed main)	fHOCO = 8 MHz,	V <sub>DD</sub> = 3.0 V		260	710	μA
			mode Note 6	fih = 8 MHz Note 4	V <sub>DD</sub> = 2.0 V		260	710	
			LV (low-voltage main)	fHOCO = 4 MHz,	V <sub>DD</sub> = 3.0 V		420	700	μA
			mode Note 6	fih = 4 MHz Note 4	V <sub>DD</sub> = 2.0 V		420	700	
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.28	1.55	mA
			mode Note 6	V <sub>DD</sub> = 5.0 V	Resonator connection		0.40	1.74	
				fmx = 20 MHz Note 3,	Square wave input		0.28	1.55	
			V <sub>DD</sub> = 3.0 V	Resonator connection		0.40	1.74		
				f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.19	0.86	
					Resonator connection		0.25	0.93	
				f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.19	0.86	
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.25	0.93	
			LS (low-speed main) mode Note 6	fmx = 8 MHz Note 3,	Square wave input		95	550	μA
					Resonator connection		140	590	]
					Square wave input		95	550	
				V <sub>DD</sub> = 2.0 V	Resonator connection		140	590	
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μΑ
			operation	T <sub>A</sub> = -40°C	Resonator connection		0.44	0.76	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.30	0.57	
				T <sub>A</sub> = +25°C	Resonator connection		0.49	0.76	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				T <sub>A</sub> = +50°C	Resonator connection		0.59	1.36	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				T <sub>A</sub> = +70°C	Resonator connection		0.72	2.16	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				T <sub>A</sub> = +85°C	Resonator connection		1.16	3.56	
	IDD3	STOP mode	TA = -40°C				0.18	0.51	μΑ
IU		Note 7	T <sub>A</sub> = +25°C				0.24	0.51	
			T <sub>A</sub> = +50°C				0.29	1.10	1
			T <sub>A</sub> = +70°C				0.41	1.90	
			T <sub>A</sub> = +85°C				0.90	3.30	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the

Note 2. During HALT instruction execution by flash memory.

peripheral modules.

- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 4.** When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V@1}$  MHz to 32 MHz

 $2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode: 1.8 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 4 MHz

- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

### (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit	
Supply	IDD1	Operating	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.6		mA	
current		mode	mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.6		1	
Note 1				fHOCO = 32 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.3		1	
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.3			
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.4	10.2	mA	
			mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.4	10.2		
				fHOCO = 32 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.0	9.6		
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.0	9.6		
				fhoco = 48 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.2	7.8		
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.2	7.8		
				fhoco = 24 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.0	7.4	1	
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.0	7.4	1	
				fhoco = 16 MHz,	Normal	V <sub>DD</sub> = 5.0 V		3.0	5.3	1	
				fih = 16 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		3.0	5.3		
			LS (low-speed main)	fносо = 8 MHz,	Normal	V <sub>DD</sub> = 3.0 V		1.4	2.3	mA	
			mode Note 5	f <sub>IH</sub> = 8 MHz Note 3	operation	V <sub>DD</sub> = 2.0 V		1.4	2.3		
			LV (low-voltage main)	fносо = 4 MHz,	Normal	V <sub>DD</sub> = 3.0 V		1.3	1.9	mA	
			mode Note 5	f <sub>IH</sub> = 4 MHz Note 3	operation	V <sub>DD</sub> = 2.0 V		1.3	1.9	1	
			HS (high-speed main)	f <sub>MX</sub> = 20 MHz Note 2,	Normal	Square wave input		3.4	6.2	mA	
			mode Note 5	V <sub>DD</sub> = 5.0 V	operation	Resonator connection		3.6	6.4		
				f <sub>MX</sub> = 20 MHz Note 2,	Normal	Square wave input		3.4	6.2	1	
					V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.6	6.4	]
				f <sub>MX</sub> = 10 MHz Note 2, V <sub>DD</sub> = 5.0 V f <sub>MX</sub> = 10 MHz Note 2,	Normal operation	Square wave input		2.1	3.6		
						Resonator connection		2.2	3.7		
						Square wave input		2.1	3.6	1	
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.2	3.7	1	
			LS (low-speed main)	f <sub>MX</sub> = 8 MHz Note 2,	Normal	Square wave input		1.2	2.2	mA	
			mode Note 5	V <sub>DD</sub> = 3.0 V	operation	Resonator connection		1.2	2.3	1	
				f <sub>MX</sub> = 8 MHz Note 2,	Normal	Square wave input		1.2	2.2	1	
				V <sub>DD</sub> = 2.0 V	operation	Resonator connection		1.2	2.3		
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.9	7.1	μΑ	
			operation	TA = -40°C	operation	Resonator connection		4.9	7.1	1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.9	7.1	1	
				T <sub>A</sub> = +25°C	operation	Resonator connection		4.9	7.1	1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.1	8.8	1	
				T <sub>A</sub> = +50°C	operation	Resonator connection		5.1	8.8	1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.5	1	
				T <sub>A</sub> = +70°C	operation	Resonator connection		5.5	10.5	1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input	t	6.5	14.5	1	
				TA = +85°C	operation	Resonator connection		6.5	14.5	1	

(Notes and Remarks are listed on the next page.)

- **Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode:  $1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 8 MHz LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
  Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)
  Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

### (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT mode	HS (high-speed main)	fHOCO = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.79	3.32	mA
current Note 1	Note 2		mode Note 6	fiH = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.79	3.32	
				fHOCO = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.49	2.63	
				fiH = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.49	2.63	
				fhoco = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.62	2.57	
				fiH = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.62	2.57	
				fhoco = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.4	2.00	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.4	2.00	
				fhoco = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.38	1.49	
				fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.38	1.49	
			LS (low-speed main)	fhoco = 8 MHz,	V <sub>DD</sub> = 3.0 V		250	800	μA
			mode Note 6	fiH = 8 MHz Note 4	V <sub>DD</sub> = 2.0 V		250	800	
			LV (low-voltage main)	fhoco = 4 MHz,	V <sub>DD</sub> = 3.0 V		420	755	μA
			mode Note 6	fiH = 4 MHz Note 4	V <sub>DD</sub> = 2.0 V		420	755	
			HS (high-speed main)	f <sub>MX</sub> = 20 MHz Note 3,	Square wave input		0.30	1.63	mA
			mode Note 6	V <sub>DD</sub> = 5.0 V	Resonator connection		0.40	1.85	
				f <sub>MX</sub> = 20 MHz Note 3,	Square wave input		0.30	1.63	
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.40	1.85	
				f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.20	0.89	
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.25	0.97	
				fmx = 10 MHz Note 3,	Square wave input		0.20	0.89	
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.25	0.97	
			LS (low-speed main)	fmx = 8 MHz Note 3,	Square wave input		110	580	μΑ
			mode Note 6	V <sub>DD</sub> = 3.0 V	Resonator connection		140	630	
				f <sub>MX</sub> = 8 MHz Note 3,	Square wave input		110	580	
				V <sub>DD</sub> = 2.0 V	Resonator connection		140	630	
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.28	0.66	μΑ
			operation	T <sub>A</sub> = -40°C	Resonator connection		0.47	0.85	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.34	0.66	
				T <sub>A</sub> = +25°C	Resonator connection		0.53	0.85	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.37	2.35	
				T <sub>A</sub> = +50°C	Resonator connection		0.56	2.54	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.61	4.08	
				T <sub>A</sub> = +70°C	Resonator connection		0.80	4.27	
			fsu	fsuB = 32.768 kHz Note 5,	Square wave input		1.55	8.09	
				T <sub>A</sub> = +85°C	Resonator connection		1.74	8.28	
	IDD3	STOP mode	TA = -40°C	1	•		0.19	0.57	μA
		Note 7	T <sub>A</sub> = +25°C				0.25	0.57	
			T <sub>A</sub> = +50°C				0.33	2.26	
			TA = +70°C				0.52	3.99	1
			T <sub>A</sub> = +85°C				1.46	8.00	1

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVss0, and EVss1. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the

Note 2. During HALT instruction execution by flash memory.

peripheral modules.

- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 4.** When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V@1}$  MHz to 32 MHz

 $2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode:  $1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 8 MHz LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 4 MHz

- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

### (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.9		mA
current Note 1		mode	mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.9		•
				fHOCO = 32 MHz, fIH = 32 MHz Note 3	Basic operation	V <sub>DD</sub> = 5.0 V		2.5		•
						V <sub>DD</sub> = 3.0 V		2.5		
			HS (high-speed main) mode Note 5	fhoco = 64 MHz, fih = 32 MHz Note 3	Normal operation	V <sub>DD</sub> = 5.0 V		6.0	11.2	mA
						V <sub>DD</sub> = 3.0 V		6.0	11.2	
				fhoco = 32 MHz, fih = 32 MHz Note 3	Normal operation	V <sub>DD</sub> = 5.0 V		5.5	10.6	
						V <sub>DD</sub> = 3.0 V		5.5	10.6	
				fhoco = 48 MHz, fih = 24 MHz Note 3	Normal operation	V <sub>DD</sub> = 5.0 V		4.7	8.6	
						V <sub>DD</sub> = 3.0 V		4.7	8.6	- - - -
				fHOCO = 24 MHz, fIH = 24 MHz Note 3	Normal operation	V <sub>DD</sub> = 5.0 V		4.4	8.2	
						V <sub>DD</sub> = 3.0 V		4.4	8.2	
				fhoco = 16 MHz, fih = 16 MHz Note 3	Normal operation	V <sub>DD</sub> = 5.0 V		3.3	5.9	
						V <sub>DD</sub> = 3.0 V		3.3	5.9	
			LS (low-speed main) mode Note 5	fhoco = 8 MHz, fih = 8 MHz Note 3	Normal operation	V <sub>DD</sub> = 3.0 V		1.5	2.5	mA
						V <sub>DD</sub> = 2.0 V		1.5	2.5	
			LV (low-voltage main) mode Note 5	fHOCO = 4 MHz, fiH = 4 MHz Note 3	Normal operation	V <sub>DD</sub> = 3.0 V		1.5	2.1	mA
						V <sub>DD</sub> = 2.0 V		1.5	2.1	
			HS (high-speed main) mode Note 5	fmx = 20 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		3.7	6.8	mA
						Resonator connection		3.9	7.0	
				fmx = 20 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		3.7	6.8	
						Resonator connection		3.9	7.0	
				fmx = 10 MHz Note 2, VDD = 5.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
				f <sub>MX</sub> = 10 MHz Note 2, V <sub>DD</sub> = 3.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
			LS (low-speed main) mode Note 5	fmx = 8 MHz Note 2, VDD = 3.0 V	Normal operation	Square wave input		1.4	2.4	mA
						Resonator connection		1.4	2.5	
				f <sub>MX</sub> = 8 MHz Note 2, V <sub>DD</sub> = 2.0 V	Normal operation	Square wave input		1.4	2.4	
						Resonator connection		1.4	2.5	
			Subsystem clock	fsuB = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		5.2		μA
			operation			Resonator connection		5.2		
				fsuB = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		5.3	7.7	
						Resonator connection		5.3	7.7	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.6	
				T <sub>A</sub> = +50°C	operation	Resonator connection		5.5	10.6	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.9	13.2	
				T <sub>A</sub> = +70°C	operation	Resonator connection		6.0	13.2	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		6.8	17.5	1
				T <sub>A</sub> = +85°C	operation	Resonator connection		6.9	17.5	1

(Notes and Remarks are listed on the next page.)

- **Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7~V \le VDD \le 5.5~V@1~MHz$  to 32 MHz

 $2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode: 1.8 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
  Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)
  Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

## (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply	IDD2	HALT mode	HS (high-speed main)	fHOCO = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.93	3.32	mA
current Note 1	Note 2		mode Note 6	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.93	3.32	
				fhoco = 32 MHz, fiн = 32 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.5	2.63	
					V <sub>DD</sub> = 3.0 V		0.5	2.63	
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	V <sub>DD</sub> = 5.0 V		0.72	2.60	
					V <sub>DD</sub> = 3.0 V		0.72	2.60	
				fHOCO = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.42	2.03	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.42	2.03	
				fhoco = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.39	1.50	
				fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.39	1.50	
			LS (low-speed main)	fhoco = 8 MHz,	V <sub>DD</sub> = 3.0 V		270	800	μA
			mode Note 6	fiH = 8 MHz Note 4	V <sub>DD</sub> = 2.0 V		270	800	
			LV (low-voltage main) mode Note 6	fHOCO = 4 MHz, fIH = 4 MHz Note 4	V <sub>DD</sub> = 3.0 V		450	755	μA
					V <sub>DD</sub> = 2.0 V		450	755	
			HS (high-speed main) mode Note 6	f <sub>MX</sub> = 20 MHz Note 3, V <sub>DD</sub> = 5.0 V	Square wave input		0.31	1.69	mA
					Resonator connection		0.41	1.91	
				fmx = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.31	1.69	
					Resonator connection		0.41	1.91	
				f <sub>MX</sub> = 10 MHz Note 3, V <sub>DD</sub> = 5.0 V	Square wave input		0.21	0.94	
					Resonator connection		0.26	1.02	
				f <sub>MX</sub> = 10 MHz Note 3, V <sub>DD</sub> = 3.0 V	Square wave input		0.21	0.94	
					Resonator connection		0.26	1.02	
			LS (low-speed main) mode Note 6	f <sub>MX</sub> = 8 MHz Note 3, V <sub>DD</sub> = 3.0 V	Square wave input		110	610	μА
					Resonator connection		150	660	
				f <sub>MX</sub> = 8 MHz Note 3, V <sub>DD</sub> = 2.0 V	Square wave input		110	610	
					Resonator connection		150	660	
			Subsystem clock operation	fsuB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.31		μΑ
					Resonator connection		0.50		
				fsuB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.38	0.76	
					Resonator connection		0.57	0.95	
				fsuB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.47	3.59	
					Resonator connection		0.70	3.78	
				fsub = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.80	6.20	
					Resonator connection		1.00	6.39	
				fsuB = 32.768 kHz Note 5,	Square wave input		1.65	10.56	
				T <sub>A</sub> = +85°C	Resonator connection		1.84	10.75	L
	IDD3	STOP mode Note 7	T <sub>A</sub> = -40°C				0.19		μΑ
			T <sub>A</sub> = +25°C				0.30	0.59	
			T <sub>A</sub> = +50°C				0.41	3.42	
			TA = +70°C				0.80	6.03	1
			T <sub>A</sub> = +85°C				1.53	10.39	1

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVss0, and EVss1. The following points apply in the HS (high-speed main), LS (low-speed main), and LV (low-voltage main) modes.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 4.** When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V@1 MHz}$  to 16 MHz

LS (low-speed main) mode:  $1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 8 MHz LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 4 MHz

- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

#### (4) Peripheral Functions (Common to all products)

#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I <sub>FIL</sub> Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I <sub>WDT</sub> Notes 1, 2, 5	fi∟ = 15 kHz		0.22		μA	
A/D converter operating current	I <sub>ADC</sub> Notes 1, 6	When conversion at maximum speed	nversion at maximum Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μA
Temperature sensor operating current	ITMPS Note 1				75.0		μA
D/A converter operating current	IDAC Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating	I <sub>CMP</sub> Notes 1, 12, 13	V <sub>DD</sub> = 5.0 V,	Window mode		12.5		μA
current		Regulator output voltage = 2.1 V	Comparator high-speed mode		6.5		μΑ
			Comparator low-speed mode		1.7		μA
		V <sub>DD</sub> = 5.0 V,	Window mode		8.0		μA
		Regulator output voltage = 1.8 V	Comparator high-speed mode		4.0		μA
			Comparator low-speed mode		1.3		μA
LVD operating current	I <sub>LVD</sub> Notes 1, 7				0.08		μA
Self-programming operating current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	I <sub>BGO</sub> Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I <sub>SNOZ</sub> Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	1.44	
		Simplified SPI (CSI)/UART operation	on		0.70	0.84	
		DTC operation			3.10		

- Note 1. Current flowing to VDD.
- Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

  The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.



- Note 8. Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/G14 User's Manual.
- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

## 2.4 AC Characteristics

## (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.03125		1	μs
(minimum instruction		clock (fmain)	mode	2.4 V ≤ V <sub>DD</sub> < 2.7 V	0.0625		1	μs
execution time)		operation	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ VDD ≤ 5.5 V	0.25		1	μs
		Subsystem clo	ock (fsub) operation	1.8 V ≤ VDD ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.03125		1	μs
		programming	mode	2.4 V ≤ V <sub>DD</sub> < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.25		1	μs
External system clock	fex	$2.7 \text{ V} \leq \text{Vdd} \leq$	5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V <sub>DD</sub> ≤	2.7 V		1.0		16.0	MHz
		1.8 V ≤ V <sub>DD</sub> <	2.4 V		1.0		8.0	MHz
		1.6 V ≤ V <sub>DD</sub> < 1.8 V			1.0		4.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7 \text{ V} \leq \text{Vdd} \leq$	5.5 V		24			ns
input high-level width,	texL	2.4 V ≤ V <sub>DD</sub> ≤	2.7 V		30			ns
low-level width		1.8 V ≤ V <sub>DD</sub> <	2.4 V		60			ns
		1.6 V ≤ V <sub>DD</sub> <	1.8 V		120			ns
	texhs, texhs				13.7			μs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	ttih, ttil				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	100			ns
				1.8 V ≤ EVDD0 < 2.7 V	300			ns
				1.6 V ≤ EVDD0 < 1.8 V	500			ns
Timer RJ input high-	tтлін,	TRJIO		2.7 V ≤ EVDD0 ≤ 5.5 V	40			ns
level width, low-level	ttjil			1.8 V ≤ EVDD0 < 2.7 V	120			ns
width				1.6 V ≤ EVDD0 < 1.8 V	200			ns

Note The following conditions are required for low voltage interface when EVDD0 < VDD

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V: MIN. } 125 \text{ ns}$  $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V: MIN. } 250 \text{ ns}$ 

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel

number (n = 0 to 3))

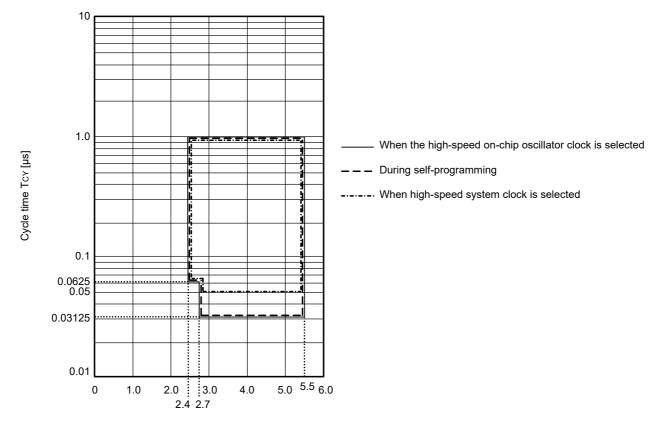
(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Items	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tтdiн, ttdil	TRDIOA0, TRDIOA1, TRDIOE TRDIOC0, TRDIOC1, TRDIO		3/fclk			ns
Timer RD forced cutoff signal	ttdsil	P130/INTP0	2MHz < fclk ≤ 32 MHz	1			μs
input low-level width			fclk ≤ 2 MHz	1/fclk + 1			
Timer RG input high-level	tтgін,	TRGIOA, TRGIOB		2.5/fclk			ns
width, low-level width	ttgil						
TO00 to TO03,	fто	HS (high-speed main) mode	$4.0~V \leq EV_{DD0} \leq 5.5~V$			16	MHz
TO10 to TO13,			2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			8	MHz
TRJIO0, TRJO0, TRDIOA0, TRDIOA1,			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
TRDIOB0, TRDIOB1,			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
TRDIOC0, TRDIOC1,		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
TRDIOD0, TRDIOD1,			1.6 V ≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
TRGIOA, TRGIOB output frequency		LV (low-voltage main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
frequency			2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			8	MHz
			1.8 V ≤ EV <sub>DD0</sub> < 2.7 V			4	MHz
			1.6 V ≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EV <sub>DD0</sub> < 1.8 V			2	MHz
Interrupt input high-level	tinth,	INTP0	$1.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	1			μs
width, low-level width	tintl	INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level	tkr	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
width			1.6 V ≤ EV <sub>DD0</sub> < 1.8 V	1			μs
RESET low-level width	trsl		•	10			μs

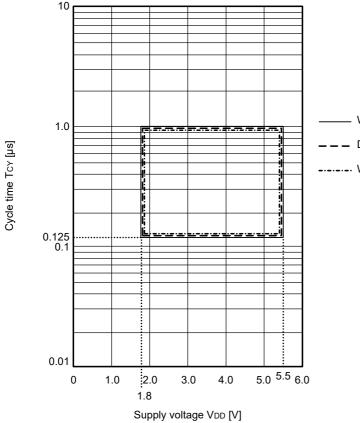
Minimum Instruction Execution Time during Main System Clock Operation

Tcy vs Vdd (HS (high-speed main) mode)



Supply voltage VDD [V]

Tcy vs Vdd (LS (low-speed main) mode)

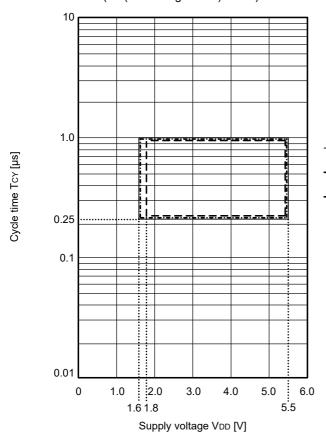


When the high-speed on-chip oscillator clock is selected

- - During self-programming

----- When high-speed system clock is selected

Tcy vs Vdd (LV (low-voltage main) mode)

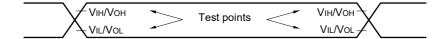


When the high-speed on-chip oscillator clock is selected

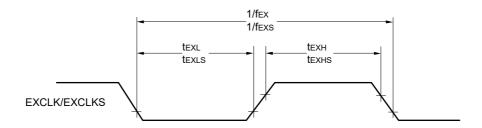
– During self-programming

----- When high-speed system clock is selected

## **AC Timing Test Points**



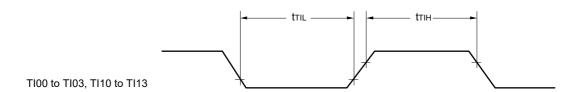
## External System Clock Timing

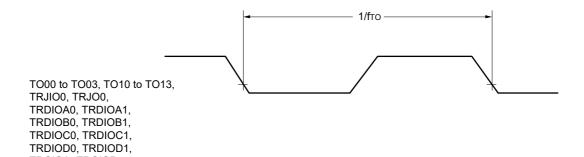


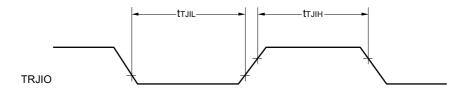
#### TI/TO Timing

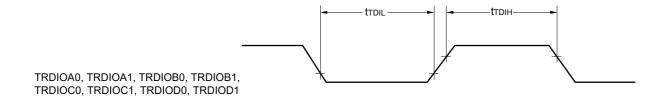
TRGIOA, TRGIOB

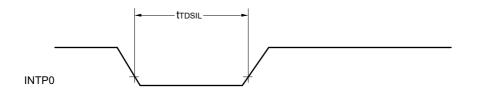
Mar 29, 2024

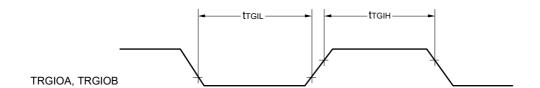




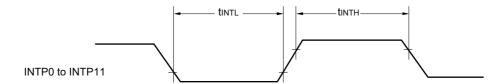




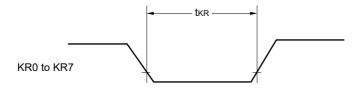




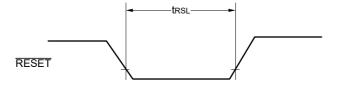
## Interrupt Request Input Timing



## Key Interrupt Input Timing

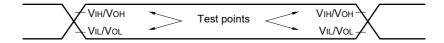


## RESET Input Timing



## 2.5 Peripheral Functions Characteristics

**AC Timing Test Points** 



## 2.5.1 Serial array unit

#### (1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

Parameter	Symbol		Conditions	, -	n-speed main) Mode		-speed main) Mode		roltage main) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		2.	4 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
Note 1			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.	8 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.	7 V ≤ EVDD0 ≤ 5.5 V		fMCK/6 Note 2		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		5.3		1.3		0.6	Mbps
		1.	6 V ≤ EVDD0 ≤ 5.5 V		_		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		_		1.3		0.6	Mbps

**Note 1.** Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \leq \text{EVDD0} < 2.7 \text{ V: MAX. } 2.6 \text{ Mbps}$ 

 $1.8 \text{ V} \leq \text{EVdd} < 2.4 \text{ V: MAX. } 1.3 \text{ Mbps}$ 

 $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V}$ : MAX. 0.6 Mbps

**Note 3.** The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:  $32 \text{ MHz} (2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V})$ 

16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)

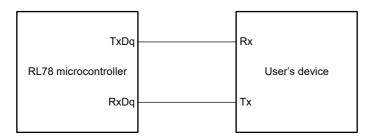
LS (low-speed main) mode: 8 MHz (1.8 V  $\leq$  VDD  $\leq$  5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V  $\leq$  VDD  $\leq$  5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

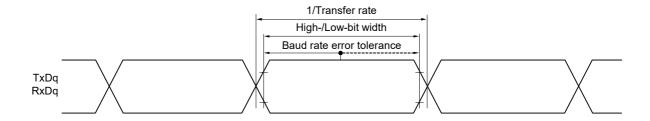
(Remarks are listed on the next page.)



## **UART** mode connection diagram (during communication at same potential)



### **UART** mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

## (2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	(	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		ltage ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	4.0 V ≤ EVDD0 ≤ 5.5 V	62.5		250		500		ns
			2.7 V ≤ EVDD0 ≤ 5.5 V	83.3		250		500		ns
SCKp high-/low-level	tкн1,	4.0 V ≤ EVDD0	V ≤ EVDD0 ≤ 5.5 V tkc			tkcy1/2 - 50		tксү1/2 - 50		ns
width	t <sub>KL1</sub>	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		tkcy1/2 - 10		tkcy1/2 - 50		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑)	tsıĸ1	4.0 V ≤ EVDD0	≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EVDD0	≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp↑) Note 2	tksi1	2.7 V ≤ EVDD0	≤ 5.5 V	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note	4		10		10		10	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
- Remark 3. fmck: Serial array unit operation clock frequency

  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

## (3) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	(	Conditions	HS (high-s main) mo	•	LS (low-speed mode	d main)	LV (low-vol main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ EVDD0 ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		1000		1000		ns
SCKp high-/low-level	tĸнı,	4.0 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 12		tkcy1/2 - 50		tkcy1/2 - 50		ns
width	t <sub>KL1</sub>	2.7 V ≤ EVDD0	2.7 V ≤ EVDD0 ≤ 5.5 V			tkcy1/2 - 50		tkcy1/2 - 50		ns
		2.4 V ≤ EVDD0	2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V			tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 50		tkcy1/2 - 50		tkcy1/2 - 50		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	tkcy1/2 - 100		tkcy1/2 - 100		tkcy1/2 - 100		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		tkcy1/2 - 100		tkcy1/2 - 100		ns
SIp setup time	tsıĸ1	4.0 V ≤ EVDD0	≤ 5.5 V	44		110		110		ns
(to SCKp↑) Note 1		2.7 V ≤ EVDD0	≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EVDD0	≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EVDD0	≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EVDD0	≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EVDD0	≤ 5.5 V	_		220		220		ns
SIp hold time	tksıı	1.7 V ≤ EVDD0	≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EVDD0	≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp output	tkso1	1.7 V ≤ EV <sub>DD0</sub> C = 30 pF Note			25		25		25	ns
Note 3		1.6 V ≤ EV <sub>DD0</sub> C = 30 pF Note			_		25		25	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))



## (4) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD0 = EVDD1 \le VDD \le 5.5 \text{ V}, VSS = EVSS0 = EVSS1 = 0 \text{ V})$  (1/2)

Parameter	Symbol	Cond	ditions	HS (high-spee mode	d main)	LS (low-speed mode	d main)	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkcy2	4.0 V ≤ EVDD0 ≤ 5.5 V	20 MHz < fmck	8/fмск		_		_		ns
time Note 5			fмcк ≤ 20 MHz	6/fмск		6/fмск		6/fмск		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	16 MHz < fmck	8/fмск		_		_		ns
			fмск ≤ 16 MHz	6/fмск		6/fмск		6/fмск		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		ĺ		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/	tkH2,	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		tkcy2/2 - 7		tkcy2/2 - 7		tkcy2/2 - 7		ns
low-level width	low-level width tkl2	2.7 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 8		tkcy2/2 - 8		tkcy2/2 - 8		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 18		tkcy2/2 - 18		tkcy2/2 - 18		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 66		tkcy2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		tkcy2/2 - 66		tkcy2/2 - 66		ns
SIp setup time	tsık2	2.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
(to SCKp↑) Note 1		1.8 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 40		1/fмск + 40		1/fмск + 40		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		1/fмск + 40		1/fмск + 40		ns
SIp hold time	tksi2	1.8 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
(from SCKp↑) Note 2		1.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 250		1/fмск + 250		1/fмск + 250		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		_		1/fмск + 250		1/fмск + 250		ns
Delay time from SCKp↓ to	tkso2	C = 30 pF Note 4	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		2/fмск + 44		2/fмск + 110		2/fмск + 110	ns
SOp output Note 3			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		2/fмск + 75		2/fмск + 110		2/fмск + 110	ns
			1.8 V ≤ EVDD0 ≤ 5.5 V		2/fмск + 100		2/fмск + 110		2/fмск + 110	ns
			1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		2/fмск + 220		2/fмск + 220		2/fмск + 220	ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		_		2/fмск + 220		2/fмск + 220	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

(Remarks are listed on the next page.)



- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fmck: Serial array unit operation clock frequency
  - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
  - n: Channel number (mn = 00 to 03, 10 to 13))

## (4) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

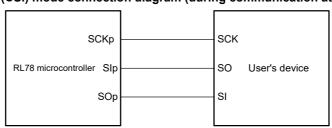
$$(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$$
 (2/2)

Parameter	Symbol		Conditions	HS (high-speed mode	d main)	LS (low-speed mode	main)	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SSI00 setup time	tssik	DAPmn = 0	2.7 V ≤ EVDD0 ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		400		400		ns
		DAPmn = 1	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		1/fмск + 400		1/fмск + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 200		1/fмск + 200		1/fмск + 200		ns
			1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		1/fмск + 400		1/fмск + 400		ns
		DAPmn = 1	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	120		120		120		ns
			1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	200		200		200		ns
			1.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	400		400		400		ns
			1.6 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	_		400		400		ns

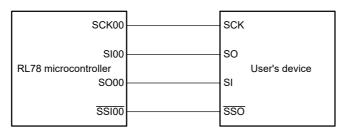
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

## Simplified SPI (CSI) mode connection diagram (during communication at same potential)



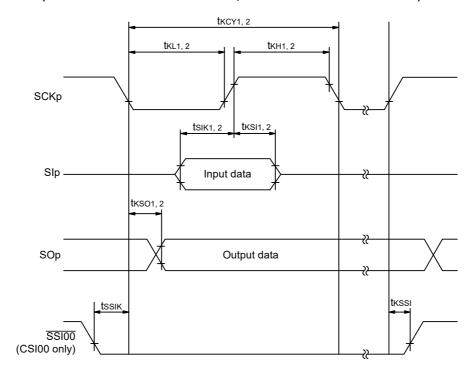
## Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



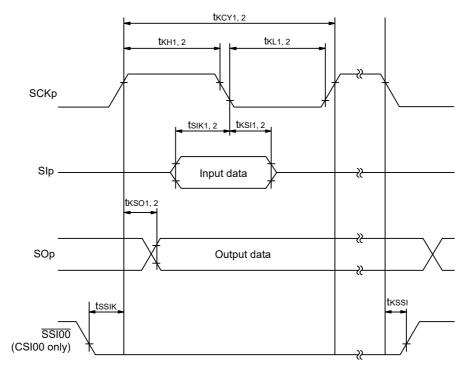
**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

## (5) During communication at same potential (simplified I<sup>2</sup>C mode)

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol	Conditions		speed main) ode	•	peed main) ode		oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		$1.8 \ V \le EV_{DD0} < 2.7 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$		300 Note 1		300 Note 1		300 Note 1	kHz
		$1.7 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$		250 Note 1		250 Note 1		250 Note 1	kHz
		$1.6 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$		_		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		1150		ns
		1.8 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ	1150		1150		1150		ns
		$1.8 \ V \leq EV_{DD0} < 2.7 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	1550		1550		1550		ns
		$1.7 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	1850		1850		1850		ns
		$1.6 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		1850		1850		ns
Hold time when SCLr = "H"	thigh	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		1150		ns
		$1.8 \ V \le EV_{DD0} \le 5.5 \ V,$ $C_b = 100 \ pF, \ R_b = 3 \ k\Omega$	1150		1150		1150		ns
		$1.8 \ V \leq EV_{DD0} < 2.7 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	1550		1550		1550		ns
		$1.7 \ V \le EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	1850		1850		1850		ns
		$1.6 \ V \leq EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

#### (5) During communication at same potential (simplified I<sup>2</sup>C mode)

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed i	main)	LS (low-speed m	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fmck + 85 Note 2		1/fмск + 145 Note 2		1/fмск + 145 Note 2		ns
		1.8 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ	1/fmck + 145 Note 2		1/fmck + 145 Note 2		1/fмск + 145 Note 2		ns
		$1.8 \ V \leq EV_{DD0} < 2.7 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	1/fmck + 230 Note 2		1/fмск + 230 Note 2		1/fмск + 230 Note 2		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1/fmck + 290 Note 2		1/fмск + 290 Note 2		1/fмск + 290 Note 2		ns
		$1.6 \ V \le EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		1/fмск + 290 Note 2		1/fмск + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	0	305	0	305	0	305	ns
		1.8 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ	0	355	0	355	0	355	ns
		$\begin{array}{c} 1.8 \; V \leq E V_{DD0} < 2.7 \; V, \\ C_b = 100 \; pF, \; R_b = 5 \; k\Omega \end{array}$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \ V \le EV_{DD0} < 1.8 \ V,$ $C_b = 100 \ pF, \ R_b = 5 \ k\Omega$	_		0	405	0	405	ns

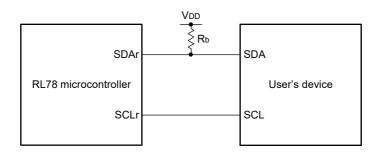
**Note 1.** The value must also be equal to or less than fmck/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

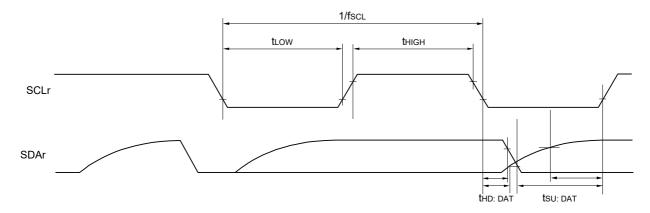
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

### Simplified I<sup>2</sup>C mode connection diagram (during communication at same potential)



### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] : \mathsf{Communication line (SDAr) pull-up \ resistance}, \ \mathsf{Cb}[F] : \mathsf{Communication line (SDAr, SCLr) load \ capacitance}$ 

**Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14), h: POM number (h = 0, 1, 3 to 5, 7, 14)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

#### (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol		Conditions	` •	-speed main) node	,	speed main) node	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		f <sub>MCK</sub> /6 Note 1		f <sub>MCK</sub> /6 Note 1		f <sub>MCK</sub> /6 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V		f <sub>MCK</sub> /6 Note 1		f <sub>MCK</sub> /6 Note 1		f <sub>MCK</sub> /6 Note 1	bps
			Theoretical value of the maximum transfer rate folk Note 4		5.3		1.3		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		fмск/6 Notes 1, 2, 3		fмск/6 Notes 1, 2		fмск/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 4		5.3		1.3		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. Use it with  $EVDD0 \ge V_b$ .

Note 3. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V: MAX. } 2.6 \text{ Mbps}$ 

 $1.8~V \leq EV_{DD0} < 2.4~V;~MAX.~1.3~Mbps$ 

**Note 4.** The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are:

HS (high-speed main) mode:  $32 \text{ MHz} (2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V})$ 

16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V  $\leq$  VDD  $\leq$  5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V  $\leq$  VDD  $\leq$  5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is

### (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol		Conditions	, ,	-speed main) node	,	-speed main) mode	,	oltage main) node	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 1.4$ k $\Omega$ , $V_b = 2.7$ V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3		Note 3		Note 3	bps	
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 2.7$ k $\Omega$ , $V_b = 2.3$ V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},  R_b = 5.5 \text{ k}\Omega, \\ V_b = 1.6 \text{ V}$		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when  $4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}$  and  $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$ 

Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]
$$\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}$$
 8 Baud rate error (theoretical value) = 
$$\frac{1}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met.

  Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- **Note 3.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V  $\leq$  EVDD0 < 4.0 V and 2.3 V  $\leq$  Vb  $\leq$  2.7 V

$$\frac{1}{\{\text{-Cb} \times \text{Rb} \times \text{ln } (1 - \frac{2.0}{\text{V}_b})\} \times 3} \text{ [bps]}$$

$$\frac{1}{\text{Transfer rate} \times 2} - \{\text{-Cb} \times \text{Rb} \times \text{ln } (1 - \frac{2.0}{\text{V}_b})\}$$

$$\times 100 \, [\%]$$
Baud rate error (theoretical value) = 
$$\frac{1}{\text{Transfer rate}} \times 2 \times \text{Number of transferred bits}$$

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with  $EVDD0 \ge V_b$ .



<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 1.8 V  $\leq$  EVDD0 < 3.3 V and 1.6 V  $\leq$  Vb  $\leq$  2.0 V

$$\frac{1}{ \left\{ -C_b \times R_b \times ln \left(1 - \frac{1.5}{V_b} \right) \right\} \times 3} \text{ [bps]}$$

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- Note 7. This value as an example is calculated when the conditions described in the "Conditions" column are met.

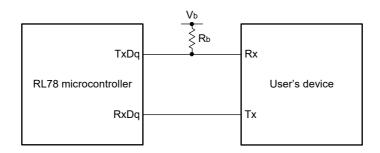
  Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

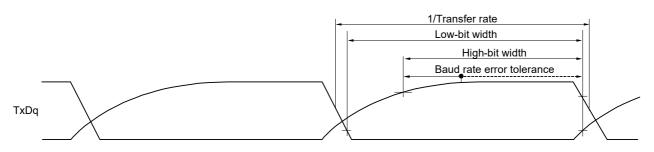


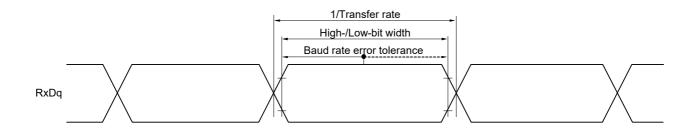
<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

### **UART** mode connection diagram (during communication at different potential)



### UART mode bit width (during communication at different potential) (reference)





- $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] \text{: } \mathsf{Communication line (TxDq) pull-up resistance,}$ 
  - Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

**Remark 4.** UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

# (7) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-speed mode	d main)	LV (low-vol main) mo	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	ns ns ns ns ns ns ns ns ns
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$\begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 20 \text{ pF}, \text{Rb} = 1.4 \text{ k}\Omega \end{aligned}$	200		1150		1150		ns
			$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 20 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	300		1150		1150		ns
SCKp high-level width	tкн1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 2$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	tксү1/2 - 50		tксү1/2 - 50		tkcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 20 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		tkcy1/2 - 120		tkcy1/2 - 120		tkcy1/2 - 120		ns
SCKp low-level width	tĸL1	$\begin{split} 4.0 \ V & \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V & \leq V_b \leq 4.0 \ V, \\ C_b & = 20 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$		tkcy1/2 - 7		tkcy1/2 - 50		tkcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 20 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		tксү1/2 - 10		tkcy1/2 - 50		tkcy1/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	tsık1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	58		479		479		ns
		$2.7 \text{ V} \leq \text{EVDD0}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 20 \text{ pF, Rb}$	2.7 V,	121		479		479		ns
SIp hold time (from SCKp↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,	10		10		10		ns
		$2.7 \text{ V} \leq \text{EVDD0}$ $2.3 \text{ V} \leq \text{V}_b \leq$ $C_b = 20 \text{ pF, Rb}$	2.7 V,	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	4.0 V,		60		60		60	ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq$ $C_{\text{b}} = 20 \text{ pF, Rb}$	2.7 V,		130		130		130	ns

(Notes, Caution, and Remarks are listed on the next page.)

(2/2)

(7) Communication at different potential (2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V 
$$\leq$$
 EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	, ,	peed main) ode	,	peed main) ode	,	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 2	tsık1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	23		110		110		ns
			33		110		110		ns
SIp hold time (from SCKp↓) Note 2	tksıı	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 20 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega $	10		10 10		ns		
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 20 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	10		10		10		ns
Delay time from SCKp↑ to SOp output Note 2	tkso1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 20 \text{ pF}, \text{R}_{\text{b}} = 1.4 \text{ k}\Omega $		10		10		10	ns
		$\begin{aligned} 2.7 & \text{ V} \leq \text{EVDD0} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b &= 20 \text{ pF, Rb} = 2.7 \text{ k}\Omega \end{aligned}$		10		10		10	ns

- **Note 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remark 1.** Rb[ $\Omega$ ]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 3, 5)
- Remark 3. fmck: Serial array unit operation clock frequency

  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
- Remark 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

# (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$  (1/3)

Parameter	Symbol		Conditions	HS (high-s main) mo		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	300		1150		1150		ns
			$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	500		1150		1150		ns
			$ \begin{aligned} &1.8 \; V \leq EV_{DDO} < 3.3 \; V, \\ &1.6 \; V \leq V_b \leq 2.0 \; V \; \text{Note}, \\ &C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{aligned} $	1150		1150		1150		ns
SCKp high-level width	tкнı	$4.0 \text{ V} \le \text{EVDD0}$ $2.7 \text{ V} \le \text{Vb} \le 4.$ $C_b = 30 \text{ pF, Rb}$	0 V,	tксү1/2 - 75		tkcy1/2 - 75		tксү1/2 - 75		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.$ $C_{\text{b}} = 30 \text{ pF, Rb}$	7 V,	tkcy1/2 - 170		tксу1/2 - 170		tксу1/2 - 170		ns
		$1.8 \text{ V} \le \text{EV}_{DD0}$ $1.6 \text{ V} \le \text{V}_{b} \le 2$ $C_{b} = 30 \text{ pF}, \text{ Rb}$	0 V Note,	tксү1/2 - 458		tkcy1/2 - 458		tkcy1/2 - 458		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \le \text{EVDD0}$ $2.7 \text{ V} \le \text{Vb} \le 4.$ $C_b = 30 \text{ pF, Rb}$	0 V,	tксү1/2 - 12		tксү1/2 <b>-</b> 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}}$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.$ $C_{\text{b}} = 30 \text{ pF, Rb}$	7 V,	tkcy1/2 - 18		tксү1/2 - 50		1150 1150 tkcy1/2 - 75 tkcy1/2 - 170 tkcy1/2 - 458		ns
		$1.8 \text{ V} \le \text{EVDD0}$ $1.6 \text{ V} \le \text{Vb} \le 2.$ $C_b = 30 \text{ pF}, \text{ Rb}$	0 V Note,	tkcy1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns

Note Use it with  $EVDD0 \ge V_b$ .

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$  (2/3)

Parameter	Symbol	Conditions		speed main) lode	,	peed main) ode	,	oltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsık1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	81		479		479		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	177		479		479		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V Note 2}, \\ &C_{\text{b}} = 30 \text{ pF, } R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	479		479		479		ns
SIp hold time (from SCKp↑) Note 1			19		19		ns		
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	19		19		19		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 30 \text{ pF},  R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	19		19		19	ode	ns
Delay time from SCKp↓ to SOp output <sup>Note 1</sup>	tkso1	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $		100		100		100	ns
		$ 2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $		195		195		195	ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} &\text{Note 2}, \\ &\text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $		483		483		483	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

Note 2. Use it with  $EV_{DD0} \ge V_b$ .

## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$  (3/3)

Parameter	Symbol	Conditions	, ,	speed main) ode	`	peed main) ode		ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) <sup>Note 1</sup>	tsıĸ1	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	44		110		110		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	44		110		110		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V Note 2}, \\ &C_{\text{b}} = 30 \text{ pF, } R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	110		110		110		ns
SIp hold time (from SCKp↓) Note 1	tksii	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{aligned} $	/b ≤ 4.0 V,		ns				
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	19		19		19		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 30 \text{ pF},  R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	19		19		19		ns
Delay time from SCKp↑ to SOp output Note 1	tkso1	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $		25		25		25	ns
		$ 2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $		25		25		25	ns
		$ \begin{aligned} &1.8 \; \text{V} \leq \text{EV}_{\text{DD0}} < 3.3 \; \text{V}, \\ &1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 2}, \\ &\text{C}_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 5.5 \; \text{k}\Omega \end{aligned} $		25		25		25	ns

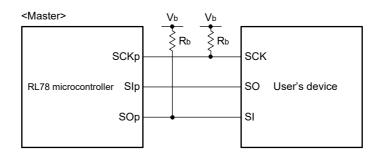
Note 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

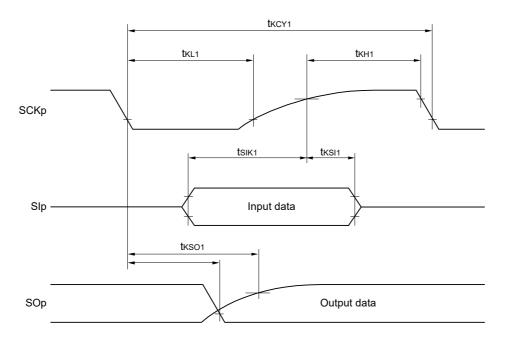
Note 2. Use it with  $EV_{DD0} \ge V_b$ .

### Simplified SPI (CSI) mode connection diagram (during communication at different potential

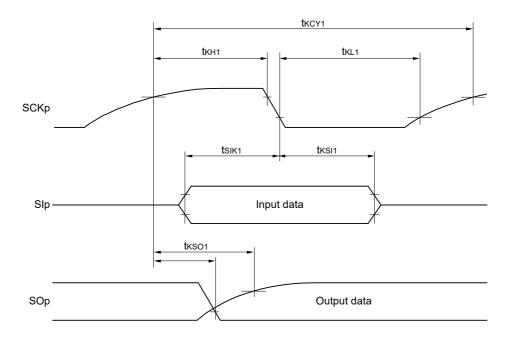


- **Remark 1.** Rb[ $\Omega$ ]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency
  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
  n: Channel number (mn = 00))
- **Remark 4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

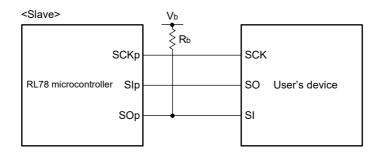
(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions			h-speed mode	,	v-speed mode	LV (low-voltage main) mode		Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	tkcy2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$	24 MHz < fmck	14/fмск		_		_		ns	
Note 1		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	12/fмск		_		_		ns	
			8 MHz < fмcк ≤ 20 MHz	10/fмск		_		_		ns	
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns	
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns	
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fmck	20/fмск		_		_			
		$2.3~V \leq V_b \leq 2.7~V$	20 MHz < fмcк ≤ 24 MHz	16/fмск		_		_		ns	
			16 MHz < fмcк ≤ 20 MHz	14/fмск		_		_		ns	
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		_		ns	
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/fмск		_		ns	
			fмcк ≤ 4 MHz	6/fмск		10/fмск		10/fмск		ns	
		1.8 V ≤ EVDD0 < 3.3 V,	24 MHz < fmck	48/fмск		_		_		ns	
		1.6 V ≤ V <sub>b</sub> ≤ 2.0 V Note 2	20 MHz < fмcк ≤ 24 MHz	36/fмск		_		_		ns ns ns ns	
		Note 2	16 MHz < fмcк ≤ 20 MHz	32/fмск		_		_			
			8 MHz < fмcк ≤ 16 MHz	26/fмск		_		_		ns	
			4 MHz < fмcк ≤ 8 MHz	16/fмск		16/fмск		_		ns	
			fмcк ≤ 4 MHz	10/fмск		10/fмск		10/fмск		ns	
SCKp high-/ low-level width	tĸH2, tĸL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	2.7 V ≤ V <sub>b</sub> ≤ 4.0 V	tkcy2/2 - 12		tkcy2/2 - 50		tксү2/2 - 50		ns	
		2.7 V ≤ EVDD0 < 4.0 V, 2	2.3 V ≤ V <sub>b</sub> ≤ 2.7 V	tkcy2/2 - 18		tkcy2/2 - 50		tксү2/2 - 50		ns	
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V Note 2}$	tkcy2/2 - 50		tkcy2/2 - 50		tксү2/2 - 50	2/fmck + 573 2/fmck + 573 2/fmck	ns	
SIp setup time (to SCKp↑) Note 3	tsık2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns		
		2.7 V ≤ EVDD0 < 4.0 V, 2	2.3 V ≤ V <sub>b</sub> ≤ 2.7 V	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns	
		1.8 V ≤ EVDD0 < 3.3 V,	$1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V Note 2}$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns	
SIp hold time (from SCKp↑) Note 4	tksı2			1/fмск + 31		1/fмск + 31		1/fмск + 31		ns	
Delay time from SCKp↓ to SOp	tĸso2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, \Omega$ Cb = 30 pF, Rb = 1.4 k $\Omega$	,		2/fмск + 120		2/fмск + 573			ns	
output Note 5		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 200 $ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$			2/fмск + 214		2/fмск + 573			ns	
		1.8 V ≤ EV <sub>DD0</sub> < 3.3 V, C <sub>b</sub> = 30 pF, R <sub>V</sub> = 5.5 kΩ	$1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V}^{\text{Note 2}},$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns	

 $(\textbf{Notes},\,\textbf{Caution},\, \text{and}\,\, \textbf{Remarks} \text{ are listed on the next page.})$ 

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with  $EVDD0 \ge V_b$ .
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

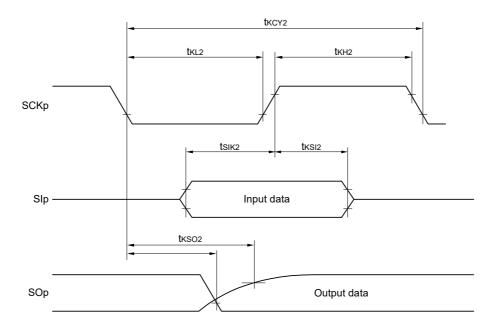
## Simplified SPI (CSI) mode connection diagram (during communication at different potential)



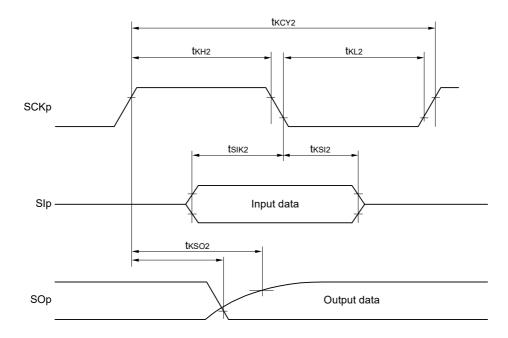
- **Remark 1.** R<sub>b</sub>[Ω]: Communication line (SOp) pull-up resistance, C<sub>b</sub>[F]: Communication line (SOp) load capacitance, V<sub>b</sub>[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

## (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode)

(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol	Conditions		speed main) node	,	speed main) node	LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	<b>.</b>
SCLr clock frequency	fscL	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $		400 Note 1		300 Note 1		300 Note 1	kHz
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega \end{split}$		300 Note 1 300 Note 1		300 Note 1	kHz		
Hold time when SCLr = "L"	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		1550		ns				
		$2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$	475		1550		1550		ns
		$2.7 \text{ V} \le V_b \le 4.0 \text{ V},$	1150		1550		1550		ns
		$2.3 \text{ V} \le V_b \le 2.7 \text{ V},$	1150		1550		1550		ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V \ ^{Note \ 2}, \\ C_b &= 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	245		610		610		ns
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $	200		610		610		ns
		$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned} $	675		610		610		ns
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega $	600		610		610		ns
		$\begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega \end{aligned}$	610		610		610		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

## (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode)

(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed r mode	main)	LS (low-speed m	nain)	LV (low-voltage r mode	main)	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} 2.7 & \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1/fmck + 135 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF},  R_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} &\text{Note 2}, \\ &C_{\text{b}} = 100 \text{ pF}, &R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	1/fmck + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		ns
Data hold time (transmission)	thd:dat	$ 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $	0	305	0	305	0	305	ns
		$ \begin{aligned} 2.7 & \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	0	305	0	305	0	305	ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}\text{DD0} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}\text{b} \leq 4.0 \text{ V}, \\ &\text{C}\text{b} = 100 \text{ pF}, \text{ Rb} = 2.8 \text{ k}\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$ \begin{aligned} &2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ &2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ Rb} = 2.7 \text{ k}\Omega \end{aligned} $	0	355	0	355	0	355	ns
		$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} &\text{Note 2}, \\ &C_{\text{b}} = 100 \text{ pF},  R_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned} $	0	405	0	405	0	405	ns

**Note 1.** The value must also be equal to or less than fMCK/4.

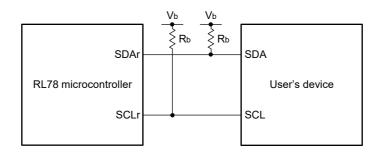
Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

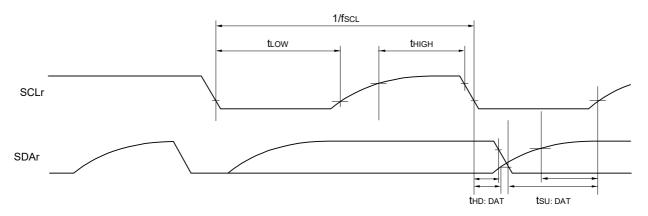
Note 2. Use it with  $EVDD0 \ge V_b$ .

**Note 3.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

## Simplified I<sup>2</sup>C mode connection diagram (during communication at different potential)



## Simplified I<sup>2</sup>C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[ $\Omega$ ]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency

  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

  n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

# 2.5.2 Serial interface IICA

# (1) I<sup>2</sup>C standard mode

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol	С	conditions	HS (high-sp	peed main) ode	, ,	peed main) ode		ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	2.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
frequency		fclk ≥ 1 MHz	1.8 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD0 ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	0	100	0	100	kHz
Setup time of	tsu: sta	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
restart condition		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V		-	_	4.7		4.7		μs
Hold time Note 1	thd: STA	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	-	_	4.0		4.0		μs
Hold time when	tLow	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	-	_	4.7		4.7		μs
Hold time when	thigh	2.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ \$	5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ \$	5.5 V	-	_	4.0		4.0		μs

 $(\textbf{Notes},\,\textbf{Caution},\, \text{and}\,\, \textbf{Remark}$  are listed on the next page.)

## (1) I<sup>2</sup>C standard mode

## (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions	` `	peed main) ode	' '	peed main) ode	`	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	1
Data setup time (reception)	tsu: DAT	2.7 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V	250		250		250		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	250		250		ns
Data hold time (transmission)	thd: dat	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
Note 2		1.8 V ≤ EVDD0 ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	0	3.45	0	3.45	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	4.0		4.0		4.0		μs
		1.8 V ≤ EVDD0 ≤ 5.5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	4.0		4.0		μs
Bus-free time	tBUF	2.7 V ≤ EVDD0 ≤ 5.5 V	4.7		4.7		4.7		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EVDD0 ≤ 5.5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EVDD0 ≤ 5.5 V	-	_	4.7		4.7		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b$  = 400 pF,  $R_b$  = 2.7  $k\Omega$ 

## (2) I2C fast mode

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	C	Conditions	, ,	h-speed mode	,	v-speed ) mode	LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	2.7 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
		fclk ≥ 3.5 MHz	1.8 V ≤ EVDD0 ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu: sta	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
Hold time Note 1	thd: STA	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	1.3		1.3		1.3		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	thigh	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
Data setup time (reception)	tsu: dat	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	100		100		100		ns
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	100		100		100		ns
Data hold time (transmission)	thd: dat	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0	0.9	0	0.9	0	0.9	μs
Note 2		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	0.6		0.6		0.6		μs
Bus-free time	<b>t</b> BUF	2.7 V ≤ EV <sub>DD0</sub> ≤	5.5 V	1.3		1.3		1.3		μs
		1.8 V ≤ EV <sub>DD0</sub> ≤	5.5 V	1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode:  $C_b = 320 \text{ pF}$ ,  $R_b = 1.1 \text{ k}\Omega$ 

## (3) I<sup>2</sup>C fast mode plus

## (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Co	onditions		h-speed mode	•	/-speed mode	,	-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fcLk ≥ 10 MHz	·		1000	_		_		kHz
Setup time of restart condition	tsu: sta	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V			_		_		μs
Hold time Note 1	thd: STA	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V			_		_		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.	5 V	0.5		_		_		μs
Hold time when SCLA0 = "H"	thigh	2.7 V ≤ EVDD0 ≤ 5.	5 V	0.26		_		-	_	μs
Data setup time (reception)	tsu: dat	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.	5 V	50		_		_		ns
Data hold time (transmission) Note 2	thd: dat	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V		0.45	-	-	-	-	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V			_		_		μs
Bus-free time	<b>t</b> BUF	2.7 V ≤ EVDD0 ≤ 5.	2.7 V ≤ EVDD0 ≤ 5.5 V			_		-		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

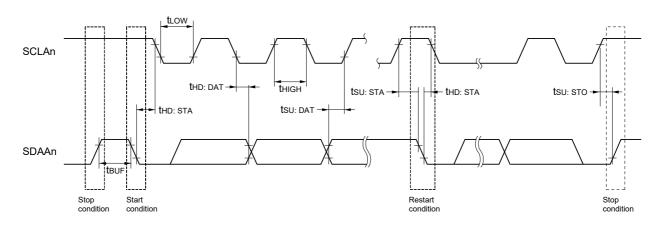
Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus:  $C_b$  = 120 pF,  $R_b$  = 1.1 k $\Omega$ 

#### **IICA** serial transfer timing



Remark n = 0, 1

# 2.6 Analog Characteristics

## 2.6.1 A/D converter characteristics

#### Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V <sub>DD</sub> Reference voltage (-) = Vss	Reference voltage (+) = V <sub>BGR</sub> Reference voltage (-)= AV <sub>REFM</sub>
ANI0 to ANI14	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI20	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1).		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
		AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 to ANI14	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V	17		39	μs
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	57		95	μs
		10-bit resolution	$3.6 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	2.375		39	μs
		Target pin: Internal reference voltage,	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.5625		39	μs
		and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
		AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	Vain	ANI2 to ANI14	•	0		AVREFP	V
		Internal reference voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed m	\	BGR Note	5	V	
		Temperature sensor output voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed m	VT	MPS25 Not	e 5	V	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AVREFP = VDD.

Note 4. Values when the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI20

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, 1.6 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target ANI pin: ANI16 to ANI20	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EV <sub>DD0</sub> ≤ AV <sub>REFP</sub> = V <sub>DD</sub> Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±6.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.0	LSB
		EVDD0 ≤ AVREFP = VDD Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI20		0		AVREFP and EVDD0	V

- Note 1. Excludes quantization error (±1/2 LSB).
- Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **Note 3.** When  $EVDD0 \le AVREFP \le VDD$ , the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

**Note 4.** When AVREFP < EVDD0 ≤ VDD, the MAX. values are as follows.

Overall error: Add  $\pm 4.0$  LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add  $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add  $\pm 2.0$  LSB to the MAX. value when AVREFP = VDD.

Note 5. When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.1875		39	μs
			1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V	17		39	μs
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	57		95	μs
		10-bit resolution	$3.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
		(HS (high-speed main) mode)	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V			±2.0	LSB
Note 1			1.6 V ≤ V <sub>DD</sub> ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		VDD	V
		ANI16 to ANI20		0		EV <sub>DD0</sub>	V
		Internal reference voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed main) mode)			V <sub>BGR</sub> Note 4		
		Temperature sensor output voltage (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high-speed main) r	V <sub>TMPS25</sub> Note 4			V	

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When the conversion time is set to 57  $\mu$ s (min.) and 95  $\mu$ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +85°C, 2.4 V  $\leq$  VDD  $\leq$  5.5 V, 1.6 V  $\leq$  EVDD = EVDD1  $\leq$  VDD, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4, HS (high-speed main) mode)

Parameter	Symbol	Со	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±1.0	LSB
Analog input voltage	VAIN			0		V <sub>BGR</sub> Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

**Note 4.** When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add  $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add  $\pm 0.5$  LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add  $\pm 0.2$  LSB to the MAX. value when reference voltage (-) = AVREFM.

# 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(TA = -40 to +85°C, 2.4 V  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

# 2.6.3 D/A converter characteristics

# (TA = -40 to +85°C, 1.6 V $\leq$ EVss0 = EVss1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Coi	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ VDD ≤ 5.5 V			±2.5	LSB
		Rload = 8 MΩ	1.8 V ≤ VDD ≤ 5.5 V			±2.5	LSB
Settling time	tset	Cload = 20 pF	2.7 V ≤ VDD ≤ 5.5 V			3	μs
			1.6 V ≤ V <sub>DD</sub> < 2.7 V			6	μs

# 2.6.4 Comparator

(TA = -40 to +85°C, 1.6 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Col	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		EVDD0 - 1.4	V
	lvcmp			-0.3		EV <sub>DD0</sub> + 0.3	V
Output delay	td	V <sub>DD</sub> = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0	5.0	μs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode	e, window mode		0.76 VDD		V
Low-electric-potential reference voltage	VTW-	Comparator high-speed mode	e, window mode		0.24 VDD		V
Operation stabilization wait time	tсмр			100			μs
Internal reference voltage Note	VBGR	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ HS (h}$	nigh-speed main) mode	1.38	1.45	1.50	V

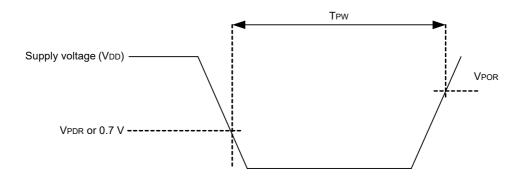
Note Not usable in LS (low-speed main) mode, LV (low-voltage main) mode, sub-clock operation, or STOP mode.

# 2.6.5 POR circuit characteristics

## $(TA = -40 \text{ to } +85^{\circ}C, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.47	1.51	1.55	V
	VPDR	Voltage threshold on VDD falling Note 1	1.46	1.50	1.54	V
Minimum pulse width Note 2	Tpw		300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



# 2.6.6 LVD circuit characteristics

# (1) Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage	Supply voltage level	VLVD0	Rising edge	3.98	4.06	4.14	V
detection			Falling edge	3.90	3.98	4.06	V
threshold		VLVD1	Rising edge	3.68	3.75	3.82	V
			Falling edge	3.60	3.67	3.74	V
		VLVD2	Rising edge	3.07	3.13	3.19	V
			Falling edge	3.00	3.06	3.12	V
		VLVD3	Rising edge	2.96	3.02	3.08	V
			Falling edge	2.90	2.96	3.02	V
		VLVD4	Rising edge	2.86	2.92	2.97	V
			Falling edge	2.80	2.86	2.91	V
		VLVD5	Rising edge	2.76	2.81	2.87	V
			Falling edge	2.70	2.75	2.81	V
		VLVD6	Rising edge	2.66	2.71	2.76	V
			Falling edge	2.60	2.65	2.70	V
		VLVD7	Rising edge	2.56	2.61	2.66	V
			Falling edge	2.50	2.55	2.60	V
		VLVD8	Rising edge	2.45	2.50	2.55	V
			Falling edge	2.40	2.45	2.50	V
		VLVD9	Rising edge	2.05	2.09	2.13	V
			Falling edge	2.00	2.04	2.08	V
		VLVD10	Rising edge	1.94	1.98	2.02	V
			Falling edge	1.90	1.94	1.98	V
		VLVD11	Rising edge	1.84	1.88	1.91	V
			Falling edge	1.80	1.84	1.87	V
		VLVD12	Rising edge	1.74	1.77	1.81	V
			Falling edge	1.70	1.73	1.77	V
		VLVD13	Rising edge	1.64	1.67	1.70	V
			Falling edge	1.60	1.63	1.66	V
Minimum puls	se width	tLW		300			μs
Detection del	ay time					300	μs

## (2) Interrupt & Reset Mode

(Ta = -40 to +85°C, VPDR  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	itions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDA0	VPOC2,	VPOC1, VPOC0 = 0, 0, 0, fal	ling reset voltage	1.60	1.63	1.66	V
threshold	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC2,	VPOC1, VPOC0 = 0, 0, 1, fal	ling reset voltage	1.80	1.84	1.87	V
	VLVDB1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC2,	VPOC1, VPOC0 = 0, 1, 0, fal	ling reset voltage	2.40	2.45	2.50	V
	VLVDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC2,	VPOC1, VPOC0 = 0, 1, 1, fal	ling reset voltage	2.70	2.75	2.81	V
	VLVDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

# 2.6.7 Power supply voltage rising slope characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

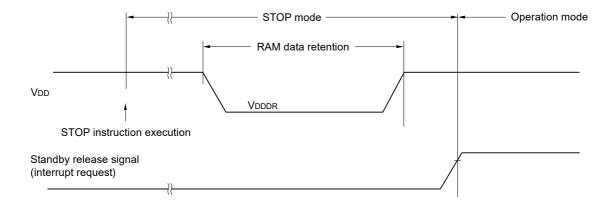
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

## 2.7 RAM Data Retention Characteristics

## $(TA = -40 \text{ to } +85^{\circ}\text{C}, Vss = 0V)$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		5.5	V

**Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



# 2.8 Flash Memory Programming Characteristics

#### $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

# 2.9 Dedicated Flash Memory Programmer Communication (UART)

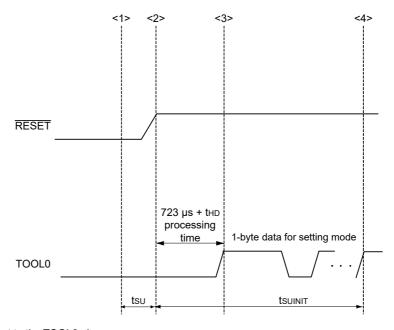
# (TA = -40 to +85°C, 1.8 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

# 2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

**Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

# 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS TA = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications  $T_A = -40$  to  $+105^{\circ}$ C R5F104xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
- Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.
- Caution 4. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C.

  Derating is the systematic reduction of load for the sake of improved reliability.
- Remark When RL78/G14 is used in the range of T<sub>A</sub> = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (T<sub>A</sub> = -40 to +85°C)**.

Operation of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differs from that of products rated "A: Consumer applications" and "D: Industrial applications" in the ways listed below.

Parameter	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	Ta = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 32 MHz	2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz
	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 16 MHz	2.4 V ≤ VDD ≤ 5.5 V@1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V ≤ V <sub>DD</sub> ≤ 5.5 V@1 MHz to 8 MHz	
	LV (low-voltage main) mode:	
	1.6 V ≤ VDD ≤ 5.5 V@1 MHz to 4 MHz	
High-speed on-chip oscillator	1.8 V ≤ VDD ≤ 5.5 V:	2.4 V ≤ VDD ≤ 5.5 V:
clock accuracy	±1.0% @ TA = -20 to +85°C	±2.0% @ TA = +85 to +105°C
	±1.5% @ TA = -40 to -20°C	±1.0% @ TA = -20 to +85°C
	1.6 V ≤ VDD < 1.8 V:	±1.5% @ TA = -40 to -20°C
	±5.0% @ TA = -20 to +85°C	
	±5.5% @ TA = -40 to -20°C	
Serial array unit	UART	UART
	Simplified SPI (CSI): fcLk/2 (16 Mbps supported),	Simplified SPI (CSI): fclk/4
	fclk/4	Simplified I <sup>2</sup> C communication
	Simplified I <sup>2</sup> C communication	
IICA	Standard mode	Standard mode
	Fast mode	Fast mode
	Fast mode plus	
Voltage detector	• Rising: 1.67 V to 4.06 V (14 stages)	• Rising: 2.61 V to 4.06 V (8 stages)
	• Falling: 1.63 V to 3.98 V (14 stages)	• Falling: 2.55 V to 3.98 V (8 stages)

**Remark** The electrical characteristics of products rated "G: Industrial applications (TA = -40 to + 105°C)" at ambient operating temperatures above 85°C differ from those of products rated "A: Consumer applications" and "D: Industrial applications". For details, refer to **3.1** to **3.10**.

# 3.1 Absolute Maximum Ratings

## **Absolute Maximum Ratings**

(1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVss0 = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V <sub>DD</sub> +0.3 Note 1	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	and -0.3 to V <sub>DD</sub> +0.3 Note 2	
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	VI3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V <sub>DD</sub> +0.3 Note 2	V
Output voltage	Vo1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-0.3 to EVDD0 +0.3 and -0.3 to VDD +0.3 Note 2	V
	VO2	P20 to P27, P150 to P156	-0.3 to V <sub>DD</sub> +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI20	-0.3 to EV <sub>DD0</sub> +0.3 and -0.3 to AV <sub>REF</sub> (+) +0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI14	-0.3 to VDD +0.3 and -0.3 to AVREF(+) +0.3 Notes 2,3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1  $\mu$ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- **Note 3.** Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

## **Absolute Maximum Ratings**

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
		-170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low lou	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
		170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	lo <sub>L2</sub>	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	Та	In normal o	peration mode	-40 to +105	°C
temperature		In flash me	mory programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

## 3.2 Oscillator Characteristics

# 3.2.1 X1, XT1 characteristics

#### $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	2.4 V ≤ V <sub>DD</sub> < 2.7 V	1.0		16.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user.

Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G14 User's Manual.

# 3.2.2 On-chip oscillator characteristics

## $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Co	onditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator clock frequency		-20 to +85°C	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	-1.0		+1.0	%
accuracy		-40 to -20°C	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	-1.5		+1.5	%
		+85 to +105°C	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

**Note 1.** High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

## 3.3 DC Characteristics

## 3.3.1 Pin characteristics

 $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le EVDD0 = EVDD1 \le VDD \le 5.5 \text{ V}, VSS = EVSS0 = EVSS1 = 0 \text{ V})$ 

(1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	2.4 V ≤ EVDD0 ≤ 5.5 V			-3.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$			-30.0	mA
		P102, P120, P130, P140 to P145	2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			-10.0	mA
		(When duty ≤ 70% Note 3)	2.4 V ≤ EV <sub>DD0</sub> < 2.7 V			-5.0	mA
		P30, P31, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EVDD0 < 4.0 V			-19.0	mA
		P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	2.4 V ≤ EVDD0 ≤ 5.5 V			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	2.4 V ≤ VDD ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EVDD0, EVDD1, VDD pins to an output pin.

**Note 3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH × 0.7)/(n × 0.01) <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins =  $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$  mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.

Note 2. Do not exceed the total current value.

## (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

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Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	loL1	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P40 to P47,	4.0 V ≤ EVDD0 ≤ 5.5 V			40.0	mA
		(When duty ≤ 70% Note 3) 2	2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			15.0	mA
			2.4 V ≤ EVDD0 < 2.7 V			9.0	mA
		Total of P05, P06, P10 to P17,	4.0 V ≤ EVDD0 ≤ 5.5 V			40.0	mA
		P30, P31, P50 to P57, P60 to P67, P70 to P77,	2.7 V ≤ EV <sub>DD0</sub> < 4.0 V			35.0	mA
		P80 to P87, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EVDD0 < 2.7 V			20.0	mA
	Total of all pins (When duty ≤ 7	Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )				80.0	mA
		Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% <sup>Note 3</sup> )	2.4 V ≤ VDD ≤ 5.5 V			5.0	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1, and Vss pins.
- **Note 2.** Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor  $\leq 70\%$ .

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

Total output current of pins = (IoL × 0.7)/(n × 0.01)
 <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins =  $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$ 

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.

A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

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-							-
Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVDD0		EV <sub>DD0</sub>	V
	VIH2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2		EV <sub>DD0</sub>	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV <sub>DD0</sub>	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5		EV <sub>DD0</sub>	V
	VIH3	P20 to P27, P150 to P156	0.7 Vdd		VDD	V	
	VIH4	P60 to P63	0.7 EVDD0		6.0	V	
	VIH5	P121 to P124, P137, EXCLK, EX	0.8 Vdd		VDD	V	
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0		0.2 EVDD0	V
	VIL2	P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55,	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	0		0.32	V
	VIL3	P20 to P27, P150 to P156	•	0		0.3 Vdd	V
	VIL4	P60 to P63		0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EX	CLKS, RESET	0		0.2 VDD	V

Caution The maximum value of ViH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(4/5)

Items	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57,	4.0 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -3.0 mA	EVDD0 - 0.7			V
		P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110,	2.7 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -2.0 mA	EVDD0 - 0.6			V
		P111, P120, P130, P140 to P147	2.4 V ≤ EVDD0 ≤ 5.5 V, IOH1 = -1.5 mA	EVDD0 - 0.5			V
	VOH2	P20 to P27, P150 to P156	2.4 V ≤ VDD ≤ 5.5 V, IOH2 = -100 μA	VDD - 0.5			V
Output voltage, low VoL1		P31, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{EVDD0} \le 5.5 \text{ V},$ IOL1 = 8.5  mA			0.7	V
		P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	2.7 V ≤ EVDD0 ≤ 5.5 V, lol1 = 3.0 mA			0.6	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, lol1 = 1.5 mA			0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, IOL1 = 0.6 mA			0.4	V
	VOL2	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V},$ $\text{Iol2} = 400  \mu\text{A}$			0.4	V
	Vol3	P60 to P63	4.0 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 15.0 mA			2.0	V
			4.0 V ≤ EVDD0 ≤ 5.5 V, lol3 = 5.0 mA			0.4	V
			2.7 V ≤ EVDD0 ≤ 5.5 V, IOL3 = 3.0 mA			0.4	V
			2.4 V ≤ EVDD0 ≤ 5.5 V, lol3 = 2.0 mA			0.4	V

Caution P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, P142 to P144 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(5/5)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVDD0				1	μА
	ILIH2	P20 to P27, P137, P150 to P156, RESET	VI = VDD				1	μA
	Ішнз	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	ILIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Vi = EVsso				-1	μА
	ILIL2	P20 to P27, P137, P150 to P156, RESET	VI = VSS				-1	μA
	ILIL3	P121 to P124 (X1, X2, EXCLK, XT1, XT2, EXCLKS)	VI = VSS	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pull-up resistance	Ru	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	VI = EVssc	o, In input port	10	20	100	kΩ

# 3.3.2 Supply current characteristics

# (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-speed main)	fhoco = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.4		mA
current Note 1		mode	mode Note 5	fiH = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.4		
Note 1				fhoco = 32 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.1		
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.1		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.1	9.3	mA
			mode Note 5	fiн = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.1	9.3	
				fHOCO = 32 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.8	8.7	
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.8	8.7	
				fносо = 48 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.0	7.3	
				fiH = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.0	7.3	
				fhoco = 24 MHz,	Normal	V <sub>DD</sub> = 5.0 V		3.8	6.7	
				fiH = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		3.8	6.7	
				fHOCO = 16 MHz,	Normal	V <sub>DD</sub> = 5.0 V		2.8	4.9	
				fih = 16 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.8	4.9	
		HS (high-speed main)	fmx = 20 MHz Note 2,	Normal	Square wave input		3.3	5.7	mA	
		mode Note 5	V <sub>DD</sub> = 5.0 V	operation	Resonator connection		3.4	5.8		
				,	Normal	Square wave input		3.3	5.7	
					operation	Resonator connection		3.4	5.8	
				fmx = 10 MHz Note 2, VDD = 5.0 V	Normal	Square wave input		2.0	3.4	
					operation	Resonator connection		2.1	3.5	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.4	
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.1	3.5	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μΑ
			operation	T <sub>A</sub> = -40°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	
				T <sub>A</sub> = +25°C	operation	Resonator connection		4.7	6.1	
				fsuB = 32.768 kHz Note 4		Square wave input		4.8	6.7	
			T <sub>A</sub> = +50°C	operation	Resonator connection		4.8	6.7		
			fsuB = 32.768 kHz Note 4		Square wave input		4.8	7.5		
			T <sub>A</sub> = +70°C	operation	Resonator connection		4.8	7.5		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9		
		T <sub>A</sub> = +85°C	operation	Resonator connection		5.4	8.9			
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		7.2	21.0		
			T <sub>A</sub> = +105°C	operation	Resonator connection		7.3	21.1		

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The following points apply in the HS (high-speed main) mode.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

# (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply current	IDD2	HALT mode	HS (high-speed main)	fhoco = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.80	4.36	mA
Note 1	Note 2		mode Note 6	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.80	4.36	
				fносо = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.49	3.67	
				fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.49	3.67	
				fносо = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.62	3.42	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.62	3.42	
				fHOCO = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.4	2.85	
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.4	2.85	
				fHOCO = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.37	2.08	
				fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.37	2.08	
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.28	2.45	mA
			mode Note 6	V <sub>DD</sub> = 5.0 V	Resonator connection		0.40	2.57	
				fmx = 20 MHz Note 3,	Square wave input		0.28	2.45	
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.40	2.57	
				f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.19	1.28	
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.25	1.36	
			fmx = 10 MHz Note 3,	Square wave input		0.19	1.28		
			V <sub>DD</sub> = 3.0 V	Resonator connection		0.25	1.36		
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.25	0.57	μA
			operation	TA = -40°C	Resonator connection		0.44	0.76	
				,	Square wave input		0.30	0.57	
				TA = +25°C	Resonator connection		0.49	0.76	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.36	1.17	
				TA = +50°C	Resonator connection		0.59	1.36	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.49	1.97	
				TA = +70°C	Resonator connection		0.72	2.16	
				fsuB = 32.768 kHz Note 5,	Square wave input		0.97	3.37	
				T <sub>A</sub> = +85°C	Resonator connection		1.16	3.56	
				fsuB = 32.768 kHz Note 5,	Square wave input		3.20	17.10	
				T <sub>A</sub> = +105°C	Resonator connection		3.40	17.50	
		STOP mode	T <sub>A</sub> = -40°C	•	•		0.18	0.51	μΑ
		Note 7	T <sub>A</sub> = +25°C				0.24	0.51	
			T <sub>A</sub> = +50°C				0.29	1.10	
			T <sub>A</sub> = +70°C				0.41	1.90	
			T <sub>A</sub> = +85°C				0.90	3.30	
		TA = +105°C					3.10	17.00	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The following points apply in the HS (high-speed main) mode.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.

In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. During HALT instruction execution by flash memory.
- Note 3. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} \text{@} 1 \text{ MHz}$  to 32 MHz
  - $2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V} @1 \text{ MHz to } 16 \text{ MHz}$
- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operating	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.6		mA
current		mode	mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.6		
Note 1				fHOCO = 32 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.3		
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.3		
			HS (high-speed main)	fHOCO = 64 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.4	10.9	mA
			mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.4	10.9	
				fHOCO = 32 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.0	10.3	İ
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.0	10.3	
				fHOCO = 48 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.2	8.2	
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.2	8.2	
				fHOCO = 24 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.0	7.8	
			fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.0	7.8	İ	
		fHOCO = 16 MHz,	Normal	V <sub>DD</sub> = 5.0 V		3.0	5.6			
		fih = 16 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		3.0	5.6			
	HS (high-speed main)	f <sub>MX</sub> = 20 MHz Note 2,	Normal	Square wave input		3.4	6.6	m		
	mode Note 5	V <sub>DD</sub> = 5.0 V	operation	Resonator connection		3.6	6.7			
			fmx = 20 MHz Note 2,	Normal	Square wave input		3.4	6.6		
			 	V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.6	6.7	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.1	3.9	
				V <sub>DD</sub> = 5.0 V f <sub>MX</sub> = 10 MHz Note 2,	operation	Resonator connection		2.2	4.0	
					Normal	Square wave input		2.1	3.9	
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.2	4.0	
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.9	7.1	μ
			operation	T <sub>A</sub> = -40°C	operation	Resonator connection		4.9	7.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		4.9	7.1	
				T <sub>A</sub> = +25°C	operation	Resonator connection		4.9	7.1	
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.1	8.8	
			T <sub>A</sub> = +50°C	operation	Resonator connection		5.1	8.8		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.5		
		T <sub>A</sub> = +70°C	operation	Resonator connection		5.5	10.5			
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		6.5	14.5	Ì	
		T <sub>A</sub> = +85°C	operation	Resonator connection		6.5	14.5			
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		13.0	58.0	1	
			T <sub>A</sub> = +105°C	operation	Resonator connection		13.0	58.0	1	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main) mode.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.
  - In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V@1 MHz}$  to 16 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit		
Supply	IDD2	HALT mode	HS (high-speed main)	fhoco = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.79	4.86	mA		
current Note 1	Note 2		mode Note 6	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.79	4.86			
				fHOCO = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.49	4.17			
				fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.49	4.17			
				fhoco = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.62	3.82			
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.62	3.82			
				fhoco = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.4	3.25			
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.4	3.25			
				fhoco = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.38	2.28			
				fih = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.38	2.28			
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.30	2.65	mA		
			mode Note 6	V <sub>DD</sub> = 5.0 V	Resonator connection		0.40	2.77			
				fmx = 20 MHz Note 3,	Square wave input		0.30	2.65			
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.40	2.77			
				f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.20	1.36			
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.25	1.46			
				fmx = 10 MHz Note 3,	Square wave input		0.20	1.36			
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.25	1.46			
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.28	0.66	μΑ		
			operation	operation	operation	TA = -40°C	Resonator connection		0.47	0.85	
				fsub = 32.768 kHz Note 5,	Square wave input		0.34	0.66			
				T <sub>A</sub> = +25°C	Resonator connection		0.53	0.85			
				fsuB = 32.768 kHz Note 5,	Square wave input		0.37	2.35			
				T <sub>A</sub> = +50°C	Resonator connection		0.56	2.54			
				fsuB = 32.768 kHz Note 5,	Square wave input		0.61	4.08			
				T <sub>A</sub> = +70°C	Resonator connection		0.80	4.27			
				fsuB = 32.768 kHz Note 5,	Square wave input		1.55	8.09			
				T <sub>A</sub> = +85°C	Resonator connection		1.74	8.28			
				fsuB = 32.768 kHz Note 5,	Square wave input		6.00	51.00			
				T <sub>A</sub> = +105°C	Resonator connection		6.00	51.00			
	IDD3	STOP mode	T <sub>A</sub> = -40°C				0.19	0.57	μΑ		
		Note 7					0.25	0.57			
							0.33	2.26			
							0.52	3.99			
							1.46	8.00			
			T <sub>A</sub> = +105°C				5.50	50.00	1		

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main) mode.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. During HALT instruction execution by flash memory.
- **Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- **Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- **Note 6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 32 MHz  $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 16 MHz
- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

# (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Uni
Supply	IDD1	Operating	HS (high-speed main)	fHOCO = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.9		mA
current		mode	mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.9		
Note 1				fHOCO = 32 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.5		
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		2.5		1
			HS (high-speed main)	fhoco = 64 MHz,	Normal	V <sub>DD</sub> = 5.0 V		6.0	11.2	m/
			mode Note 5	fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		6.0	11.2	1
				fHOCO = 32 MHz,	Normal	V <sub>DD</sub> = 5.0 V		5.5	10.6	
				fih = 32 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		5.5	10.6	-
				fhoco = 48 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.7	8.6	
				fih = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.7	8.6	-
				fhoco = 24 MHz,	Normal	V <sub>DD</sub> = 5.0 V		4.4	8.2	1
		f <sub>IH</sub> = 24 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		4.4	8.2			
		fHOCO = 16 MHz,	Normal	V <sub>DD</sub> = 5.0 V		3.3	5.9	1		
		fih = 16 MHz Note 3	operation	V <sub>DD</sub> = 3.0 V		3.3	5.9	1		
		HS (high-speed main)	fmx = 20 MHz Note 2,	Normal	Square wave input		3.7	6.8	m	
		mode Note 5	V <sub>DD</sub> = 5.0 V	operation	Resonator connection		3.9	7.0		
		fmx = 20 MHz Note 2,	Normal	Square wave input		3.7	6.8			
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.9	7.0	1
				V <sub>DD</sub> = 5.0 V	Normal	Square wave input		2.3	4.1	1
					operation	Resonator connection		2.3	4.2	1
					Normal	Square wave input		2.3	4.1	1
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		2.3	4.2	1
			Subsystem clock	fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.2	7.7	μ/
			operation	TA = -40°C	operation	Resonator connection		5.2	7.7	1
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.3	7.7	1
				T <sub>A</sub> = +25°C	operation	Resonator connection		5.3	7.7	1
				fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.5	10.6	1
			T <sub>A</sub> = +50°C	operation	Resonator connection		5.5	10.6	1	
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		5.9	13.2	1	
			TA = +70°C	operation	Resonator connection		6.0	13.2		
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		6.8	17.5		
			T <sub>A</sub> = +85°C	operation	Resonator connection		6.9	17.5	1	
			fsuB = 32.768 kHz Note 4	Normal	Square wave input		15.5	77.8	1	
			T <sub>A</sub> = +105°C	operation	Resonator connection		15.5	77.8	1	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main) mode.
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.
  - In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation).
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V@1 MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz to } 16 \text{ MHz}$ 

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fil: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

### (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit	
Supply	IDD2	HALT mode	HS (high-speed main)	fhoco = 64 MHz,	V <sub>DD</sub> = 5.0 V		0.93	5.16	mA	
current Note 1	Note 2		mode Note 6	fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.93	5.16		
				fhoco = 32 MHz,	V <sub>DD</sub> = 5.0 V		0.5	4.47		
				fih = 32 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.5	4.47		
				fhoco = 48 MHz,	V <sub>DD</sub> = 5.0 V		0.72	4.08		
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.72	4.08		
				fhoco = 24 MHz,	V <sub>DD</sub> = 5.0 V		0.42	3.51		
				fih = 24 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.42	3.51		
				fhoco = 16 MHz,	V <sub>DD</sub> = 5.0 V		0.39	2.38		
				fiH = 16 MHz Note 4	V <sub>DD</sub> = 3.0 V		0.39	2.38		
			HS (high-speed main)	fmx = 20 MHz Note 3,	Square wave input		0.31	2.83	mA	
			mode Note 6	V <sub>DD</sub> = 5.0 V	Resonator connection		0.41	2.92		
				f <sub>MX</sub> = 20 MHz <sup>Note 3</sup> , Square wave input	Square wave input		0.31	2.83		
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.41	2.92		
					f <sub>MX</sub> = 10 MHz Note 3,	Square wave input		0.21	1.46	
				V <sub>DD</sub> = 5.0 V	Resonator connection		0.26	1.57		
				fmx = 10 MHz Note 3,	Square wave input		0.21	1.46		
				V <sub>DD</sub> = 3.0 V	Resonator connection		0.26	1.57		
			Subsystem clock	fsuB = 32.768 kHz Note 5,	Square wave input		0.31	0.76	μΑ	
			operation	TA = -40°C	Resonator connection		0.50	0.95		
						fsuB = 32.768 kHz Note 5,	Square wave input		0.38	0.76
				T <sub>A</sub> = +25°C	Resonator connection		0.57	0.95		
				fsuB = 32.768 kHz Note 5,	Square wave input		0.47	3.59		
				T <sub>A</sub> = +50°C	Resonator connection		0.70	3.78		
				fsuB = 32.768 kHz Note 5,	Square wave input		0.80	6.20		
				T <sub>A</sub> = +70°C	Resonator connection		1.00	6.39		
				fsuB = 32.768 kHz Note 5,	Square wave input		1.65	10.56		
				T <sub>A</sub> = +85°C	Resonator connection		1.84	10.75		
				fsuB = 32.768 kHz Note 5,	Square wave input		8.00	65.7		
				T <sub>A</sub> = +105°C	Resonator connection		8.00	65.7		
	IDD3	STOP mode	T <sub>A</sub> = -40°C				0.19	0.63	μΑ	
		Note 7	TA = +25°C				0.30	0.63	•	
			TA = +50°C				0.41	3.47		
			TA = +70°C				0.80	6.08	1	
			TA = +85°C							
			T <sub>A</sub> = +105°C				6.50	67.14	1	

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVsso, and EVss1. The following points apply in the HS (high-speed main)
  - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
  - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules. However, in HALT mode, including the current flowing into the RTC. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. During HALT instruction execution by flash memory.
- **Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4. When high-speed system clock and subsystem clock are stopped.
- Note 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1).
- Note 6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 32 MHz

2.4 V ≤ V<sub>DD</sub> ≤ 5.5 V@1 MHz to 16 MHz

- Note 7. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

#### (4) Peripheral Functions (Common to all products)

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I <sub>FIL</sub> Note 1				0.20		μA
RTC operating current	IRTC Notes 1, 2, 3				0.02		μA
12-bit interval timer operating current	IT Notes 1, 2, 4				0.02		μA
Watchdog timer operating current	I <sub>WDT</sub> Notes 1, 2, 5	fi∟ = 15 kHz			0.22		μA
A/D converter operating current	IADC Notes 1, 6	When conversion at maximum speed	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
			Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μА
Temperature sensor operating current	ITMPS Note 1				75.0		μA
D/A converter operating current	IDAC Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating	I <sub>CMP</sub> Notes 1, 12, 13	V <sub>DD</sub> = 5.0 V,	Window mode		12.5		μA
current		Regulator output voltage = 2.1 V	Comparator high-speed mode		6.5		μΑ
			Comparator low-speed mode		1.7		μA
		V <sub>DD</sub> = 5.0 V, Regulator output voltage = 1.8 V	Window mode		8.0		μΑ
			Comparator high-speed mode		4.0		μΑ
			Comparator low-speed mode		1.3		μΑ
LVD operating current	I <sub>LVD</sub> Notes 1, 7				0.08		μΑ
Self-programming operating current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	I <sub>BGO</sub> Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	2.04	
		Simplified SPI (CSI)/UART operation			0.70	1.54	
		DTC operation			3.10		

- Note 1. Current flowing to VDD.
- **Note 2.** When high speed on-chip oscillator and high-speed system clock are stopped.
- Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

  The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.



- Note 8. Current flowing during programming of the data flash.
- Note 9. Current flowing during self-programming.
- Note 10. For shift time to the SNOOZE mode, see 23.3.3 SNOOZE mode in the RL78/G14 User's Manual.
- **Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- **Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 3. fclk: CPU/peripheral hardware clock frequency
- Remark 4. Temperature condition of the TYP. value is TA = 25°C

#### 3.4 **AC Characteristics**

### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(1/2)

Itama	Cumb -!		Canditiana		MINI	TYP.	MANY	Unit
Items	Symbol		Conditions	T	MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.03125		1	μs
(minimum instruction execution time)		clock (fMAIN) operation	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μS
		Subsystem clo	ck (fsuв) operation	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	28.5	30.5	31.3	μS
		In the self-	HS (high-speed main)	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	0.03125		1	μS
		programming m mode	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μS
External system clock	fEX	2.7 V ≤ V <sub>DD</sub> ≤	5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V <sub>DD</sub> ≤	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texн,	2.7 V ≤ V <sub>DD</sub> ≤	5.5 V		24			ns
input high-level width,	texL	2.4 V ≤ V <sub>DD</sub> ≤	2.7 V		30			ns
low-level width	texhs, texhs				13.7			μS
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	tтін, tтіL				1/fMCK + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	100			ns
				2.4 V ≤ EVDD0 < 2.7 V	300			ns
Timer RJ input high-	tтлін,	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	40			ns
level width, low-level width	t⊤JIL			2.4 V ≤ EVDD0 < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when EVDD0 < VDD

2.4 V ≤ EV<sub>DD0</sub> < 2.7 V: MIN. 125 ns

fмск: Timer array unit operation clock frequency Remark

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel

number (n = 0 to 3))

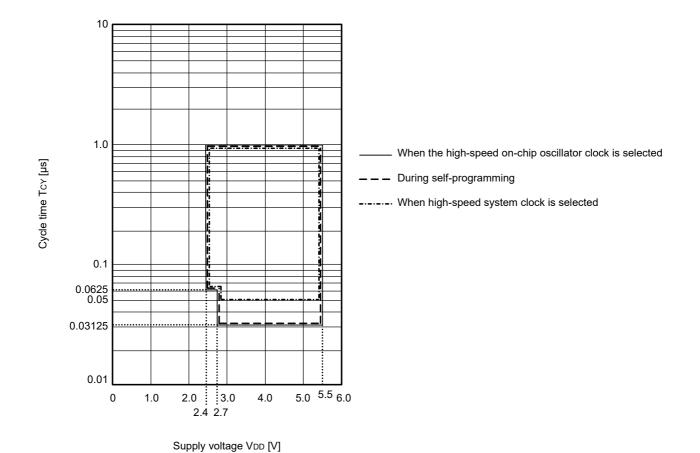
## (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

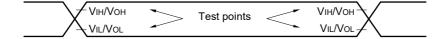
				· ·			-
Items	Symbol	Condition	ons	MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tтdiн, ttdil	TRDIOA0, TRDIOA1, TRDIOE TRDIOC0, TRDIOC1, TRDIOI	•	3/fclk			ns
Timer RD forced cutoff signal	ttdsil	P130/INTP0	2MHz < fclk ≤ 32 MHz	1			μS
input low-level width			fclk ≤ 2 MHz	1/fcLK + 1			
Timer RG input high-level width, low-level width	tтgін, tтgіL	TRGIOA, TRGIOB	TRGIOA, TRGIOB				ns
TO00 to TO03,	fто	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
TO10 to TO13,		2.7 V ≤ EV <sub>DD0</sub> < 4.0 V				8	MHz
TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-speed main) mode	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$			16	MHz
frequency			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}$			8	MHz
			2.4 V ≤ EVDD0 < 2.7 V			4	MHz
Interrupt input high-level	tinth,	INTP0	$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1			μS
width, low-level width	tintl	INTP1 to INTP11	2.4 V ≤ EVDD0 ≤ 5.5 V	1			μS
Key interrupt input low-level width	tkr	KR0 to KR7	2.4 V ≤ EVDD0 ≤ 5.5 V	250			ns
RESET low-level width	trsl			10			μS

Minimum Instruction Execution Time during Main System Clock Operation

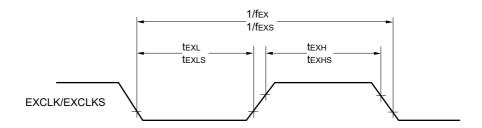
Tcy vs VDD (HS (high-speed main) mode)



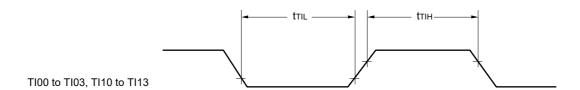
## **AC Timing Test Points**

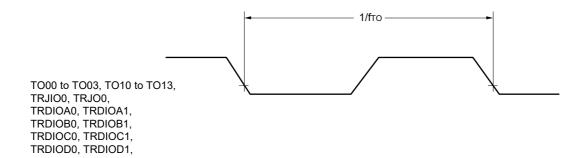


## External System Clock Timing

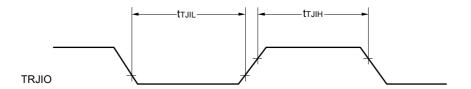


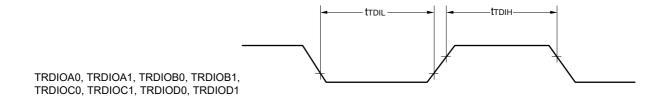
#### TI/TO Timing

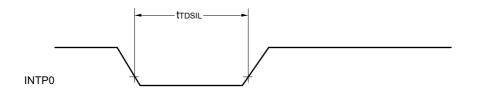


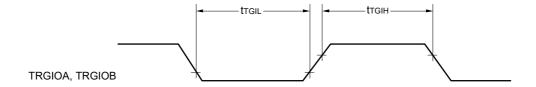


TRGIOA, TRGIOB

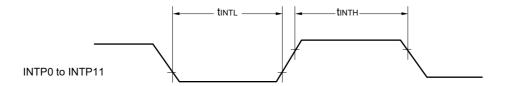




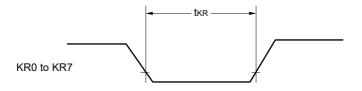




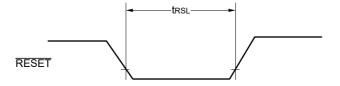
## Interrupt Request Input Timing



## Key Interrupt Input Timing

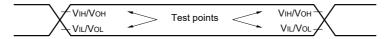


## RESET Input Timing



## 3.5 Peripheral Functions Characteristics

**AC Timing Test Points** 



## 3.5.1 Serial array unit

#### (1) During communication at same potential (UART mode)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

Parameter	Symbol	Conditions	Conditions HS (high-speed main) Mode		Unit
			MIN.	MAX.	
Transfer rate Note 1		2.4 V ≤ EVDD0 ≤ 5.5 V		fMCK/12 Note 2	bps
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

**Note 2.** The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \leq \text{EVDD0} < 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$ 

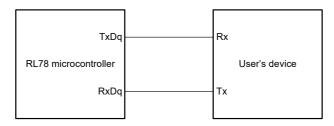
Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V  $\leq$  VDD  $\leq$  5.5 V)

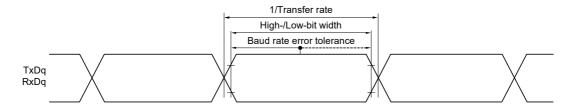
16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

#### **UART** mode connection diagram (during communication at same potential)



### UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

## (2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit	
				MIN.	MAX.	,	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ Evddo ≤ 5.5 V	250		ns	
			2.4 V ≤ EVDD0 ≤ 5.5 V	500		ns	
SCKp high-/low-level width	tkH1, tkL1	4.0 V ≤ EVDD0 ≤ 5.5 V		tксү1/2 - 24		ns	
		$2.7 \text{ V} \le \text{EVddo} \le 5.5 \text{ V}$		tксү1/2 - 36		ns	
		2.4 V ≤ EVDD0 ≤ 5.5 V		tксү1/2 - 76		ns	
SIp setup time (to SCKp↑) Note 1	tsık1	4.0 V ≤ EV <sub>DD0</sub> ≤	5.5 V	66		ns	
		2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		66		ns	
		2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		113		ns	
SIp hold time (from SCKp↑) Note 2	tksıı			38		ns	
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4	ı		50	ns	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fmck: Serial array unit operation clock frequency
  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

## (3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

•				•		٠,
Parameter	Symbol	Cond	ditions	HS (high-speed	l main) mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	4.0 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	20 MHz < fмск	16/ƒмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V	16 MHz < fмск	16/fмск		ns
			fмcк ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		12/fмск and 1000		ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V		tксү2/2 - 14		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 16		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		tkcy2/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	tsık2	2.7 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 40		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 2	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 3	tkso2	C = 30 pF Note 4	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		2/fмск + 66	ns
			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V		2/fмск + 113	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- **Note 5.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
  - n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)
- Remark 2. fmck: Serial array unit operation clock frequency
  - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
  - n: Channel number (mn = 00 to 03, 10 to 13))

## (3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

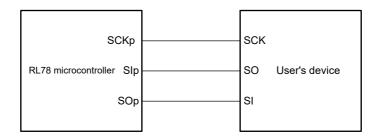
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Parameter	Symbol	Conditions		HS (high-speed	d main) mode	Unit
				MIN.	MAX.	
SSI00 setup time	setup time tssik DAPm		2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	240		ns
			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	400		ns
		DAPmn = 1	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 240		ns
			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 240		ns
			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	1/fмск + 400		ns
		DAPmn = 1	2.7 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	240		ns
			2.4 V ≤ EV <sub>DD0</sub> ≤ 5.5 V	400		ns

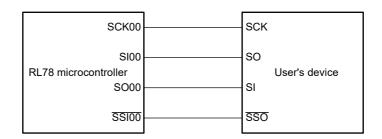
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

**Remark** p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM number (g = 3, 5)

#### Simplified SPI (CSI) mode connection diagram (during communication at same potential)



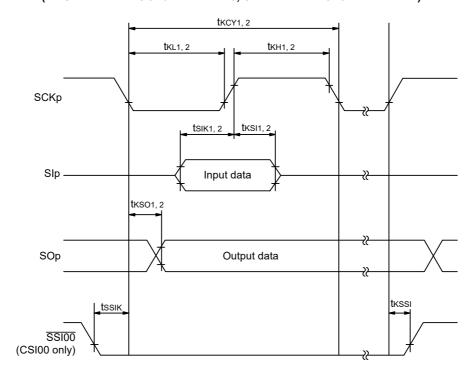
## Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))



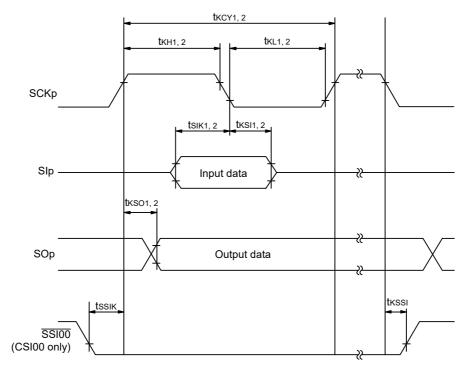
**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

## (4) During communication at same potential (simplified I<sup>2</sup>C mode)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed	main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		400 Note 1	kHz
		2.4 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4V \le EV_{DD0} \le 5.5 V$ , $C_b = 100 pF$ , $R_b = 3 k\Omega$	4600		ns
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		2.4 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ	4600		ns
Data setup time (reception)	tsu: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fmck + 220 Note 2		ns
		$2.4 \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $C_b = 100 \text{ pF}, \text{ R}_b = 3 \text{ k}\Omega$	1/fmck + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	770	ns
		2.4 V $\leq$ EV <sub>DD0</sub> $\leq$ 5.5 V, C <sub>b</sub> = 100 pF, R <sub>b</sub> = 3 kΩ	0	1420	ns

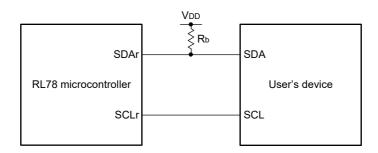
**Note 1.** The value must also be equal to or less than fMCK/4.

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

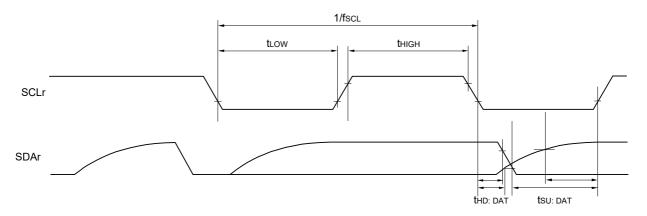
(Remarks are listed on the next page.)

**Note 2.** Set the fмcκ value to keep the hold time of SCLr = "L" and SCLr = "H".

### Simplified I<sup>2</sup>C mode connection diagram (during communication at same potential)



### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] : \mathsf{Communication line (SDAr) pull-up resistance}, \ \, \mathsf{Cb}[F] : \mathsf{Communication line (SDAr, SCLr) load capacitance}$ 

**Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14), h: POM number (h = 0, 1, 3 to 5, 7, 14)

Remark 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

#### (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol		Conditions	HS (high-s	peed main) mode	Unit
				MIN.	MAX.	•
Transfer rate		reception	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		fMCK/12 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps
			$2.7 \text{ V} \le \text{EVdd} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$		fMCK/12 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps
			$2.4 \text{ V} \le \text{EVddo} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$		f <sub>MCK</sub> /12 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.

 $2.4 \text{ V} \le \text{EV}_{DD0} < 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$ 

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 32 MHz (2.7 V  $\leq$  VDD  $\leq$  5.5 V)

16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remark 1. Vb [V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13)

**Remark 4.** UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

#### (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

#### $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$

(2/2)

Parameter	Symbol		Conditions		eed main) mode	Unit
				MIN.	MAX.	
Transfer rate		transmission	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$		Note 1	bps
		Theoretical value of the maximum transfer rate $C_b$ = 50 pF, $R_b$ = 1.4 k $\Omega$ , $V_b$ = 2.7 V		2.6 Note 2	Mbps	
	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$		Note 3	bps		
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega,$ $V_b = 2.3 \text{ V}$		1.2 Note 4	Mbps
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		Note 5	bps	
	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF},  R_b = 5.5 \text{ k}\Omega, \\ V_b = 1.6 \text{ V}$		0.43 Note 6	Mbps		

Note 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V  $\leq$  EVDD0  $\leq$  5.5 V and 2.7 V  $\leq$  Vb  $\leq$  4.0 V

Maximum transfer rate = 
$$\frac{1}{\left\{-C_b \times R_b \times \ln \left(1 - \frac{2.2}{V_b}\right)\right\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{C}_b \times \text{R}_b \times \text{In } (1 - \frac{2.2}{V_b})\}}{\text{value}} \times 100 \, [\%]$$

$$(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}$$

**Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V  $\leq$  EVDD0 < 4.0 V and 2.3 V  $\leq$  Vb  $\leq$  2.7 V

Maximum transfer rate = 
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met.

Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

Note 5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate

Expression for calculating the transfer rate when 2.4 V  $\leq$  EVDD0 < 3.3 V and 1.6 V  $\leq$  Vb  $\leq$  2.0 V

Maximum transfer rate = 
$$\frac{1}{ \{ -C_b \times R_b \times ln (1 - \frac{1.5}{V_b}) \} \times 3}$$
 [bps]

Baud rate error (theoretical value) = 
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- Note 6. This value as an example is calculated when the conditions described in the "Conditions" column are met.

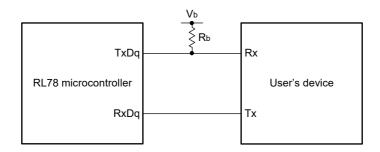
  Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

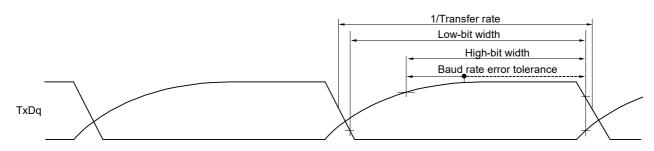


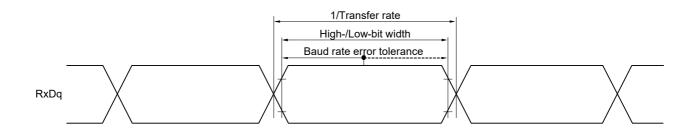
<sup>\*</sup> This value is the theoretical value of the relative difference between the transmission and reception sides.

### **UART** mode connection diagram (during communication at different potential)



### UART mode bit width (during communication at different potential) (reference)





- $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] \text{: } \mathsf{Communication line (TxDq) pull-up resistance,}$ 
  - Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).

m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$  (1/3)

Parameter	Symbol	Co	onditions	HS (high-speed	l main) mode	Unit
				MIN.	MAX.	
SCKp cycle time	tKCY1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
			$2.7 \ V \leq EV_{DDO} < 4.0 \ V,$ $2.3 \ V \leq V_b \leq 2.7 \ V,$ $C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega$	1000		ns
			$2.4 \ V \leq EV_{DDO} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	≤ 2.0 V, R <sub>b</sub> = 5.5 kΩ	ns	
SCKp high-level width	<b>t</b> кн1	$ 4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, \\ 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega $		tксү1/2 - 150		ns
		2.7 V $\leq$ EV <sub>DD0</sub> $<$ 4.0 V, 2.3 V $\leq$ V <sub>b</sub> $\leq$ 2.7 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 2.7 kΩ		tксү1/2 - 340		ns
		2.4 V $\leq$ EV <sub>DDO</sub> < 3.3 V, 1.6 V $\leq$ V <sub>b</sub> $\leq$ 2.0 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 5.5 kΩ		tксү1/2 - 916		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \le \text{EVddo} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}Ω$		tkcy1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}$	,	tксү1/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$		tксү1/2 - 100		ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

(2/3)

Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↑) <sup>Note</sup>	tsıĸ1	$ \begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	162		ns
		$\begin{split} 2.7 \ V &\leq EV_{DDO} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	354		ns
		$2.4 \ V \le EV_{DDO} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	958		ns
SIp hold time (from SCKp↑) Note	tksıı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	38		ns
		$\begin{split} 2.7 \ V &\leq EV_{DDO} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	38		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{Rb} = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↓ to SOp output <sup>Note</sup>	tkso1	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$		200	ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 30 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega$		390	ns
		$2.4 \ V \le EV_{DDO} < 3.3 \ V,$ $1.6 \ V \le V_b \le 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$		966	ns

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

 $(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD0} = \text{EVDD1} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = \text{EVss0} = \text{EVss1} = 0 \text{ V})$ 

(3/3)

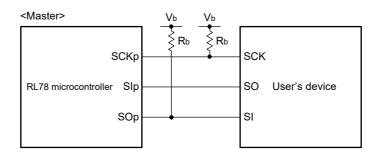
Parameter	Symbol	Conditions	HS (high-spee	HS (high-speed main) mode		
			MIN.	MAX.		
SIp setup time (to SCKp↓) <sup>Note</sup>	tsıĸ1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{Rb} = 1.4 \text{ k}\Omega $	88		ns	
		$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	88		ns	
		$\begin{array}{l} 2.4 \; V \leq EV_{DDO} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	220		ns	
SIp hold time (from SCKp↓) <sup>Note</sup>	tksıı	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, \; R_b = 1.4 \; k\Omega \end{array}$	38		ns	
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	38		ns	
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega$	38		ns	
Delay time from SCKp↑ to SOp output Note	tkso1	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 1.4 \text{ k}\Omega $		50	ns	
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		50	ns	
		$ 2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \text{ Rb} = 5.5 \text{ k}\Omega $		50	ns	

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

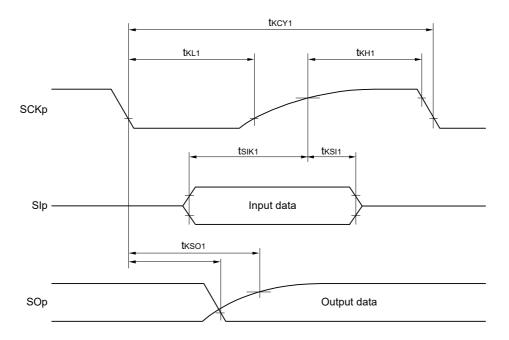
(Remarks are listed on the next page.)

### Simplified SPI (CSI) mode connection diagram (during communication at different potential

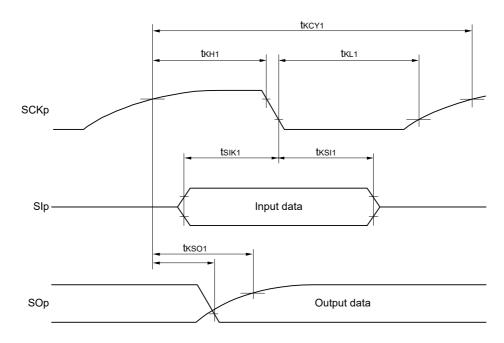


- **Remark 1.** Rb[ $\Omega$ ]: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency
  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
  n: Channel number (mn = 00))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

# (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

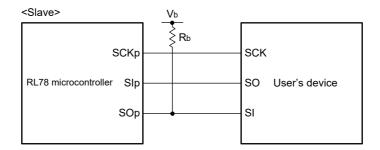
Parameter	Symbol	Conditions		HS (high-spee	Unit	
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	24 MHz < fmck	28/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcκ ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fmck	40/fмck		ns
		$2.3 \text{ V} \leq \text{Vb} \leq 2.7 \text{ V}$	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.4 \text{ V} \le \text{EVDD0} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{Vb} \le 2.0 \text{ V}$	24 MHz < fmck	96/fмск		ns
			20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмск ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcκ ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level	tkH2, tkL2	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		tkcy2/2 - 24		ns
width		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		tkcy2/2 - 36		ns
		$2.4~V \le EV_{DD0} < 3.3~V,~1.6~V \le V_b \le 2.0~V$		tkcy2/2 - 100		ns
SIp setup time	tsik2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.	7 V ≤ V <sub>b</sub> ≤ 4.0 V	1/fмск + 40		ns
(to SCKp↑) Note 2		2.7 V ≤ EVDD0 < 4.0 V, 2.	3 V ≤ V <sub>b</sub> ≤ 2.7 V	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkso2	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $			2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.$ $C_{\text{b}} = 30 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.$ Cb = 30 pF, Rv = 5.5 kΩ	$6 \text{ V} \le \text{Vb} \le 2.0 \text{ V},$		2/fмск + 1146	ns

(Notes, Caution, and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin, and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

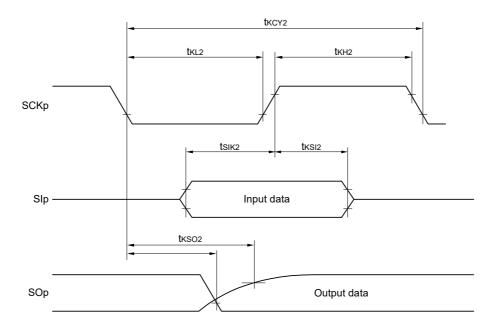
#### Simplified SPI (CSI) mode connection diagram (during communication at different potential)



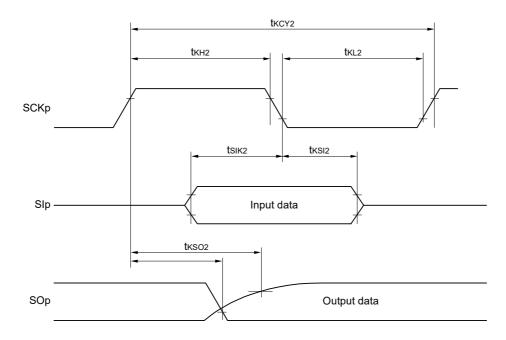
- **Remark 1.** R<sub>b</sub>[Ω]: Communication line (SOp) pull-up resistance, C<sub>b</sub>[F]: Communication line (SOp) load capacitance, V<sub>b</sub>[V]: Communication line voltage
- **Remark 2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency
  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
  m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
- Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



**Remark 1.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

Also, communication at different potential cannot be performed during clock synchronous serial communication with the slave select function.

## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol	Conditions	HS (high-spe	ed main) mode	Unit
i diametei	3,26.	Conditions	MIN.	MAX.	Offic
SCLr clock frequency	fscL	$ 4.0 \text{ V} \leq \text{EVDD0} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega $	IVIIIV.	400 Note 1	kHz
		$\begin{split} 2.7 \ V &\leq \text{EV}_{\text{DD0}} < 4.0 \ \text{V}, \\ 2.3 \ V &\leq \text{V}_{\text{b}} \leq 2.7 \ \text{V}, \\ C_{\text{b}} &= 50 \ \text{pF}, \ R_{\text{b}} = 2.7 \ \text{k}\Omega \end{split}$		400 Note 1	kHz
		$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned}$		100 Note 1	kHz
		$\begin{split} 2.7 & \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		100 Note 1	kHz
		$\begin{split} 2.4 & \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 & \ V \leq V_b \leq 2.0 \ V, \\ C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLow	$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1200		ns
		$\begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1200		ns
		$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned}$	4600		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	4600		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	thigh	$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	620		ns
		$\begin{split} 2.7 \ V &\leq \text{EV}_{\text{DDO}} < 4.0 \ \text{V}, \\ 2.3 \ V &\leq \text{V}_{\text{b}} \leq 2.7 \ \text{V}, \\ C_{\text{b}} &= 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{split}$	500		ns
		$\begin{aligned} 4.0 & \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 & \ V \leq V_b \leq 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned}$	2700		ns
		$\begin{split} 2.7 \ V &\leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V &\leq V_b \leq 2.7 \ V, \\ C_b &= 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	2400		ns
		$2.4 \ V \leq EV_{DD0} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 100 \ pF, \ R_b = 5.5 \ k\Omega$	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

#### (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I<sup>2</sup>C mode)

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-speed m	Unit	
			MIN.	MAX.	
Data setup time (reception)	tsu:DAT	$ 4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ \text{C}_{\text{b}} = 50 \text{ pF}, \text{R}_{\text{b}} = 2.7 \text{ k}\Omega $	1/fмск + 340 Note 2		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/fмск + 340 Note 2		ns
		$\begin{array}{l} 4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{array}$	1/fмск + 760 Note 2		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/fмск + 760 Note 2		ns
		$\begin{aligned} 2.4 & \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF, R}_{\text{b}} = 5.5 \text{ k}\Omega \end{aligned}$	1/fмск + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$ 4.0 \text{ V} \leq \text{EVddo} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 50 \text{ pF}, \text{Rb} = 2.7 \text{ k}\Omega $	0	770	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns
		$\begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b = 100 \ pF, \ R_b = 2.8 \ k\Omega \end{aligned}$	0	1420	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	1420	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	0	1215	ns

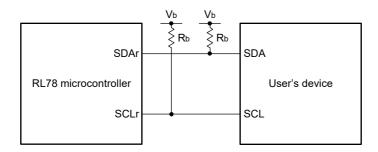
**Note 1.** The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

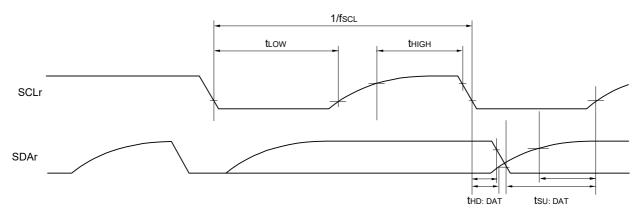
(Remarks are listed on the next page.)

**Note 2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

#### Simplified I<sup>2</sup>C mode connection diagram (during communication at different potential)



### Simplified I<sup>2</sup>C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[ $\Omega$ ]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01, 10, 11, 20, 30, 31), g: PIM, POM number (g = 0, 1, 3 to 5, 14)
- Remark 3. fmck: Serial array unit operation clock frequency

  (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),

  n: Channel number (n = 0, 2), mn = 00, 01, 02, 10, 12, 13)

#### 3.5.2 Serial interface IICA

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode			mode	Unit
			Standaı	rd mode	Fast	mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLk ≥ 3.5 MHz	_	_	0	400	kHz
		Standard mode: fcLκ ≥ 1 MHz	0	100	_	_	kHz
Setup time of restart condition	tsu: sta		4.7		0.6		μs
Hold time Note 1	thd: sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLow		4.7		1.3		μs
Hold time when SCLA0 = "H"	thigh		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	tBUF		4.7		1.3		μs

**Note 1.** The first clock pulse is generated after this period when the start/restart condition is detected.

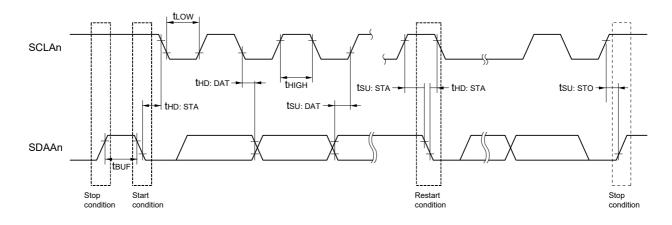
Note 2. The maximum value (MAX.) of this during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

**Remark** The maximum value of C<sub>b</sub> (communication line capacitance) and the value of R<sub>b</sub> (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode:  $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode:  $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$ 

#### **IICA** serial transfer timing



Remark n = 0, 1

## 3.6 Analog Characteristics

#### 3.6.1 A/D converter characteristics

#### Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V <sub>DD</sub> Reference voltage (-) = Vss	Reference voltage (+) = V <sub>BGR</sub> Reference voltage (-)= AV <sub>REFM</sub>
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI20	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$	2.375		39	μs
			$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	3.5625		39	μs
			$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV <sub>REFP</sub> = V <sub>DD</sub> Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
Analog input voltage	VAIN	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed main) mode)		V <sub>BGR</sub> Note 4			V
		Temperature sensor output voltage (2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V, HS (high-speed main) mode)		V <sub>TMPS25</sub> Note 4			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add  $\pm 0.5$  LSB to the MAX. value when AVREFP = VDD.

Note 4. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI20

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, 2.4 V  $\leq$  AVREFP  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution EVDD0 ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	2.125		39	μs
		Target ANI pin: ANI16 to ANI20	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EV <sub>DD0</sub> ≤ AV <sub>REFP</sub> = V <sub>DD</sub> Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution EV <sub>DD0</sub> ≤ AV <sub>REFP</sub> = V <sub>DD</sub> Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution EV <sub>DD0</sub> ≤ AV <sub>REFP</sub> = V <sub>DD</sub> Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution EV <sub>DD0</sub> ≤ AV <sub>REFP</sub> = V <sub>DD</sub> Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI20		0		AVREFP and EVDD0	V

**Note 1.** Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

**Note 3.** When  $EVDD0 \le AVREFP \le VDD$ , the MAX. values are as follows.

Overall error: Add  $\pm 1.0$  LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add  $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add  $\pm 0.5\%$ FSR to the MAX. value when AVREFP = VDD.

**Note 4.** When AVREFP  $\leq$  EVDD0  $\leq$  VDD, the MAX. values are as follows.

Overall error: Add  $\pm 4.0$  LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add  $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add  $\pm 2.0$  LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ V <sub>DD</sub> ≤ 5.5 V	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	3.5625		39	μs
			$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	2.4 V ≤ V <sub>DD</sub> ≤ 5.5 V			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		VDD	V
		ANI16 to ANI20		0		EV <sub>DD0</sub>	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)		V <sub>BGR</sub> Note 3		3	V
		Temperature sensor output voltage (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high-speed main) mode)		V <sub>TMPS25</sub> Note 3			V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +105°C, 2.4 V  $\leq$  VDD  $\leq$  5.5 V, 1.6 V  $\leq$  EVDD = EVDD1  $\leq$  VDD, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VBGR Note  $^3$ , Reference voltage (-) = AVREFM = 0 V Note  $^4$ , HS (high-speed main) mode)

Parameter	Symbol	Со	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8			
Conversion time	tconv	8-bit resolution	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	17		39	μS
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	Vain	1		0		V <sub>BGR</sub> Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

**Note 4.** When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add  $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add  $\pm 0.5$  LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add  $\pm 0.2$  LSB to the MAX. value when reference voltage (-) = AVREFM.

## 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic

(TA = -40 to +105°C, 2.4 V  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T <sub>A</sub> = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

## 3.6.3 D/A converter characteristics

## (TA = -40 to +105°C, 2.4 V $\leq$ EVsso = EVss1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
		Rload = 8 MΩ	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			3	μS
			2.4 V ≤ V <sub>DD</sub> < 2.7 V			6	μS

## 3.6.4 Comparator

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Col	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	Ivref			0		EVDD0 - 1.4	V
	Ivcmp			-0.3		EV <sub>DD0</sub> + 0.3	V
Output delay	td	V <sub>DD</sub> = 3.0 V Input slew rate > 50 mV/µs	Comparator high-speed mode, standard mode			1.2	μs
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3.0	5.0	μs
High-electric-potential reference voltage	VTW+	Comparator high-speed mode	e, window mode		0.76 Vdd		V
Low-electric-potential reference voltage	VTW-	Comparator high-speed mode	e, window mode		0.24 VDD		V
Operation stabilization wait time	tсмр			100			μs
Internal reference voltage Note	VBGR	$2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{ HS (h}$	nigh-speed main) mode	1.38	1.45	1.50	V

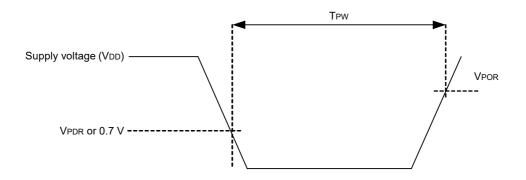
Note Not usable in sub-clock operation or STOP mode.

### 3.6.5 POR circuit characteristics

#### $(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power on/down reset threshold	VPOR	Voltage threshold on VDD rising	1.45	1.51	1.57	V
	VPDR	Voltage threshold on VDD falling Note 1	1.44	1.50	1.56	V
Minimum pulse width Note 2	Tpw		300			μS

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



## 3.6.6 LVD circuit characteristics

## (1) Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection	Supply voltage level	VLVD0	Rising edge	3.90	4.06	4.22	V
threshold			Falling edge	3.83	3.98	4.13	V
		VLVD1	Rising edge	3.60	3.75	3.90	V
			Falling edge	3.53	3.67	3.81	V
		VLVD2	Rising edge	3.01	3.13	3.25	V
			Falling edge	2.94	3.06	3.18	V
		VLVD3	Rising edge	2.90	3.02	3.14	V
			Falling edge	2.85	2.96	3.07	V
		_	Rising edge	2.81	2.92	3.03	V
			Falling edge	2.75	2.86	2.97	V
		VLVD5	Rising edge	2.70	2.81	2.92	V
			Falling edge	2.64	2.75	2.86	V
		VLVD6	Rising edge	2.61	2.71	2.81	V
			Falling edge	2.55	2.65	2.75	V
		VLVD7	Rising edge	2.51	2.61	2.71	V
			Falling edge	2.45	2.55	2.65	V
Minimum pulse wid	Ith	tLW		300			μS
Detection delay tim	ne					300	μs

### (2) Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR  $\leq$  VDD  $\leq$  5.5 V, Vss = 0 V)

Parameter	Symbol	Cond	ditions	MIN.	TYP.	MAX.	Unit
Voltage detection	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, fa	ılling reset voltage	2.64	2.75	2.86	V
threshold	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

# 3.6.7 Power supply voltage rising slope characteristics

### (TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

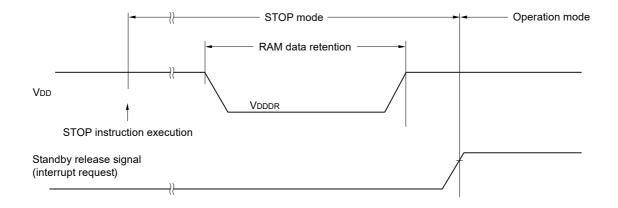
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

#### 3.7 RAM Data Retention Characteristics

#### $(TA = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0\text{V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		5.5	V

**Note** The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



## 3.8 Flash Memory Programming Characteristics

#### $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years TA = 85°C Note 4	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
- Note 4. This temperature is the average value at which data are retained.

## 3.9 Dedicated Flash Memory Programmer Communication (UART)

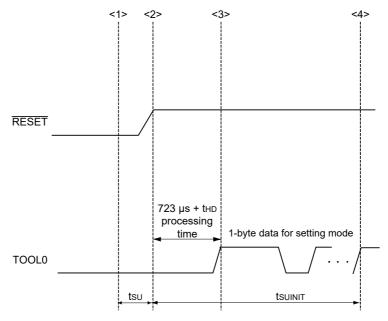
### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

## 3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μS
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	thD	POR and LVD reset must end before the external reset ends.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

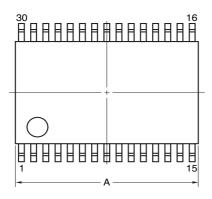
**Remark** tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

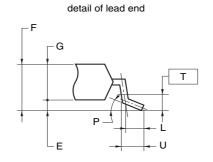
tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

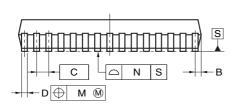
## 4. PACKAGE DRAWINGS

## 4.1 30-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

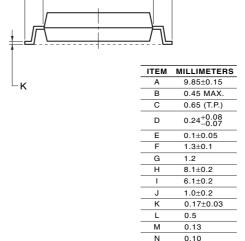






#### NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



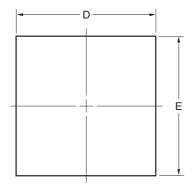
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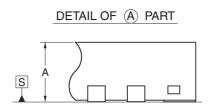
U

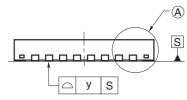
3°+5° 0.25 0.6±0.15

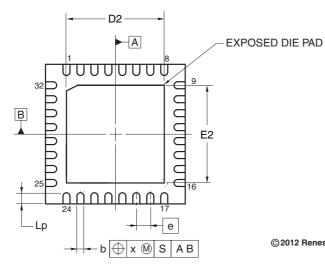
# 4.2 32-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-4	0.06







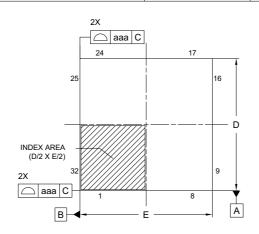


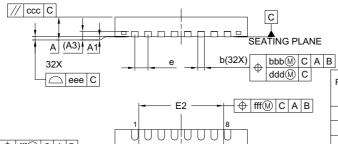
Reference Symbol	Dimension in Millimeters			
	Min	Nom	Max	
D	4.95	5.00	5.05	
Е	4.95	5.00	5.05	
Α	0.70	0.75	0.80	
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
У	_		0.05	

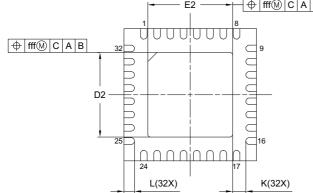
ITEM		D2		E2			
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	Α	3.45	3.50	3.55	3.45	3.50	3.55

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN032-5x5-0.50	PWQN0032KE-A	0.06



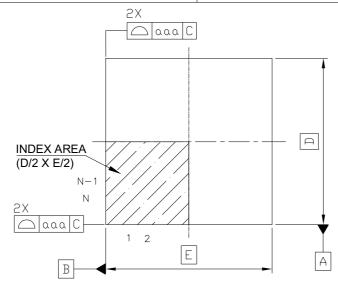


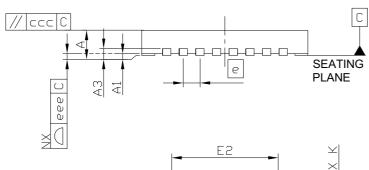


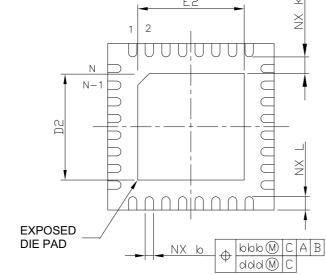
Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
Α	_	_	0.80	
A <sub>1</sub>	0.00	0.02	0.05	
A <sub>3</sub>	(	0.203 REF		
b	0.18	0.25	0.30	
D		5.00 BSC		
Е	5.00 BSC			
е		0.50 BSC		
L	0.35	0.40	0.45	
К	0.20	_	-	
D <sub>2</sub>	3.15	3.20	3.25	
E <sub>2</sub>	3.15	3.20	3.25	
aaa		0.15		
bbb	0.10			
ccc	0.10			
ddd	0.05			
eee	0.08			
fff	0.10			

RENESAS

JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN32-5×5-0.50	PWQN0032KG-A	0.06

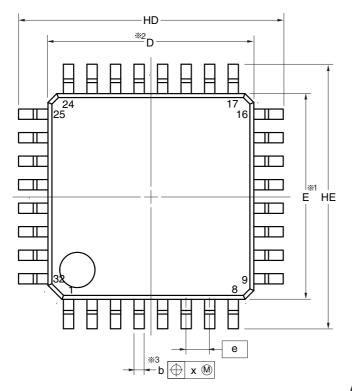


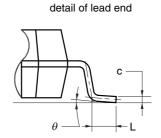


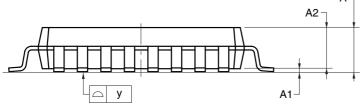


Reference	Dimens	ion in Mil	limeters
Symbol	Min.	Nom.	Max.
Α	_	_	0.80
A <sub>1</sub>	0.00	_	0.05
A <sub>3</sub>	0	.20 REF	=.
b	0.20	0.25	0.30
D	_	5.00	1
E	_	5.00	1
е	_	0.50	1
N		32	
L	0.30	0.40	0.50
K	0.20	_	_
D <sub>2</sub>	3.10	3.20	3.30
E <sub>2</sub>	3.10	3.20	3.30
aaa	_	1	0.15
bbb	_	1	0.10
ccc	_	_	0.10
ddd	_	_	0.05
eee	_	_	0.08

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP32-7x7-0.80	PLQP0032GB-A	P32GA-80-GBT-1	0.2







## (UNIT:mm)

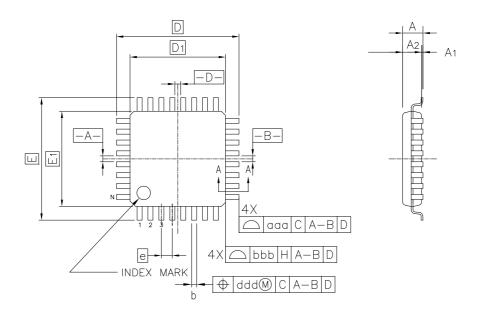
	( - /
ITEM	DIMENSIONS
D	7.00±0.10
E	7.00±0.10
HD	9.00±0.20
HE	9.00±0.20
Α	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	0.37±0.05
С	0.145±0.055
L	0.50±0.20
θ	0° to 8°
е	0.80
х	0.20
у	0.10

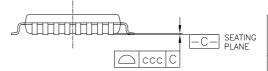
### NOTE

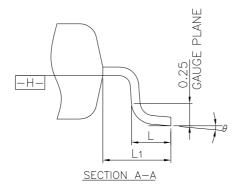
- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LQFP32-7x7-0.80	PLQP0032GE-A	0.18





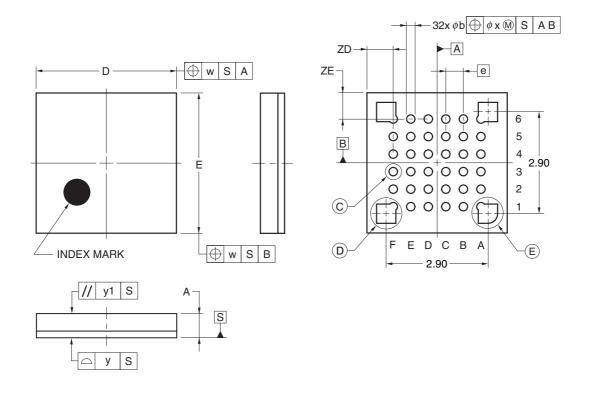


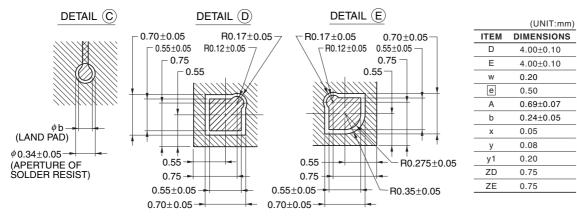
Reference	Dimensi	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.		
А	-	_	1.60		
A <sub>1</sub>	0.05	_	0.15		
A <sub>2</sub>	1.35	1.40	1.45		
D	_	9.00	_		
D <sub>1</sub>	_	7.00	_		
E	_	9.00	_		
E <sub>1</sub>	_	7.00	_		
N	_	32	_		
е	_	0.80	_		
b	0.30	0.37	0.45		
С	0.09	_	0.20		
θ	0,	3.5°	7*		
L	0.45	0.60	0.75		
L <sub>1</sub>	_	1.00	_		
aaa	_	_	0.20		
bbb	_	_	0.20		
ccc	_	_	0.10		
ddd	_	_	0.20		

RL78/G14 4. PACKAGE DRAWINGS

## 4.3 36-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023

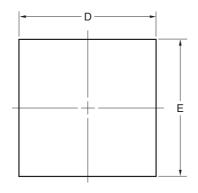


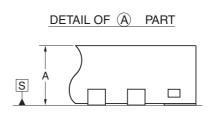


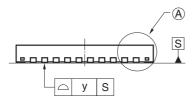
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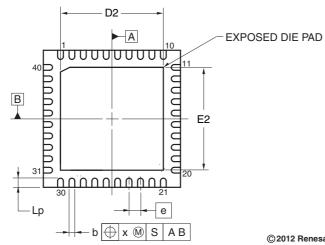
# 4.4 40-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-4	0.09







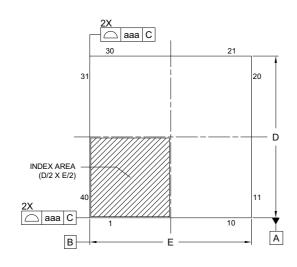


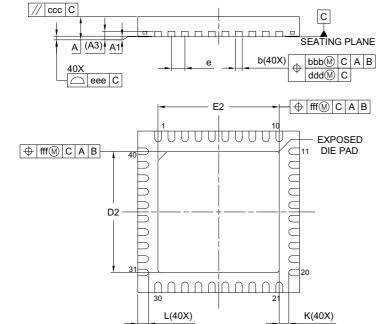
Reference	Dimension in Millimeters			
Symbol	Min	Nom	Max	
D	5.95	6.00	6.05	
Е	5.95	6.00	6.05	
Α	0.70	0.75	0.80	
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у			0.05	

ITEM		D2		E2			
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	А	4.45	4.50	4.55	4.45	4.50	4.55

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN040-6x6-0.50	PWQN0040KD-A	0.08

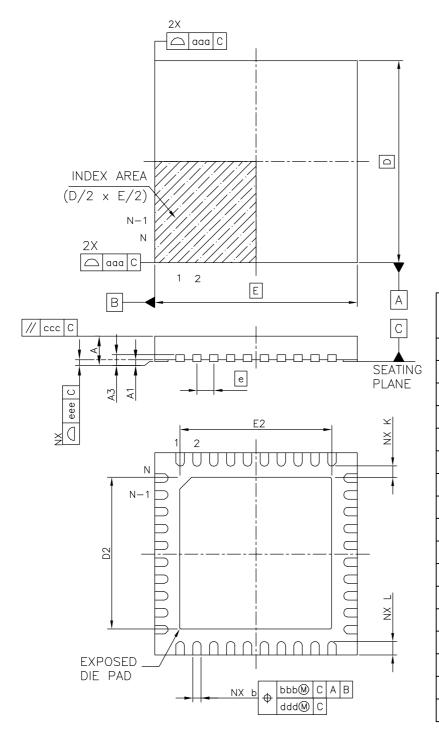




Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
А	_	_	0.80	
<b>A</b> <sub>1</sub>	0.00	0.02	0.05	
A₃		0.203 REF		
b	0.18	0.25	0.30	
D		6.00 BSC		
Е	6.00 BSC			
е		0.50 BSC		
L	0.30	0.40	0.50	
K	0.20	_	_	
D <sub>2</sub>	4.45	4.50	4.55	
E <sub>2</sub>	4.45	4.50	4.55	
aaa		0.15		
bbb	0.10			
ccc	0.10			
ddd	0.05			
eee	0.08			
fff	0.10			

<R>

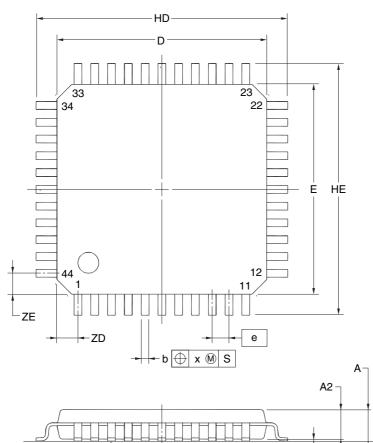
JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN40-6×6-0.50	PWQN0040KE-A	0.09



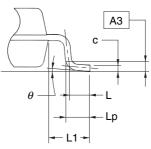
Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
Α	_	_	0.80	
$A_1$	0.00	_	0.05	
$A_3$	0	.20 REF	=.	
b	0.20	0.25	0.30	
D	_	6.00	_	
E	_	6.00	_	
е	_	0.50	_	
N		40		
L	0.30	0.40	0.50	
K	0.20	_	-	
$D_2$	4.40	4.50	4.60	
$E_2$	4.40	4.50	4.60	
aaa	ı	_	0.15	
bbb		_	0.10	
ссс		_	0.10	
ddd		_	0.05	
eee	_	_	0.08	

# 4.5 44-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



detail of lead end



(UNIT:mm)

	, ,
ITEM	DIMENSIONS
D	10.00±0.20
Е	10.00±0.20
HD	12.00±0.20
HE	12.00±0.20
Α	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.37^{+0.08}_{-0.07}$
С	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	3°+5° -3°
е	0.80
х	0.20
у	0.10
ZD	1.00
ZE	1.00

### NOTE

Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

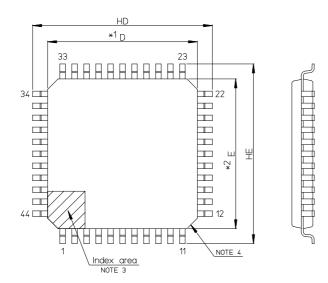
y S

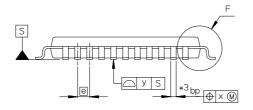
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Α1

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP44-10×10-0.80	PLQP0044GC-D		0.36g







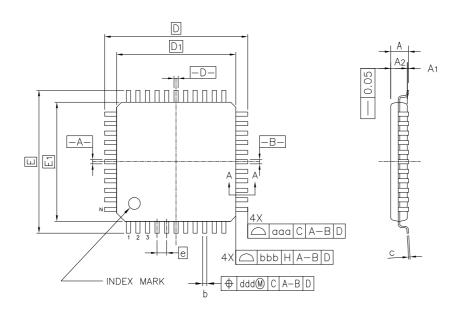
- NOTE) 1. 2. 3. OTE)

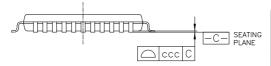
  1. DIMENSIONS '\*4" AND '\*2" DO NOT INCLUDE MOLD FLASH.
  2. DIMENSION '\*3" DOES NOT INCLUDE TRIM OFFSET.
  3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
  4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

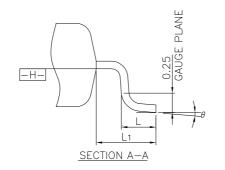
A A2		Lp L1
	Detail F	

Reference	Dimens	ion in Mil	limeters
Symbol	Min	Nom	Max
D	9.8	10.0	10.2
Е	9.8	10.0	10.2
A2		1.4	
HD	11.8	12.0	12.2
HE	11.8	12.0	12.2
Α			1.6
A1	0.05		0.15
bp	0.22	0.37	0.45
С	0.09		0.20
θ	0 °	3.5°	8 °
е		0.80	
×			0.20
У			0.10
Lp	0.45	0.6	0.75
L1		1.0	

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LQFP044-10x10-0.80	PLQP0044GE-A	0.34



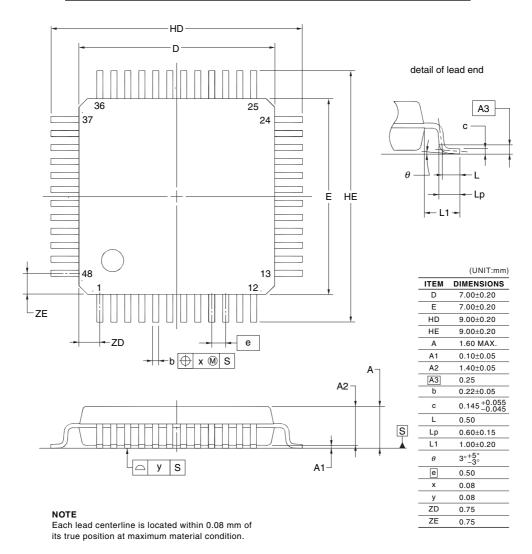




Dimension in Millimeters				
Min.	Nom.	Max.		
_	-	1.60		
0.05	_	0.15		
1.35	1.40	1.45		
_	12.00	_		
_	10.00	_		
_	12.00	_		
_	10.00	_		
_	44	_		
_	0.80	_		
0.30	0.37	0.45		
0.09	_	0.20		
0,	3.5°	7°		
0.45	0.60	0.75		
_	1.00	_		
_	_	0.20		
		0.20		
_	_	0.10		
_	_	0.20		
	Min 0.05 1.35 0.30 0.09 0°	Min. Nom.		

# 4.6 48-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP48-7x7-0.50	PLQP0048KF-A	P48GA-50-8EU-1	0.16



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Unit: mm

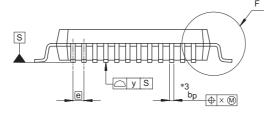
JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP48-7x7-0.50	PLQP0048KB-B	_	0.2

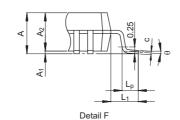
 $H_{\mathsf{D}}$ \*1 D 37 ш \*2 E ш 13 48 □□ NOTE 4 NOTE)

1. DIMENSIONS \*\*1" AND \*\*2" DO NOT INCLUDE MOLD FLASH.

2. DIMENSION \*\*3" DOES NOT INCLUDE TRIM OFFSET.

3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE





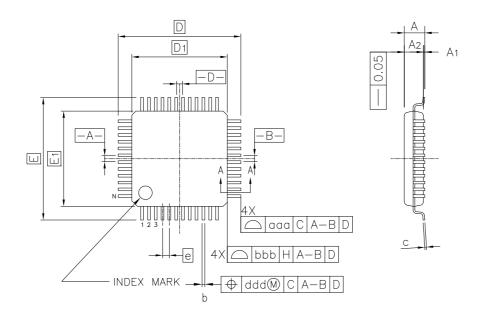
- LOCATED WITHIN THE HATCHED AREA.

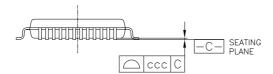
  4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

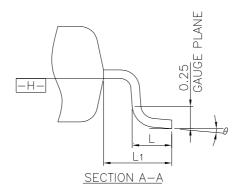
Reference	Dimensions in millimeters			
Symbol	Min	Nom	Max	
D	6.9	7.0	7.1	
E	6.9	7.0	7.1	
A <sub>2</sub>	_	1.4		
$H_D$	8.8	9.0	9.2	
HE	8.8	9.0	9.2	
Α	_	_	1.7	
A <sub>1</sub>	0.05		0.15	
bp	0.17	0.20	0.27	
С	0.09		0.20	
θ	0°	3.5°	8°	
е	_	0.5		
х	_		0.08	
У	_		0.08	
Lp	0.45	0.6	0.75	
L <sub>1</sub>		1.0		

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP48-7x7-0.50	PLQP0048KL-A	0.18

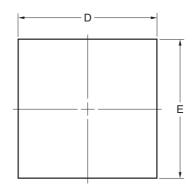


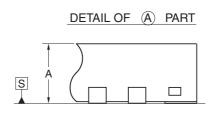


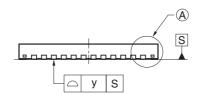


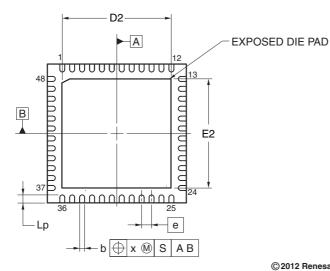
Reference	Dimension in Millimeters				
Symbol	Min.	Nom.	Max.		
А	_	_	1.60		
A <sub>1</sub>	0.05	_	0.15		
A <sub>2</sub>	1.35	1.40	1.45		
D	_	9.00	_		
D <sub>1</sub>	_	7.00	_		
E	_	9.00	_		
E <sub>1</sub>	7.00		_		
N	_	48	_		
е	- 0.50		_		
b	0.17	0.22	0.27		
С	0.09	_	0.20		
θ	0,	3.5°	7°		
L	0.45	0.60	0.75		
L <sub>1</sub>	_	1.00	-		
aaa	_	_	0.20		
bbb	_	-	0.20		
ccc	_	_	0.08		
ddd	_	_	0.08		

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-5	0.13







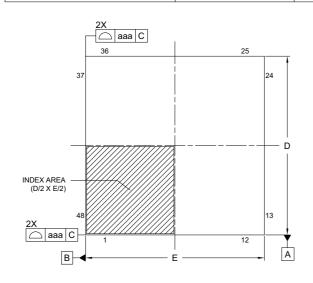


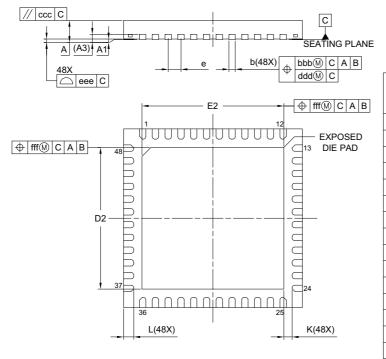
Reference	Dimension in Millimeters				
Symbol	Min	Nom	Max		
D	6.95	7.00	7.05		
E	6.95	7.00	7.05		
Α	0.70	0.75	0.80		
b	0.18	0.25	0.30		
е		0.50			
Lp	0.30	0.40	0.50		
х			0.05		
У			0.05		

ITEM		D2		E2			
112101		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	Α	5.45	5.50	5.55	5.45	5.50	5.55

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN048-7x7-0.50	PWQN0048KE-A	0.13

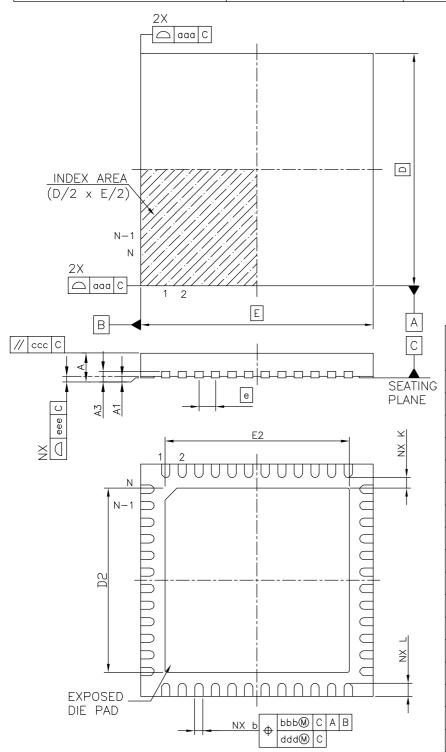




Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
Α	_	1	0.80	
A <sub>1</sub>	0.00	0.02	0.05	
A <sub>3</sub>	(	0.203 REF	-	
b	0.20	0.25	0.30	
D		7.00 BSC		
Е		7.00 BSC		
е		0.50 BSC		
L	0.30	0.40	0.50	
K	0.20	-	_	
$D_2$	5.50	5.55	5.60	
E <sub>2</sub>	5.50	5.55	5.60	
aaa	0.15			
bbb	0.10			
ccc	0.10			
ddd	0.05			
eee	0.08			
fff	0.10			

<R>

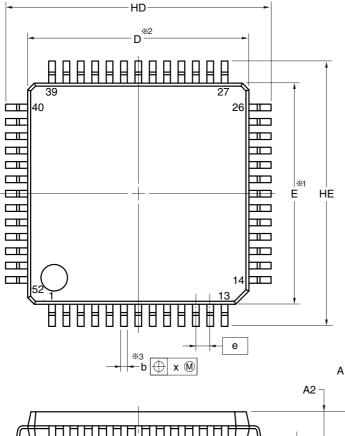
JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN48-7×7-0.50	PWQN0048KG-A	0.13

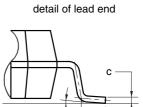


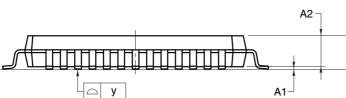
Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А	_	_	0.80
A <sub>1</sub>	0.00	_	0.05
$A_3$	0	.20 REF	=_
b	0.20	0.25	0.30
D	_	7.00	_
Ε	_	7.00	_
е	_	0.50	_
N		48	
L	0.30	0.40	0.50
K	0.20	_	_
$D_2$	5.50	5.55	5.60
E <sub>2</sub>	5.50	5.55	5.60
aaa	_	_	0.15
bbb			0.10
ccc	_	_	0.10
ddd	_	_	0.05
eee	_	_	0.08

#### 52-pin Package 4.7

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3







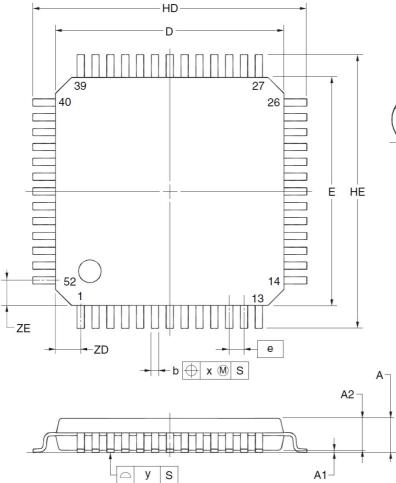
#### NOTE

- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

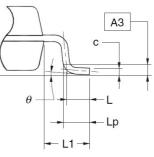
(UNIT:mm)
DIMENSIONS
10.00±0.10
10.00±0.10
12.00±0.20
12.00±0.20
1.70 MAX.
0.10±0.05
1.40
0.32±0.05
0.145±0.055
0.50±0.15
0° to 8°
0.65
0.13
0.10

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JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JD-B	P52GB-65-UET-2	0.36



detail of lead end



	(UNIT:mm)
ITEM	DIMENSIONS
D	10.00±0.20
E	10.00±0.20
HD	12.00±0.20
HE	12.00±0.20
Α	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
<b>A</b> 3	0.25
b	$0.32^{+0.08}_{-0.07}$
С	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
$\theta$	3°+5°
е	0.65
X	0.13
у	0.10
ZD	1.10
ZE	1.10

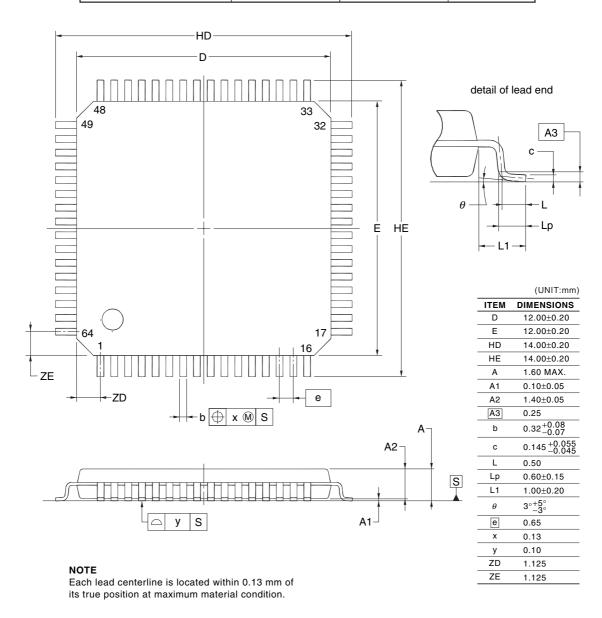
S

## NOTE

Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

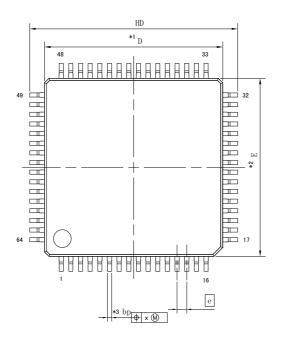
## 4.8 64-pin Package

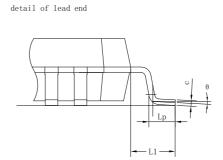
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51

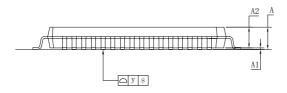


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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LQFP64-12x12-0.65	PLQP0064JB-A	0.50





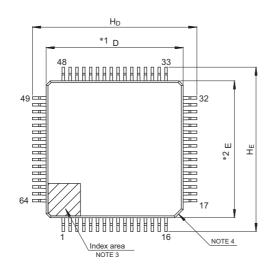


NOTE
1.DIMENSIONS "\*1" AND "\*2"DO NOT INCLUDE MOLD FLASH.
2.DIMENSION "\*3" DOES NOT INCLUDE TRIM OFFSET.

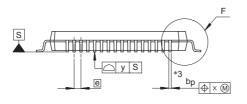
Reference Symbol	Dimension in Millimeters			
	Min.	Nom.	Max.	
Е	11.90	12.00	12.10	
D	11.90	12.00	12.10	
$A_2$	_	1.40	-	
$H_D$	13.80	14.00	14.20	
H <sub>E</sub>	13.80	14.00	14.20	
Α	_	-	1.70	
A <sub>1</sub>	0.05	_	0.15	
Lp	0.45	0.60	0.75	
L1	_	1.00	_	
b <sub>p</sub>	0.27	0.32	0.37	
С	0.09	1	0.20	
е	_	0.65	_	
θ	0.00	3.50	8.00	
х	_	_	0.08	
у	_	_	0.08	

JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP64-10x10-0.50	PLQP0064KB-C	_	0.3

Unit: mm







#### NOTE)

- NOTE)

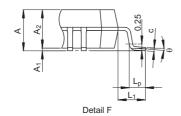
  1. DIMENSIONS "\*1" AND "\*2" DO NOT INCLUDE MOLD FLASH.

  2. DIMENSION "\*3" DOES NOT INCLUDE TRIM OFFSET.

  3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.

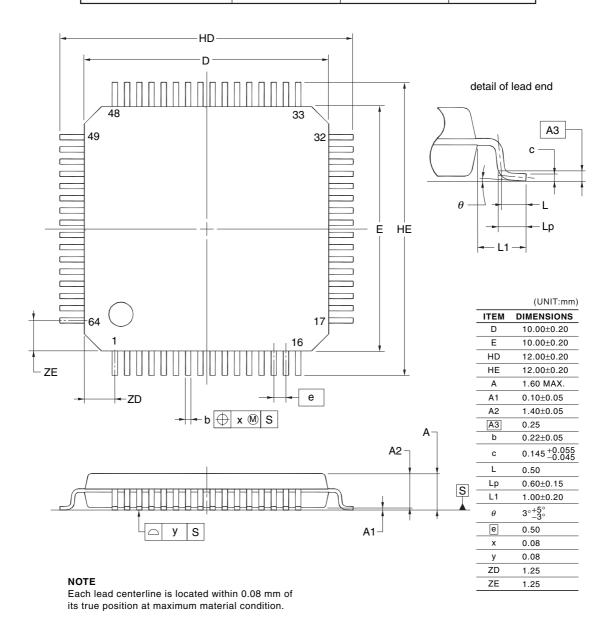
  4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference	Dimensions in millimeters		
Symbol	Min	Nom	Max
D	9.9	10.0	10.1
Е	9.9	10.0	10.1
A <sub>2</sub>		1.4	
$H_D$	11.8	12.0	12.2
HE	11.8	12.0	12.2
Α	_	_	1.7
A <sub>1</sub>	0.05		0.15
bp	0.15	0.20	0.27
С	0.09	_	0.20
θ	0°	3.5°	8°
е	_	0.5	
х	_		0.08
у			0.08
Lp	0.45	0.6	0.75
L <sub>1</sub>	_	1.0	_



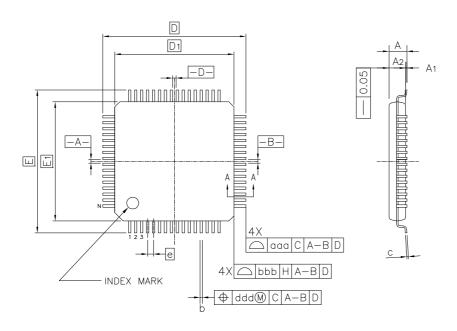
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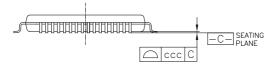
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35

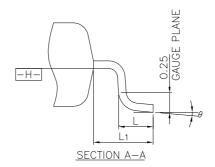


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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP064-10x10-0.50	PLQP0064KL-A	0.36



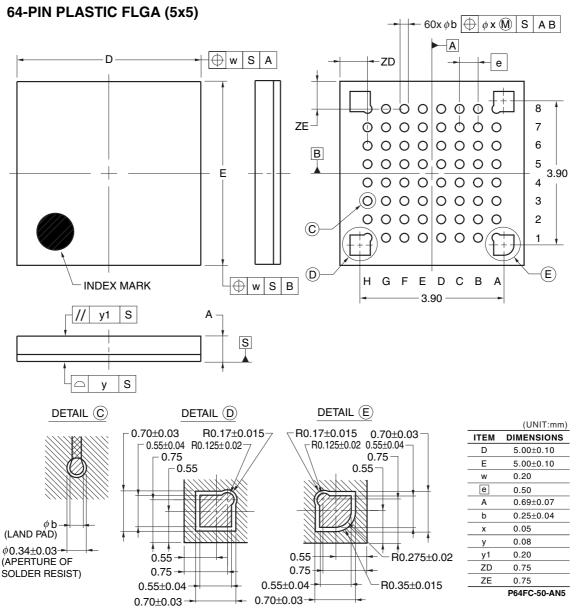




Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А	_	_	1.60
A <sub>1</sub>	0.05	_	0.15
$A_2$	1.35	1.40	1.45
D	1	12.00	_
$D_1$	_	10.00	_
Е	1	12.00	_
E <sub>1</sub>	_	10.00	_
Ν	1	64	_
е	_	0.50	_
b	0.17	0.22	0.27
С	0.09	-	0.20
θ	0,	3.5°	7°
L	0.45	0.60	0.75
L <sub>1</sub>	1	1.00	_
aaa		_	0.20
bbb		_	0.20
ccc	_	_	0.08
ddd	_	_	0.08

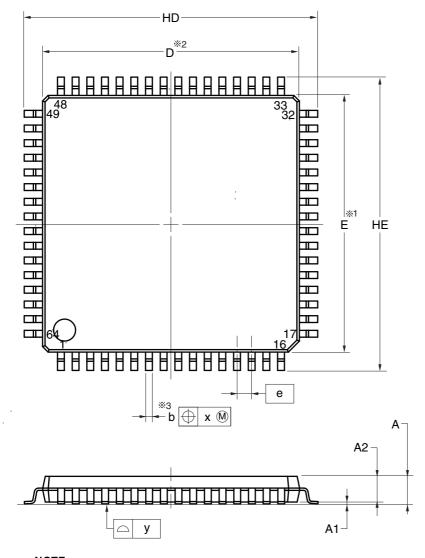
RL78/G14 4. PACKAGE DRAWINGS

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA64-5x5-0.50	PWLG0064KA-A	P64FC-50-AN5	0.037

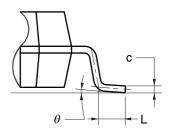


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JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-14x14-0.80	PLQP0064GA-A	P64GC-80-GBW-1	0.7



detail of lead end



	(UNIT:mm)
ITEM	DIMENSIONS
D	14.00±0.10
Е	14.00±0.10
HD	16.00±0.20
HE	16.00±0.20
Α	1.70 MAX.
A1	0.10±0.10
A2	1.40
b	$0.37^{+0.08}_{-0.05}$
С	$0.125^{+0.05}_{-0.02}$
L	$0.50 {\pm} 0.20$
θ	0° to 8°
е	0.80
х	0.20
У	0.10

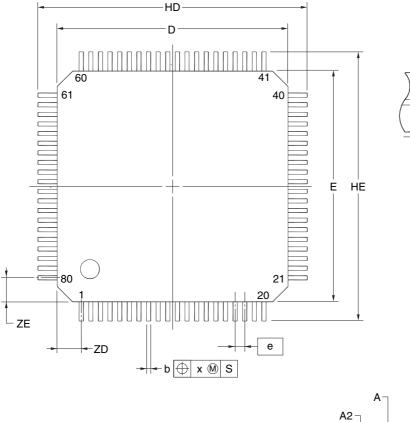
NOTE

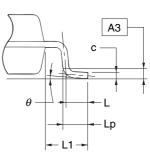
- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

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# 4.9 80-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

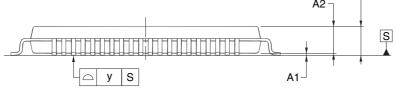




detail of lead end

	(UNIT:mm)
ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
Α	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	0.22±0.05
С	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
$\theta$	3°+5° -3°
е	0.50
х	0.08
у	0.08
ZD	1.25

1.25



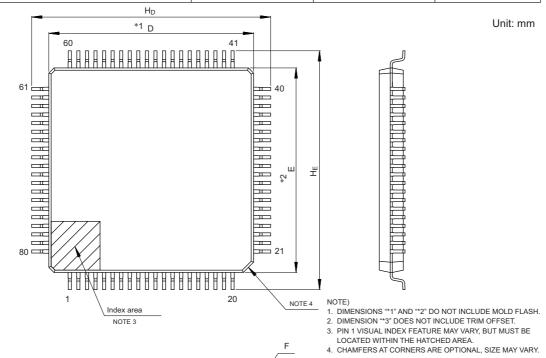
#### NOTE

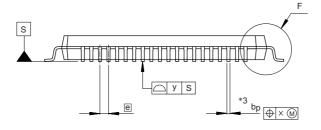
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

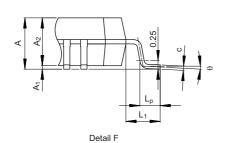
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JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP80-12x12-0.50	PLQP0080KB-B	_	0.5



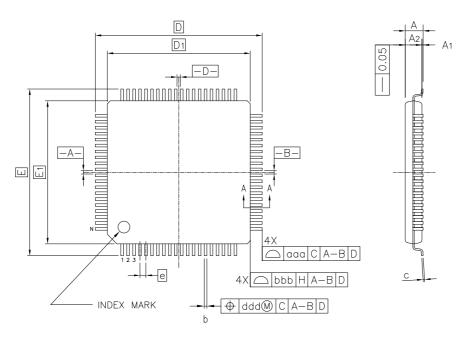




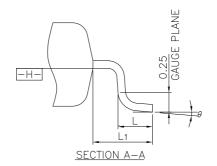
Reference	Dimensions in millimeter		
Symbol	Min	Nom	Max
D	11.9	12.0	12.1
Е	11.9	12.0	12.1
A <sub>2</sub>	_	1.4	
H <sub>D</sub>	13.8	14.0	14.2
HE	13.8	14.0	14.2
Α	_	_	1.7
A <sub>1</sub>	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09	_	0.20
θ	0°	3.5°	8°
е	_	0.5	
х	_	_	0.08
у	_		0.08
Lp	0.45	0.6	0.75
L <sub>1</sub>	_	1.0	_

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP80-12x12-0.50	PLQP0080KJ-A	0.49

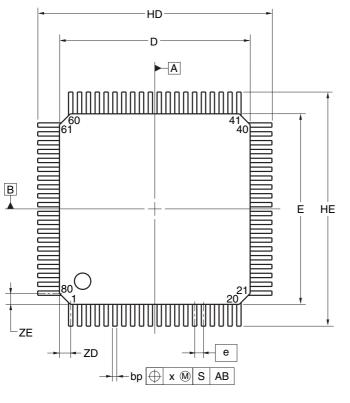


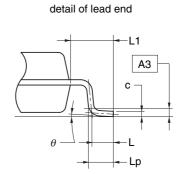


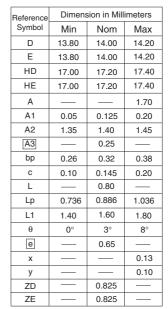


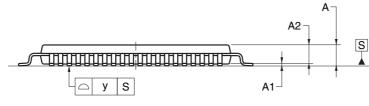
Reference	Dimensi	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.	
А	_	_	1.60	
A <sub>1</sub>	0.05	_	0.15	
A <sub>2</sub>	1.35	1.40	1.45	
D	_	14.00	_	
D <sub>1</sub>	_	12.00	_	
E	_	14.00	_	
E <sub>1</sub>	_	12.00	_	
N	_	80	_	
е	_	0.50	_	
b	0.17	0.22	0.27	
С	0.09	_	0.20	
θ	0°	3.5°	7°	
L	0.45	0.60	0.75	
L <sub>1</sub>	_	1.00	_	
aaa	=	-	0.20	
bbb	_	_	0.20	
ccc	_	_	0.08	
ddd	_	_	0.08	

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69





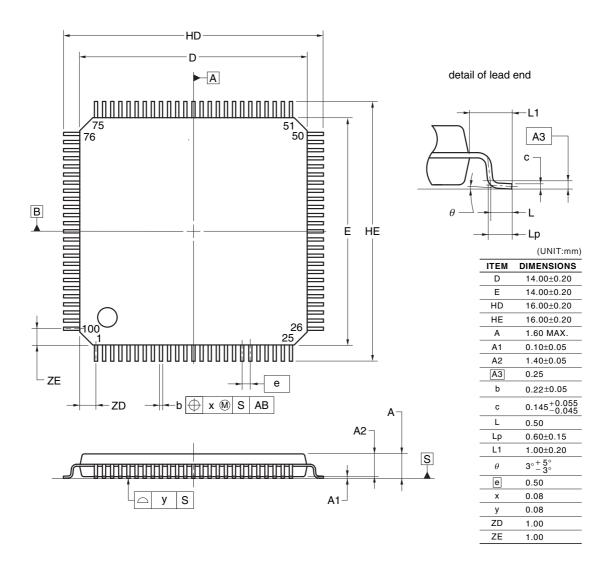




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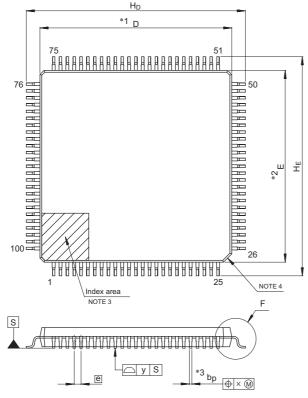
# 4.10 100-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP100-14x14-0.50	PLQP0100KB-B	_	0.6



Unit: mm

- NOTE)

  1. DIMENSIONS "\*1" AND "\*2" DO NOT INCLUDE MOLD FLASH.

  2. DIMENSION "\*3" DOES NOT INCLUDE TRIM OFFSET.

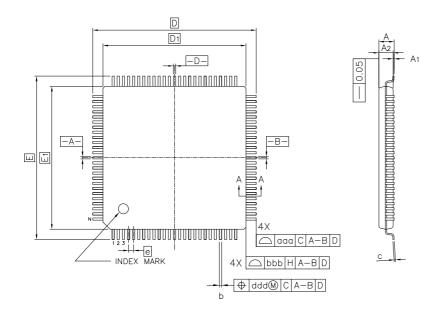
  3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
- 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

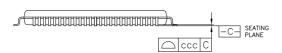
Reference	Dimensi	ons in mi	llimeters
Symbol	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A <sub>2</sub>	_	1.4	_
H <sub>D</sub>	15.8	16.0	16.2
HE	15.8	16.0	16.2
Α	_	_	1.7
A <sub>1</sub>	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09	_	0.20
θ	0°	3.5°	8°
е	_	0.5	_
х	_	_	0.08
у	_	_	0.08
Lp	0.45	0.6	0.75
L <sub>1</sub>		1.0	_

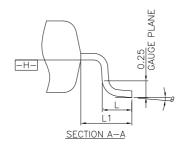
Detail F

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-LFQFP100-14x14-0.50	PLQP0100KP-A	0.67

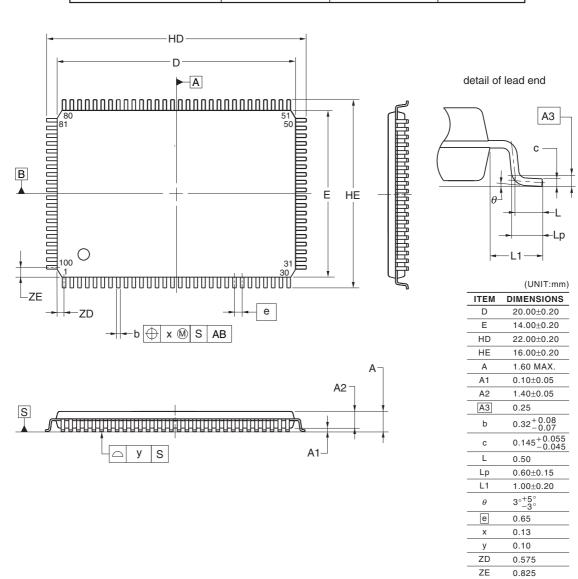






Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А	-	_	1.60
A <sub>1</sub>	0.05	_	0.15
A <sub>2</sub>	1.35	1.40	1.45
D	-	16.00	_
D <sub>1</sub>	_	14.00	-
Е	_	16.00	_
E <sub>1</sub>	_	14.00	_
N	_	100	-
е	-	0.50	_
b	0.17	0.22	0.27
С	0.09	_	0.20
θ	0,	3.5°	7°
L	0.45	0.60	0.75
L <sub>1</sub>	_	1.00	_
aaa	_	_	0.20
bbb	_	_	0.20
ccc	_	_	0.08
ddd	_	_	0.08

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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# RL78/G14 Datasheet

Rev. Date —		Description		
		Page	Summary	
0.01	Feb 10, 2011	_	First Edition issued	
0.02	May 01, 2011	1 to 2	1.1 Features revised	
		3	1.2 Ordering Information revised	
		4 to 13	1.3 Pin Configuration (Top View) revised	
		14	1.4 Pin Identification revised	
		15 to 17	1.5.1 30-pin products to 1.5.3 36-pin products revised	
		23 to 26	1.6 Outline of Functions revised	
0.03	Jul 28, 2011	1	1.1 Features revised	
1.00	Feb 21, 2012	1 to 40	1. OUTLINE revised	
		41 to 97	2. ELECTRICAL SPECIFICATIONS added	
2.00	Oct 25, 2013	1	Modification of 1.1 Features	
		3 to 8	Modification of 1.2 Ordering Information	
		9 to 22	Modification of package type in 1.3 Pin Configuration (Top View)	
		34 to 43	Modification of description of subsystem clock in 1.6 Outline of Functions	
		34 to 43	Modification of description of timer output in 1.6 Outline of Functions	
		34 to 43	Modification of error of data transfer controller in 1.6 Outline of Functions	
		34 to 43	Modification of error of event link controller in 1.6 Outline of Functions	
		45, 46	Modification of description of Tables in 2.1 Absolute Maximum Ratings	
		47	Modification of Tables, notes, cautions, and remarks in 2.2 Oscillator Characteristics	
		48	Modification of error of conditions of high level input voltage in 2.3.1 Pin characteristics	
		49	Modification of error of conditions of low level output voltage in 2.3.1 Pin characteristics	
		53 to 62	Modification of Notes and Remarks in 2.3.2 Supply current characteristics	
		65, 66	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		67 to 69	Addition of AC Timing Test Points	
		70 to 97	Addition of LS mode and LV mode characteristics in 2.5.1 Serial array unit	
		98 to 101	Addition of LS mode and LV mode characteristics in 2.5.2 Serial interface IICA	
		102 to 105	Addition of characteristics about conversion of internal reference voltage and temperature sensor in 2.6.1 A/D converter characteristics	
		107	Addition of characteristic in 2.6.4 Comparator	
		107	Deletion of detection delay in 2.6.5 POR circuit characteristics	
		109	Modification of 2.6.7 Power supply voltage rising slope characteristics	
		110	Modification of 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics	
		110	Addition of characteristic in 2.8 Flash Memory Programming Characteristics	
		111	Addition of description in 2.10 Timing for Switching Flash Memory Programming Modes	

# RL78/G14 Datasheet

D	D-4-		Description
Rev.	Date	Page	Summary
2.00	Oct 25, 2013	112 to 169	Addition of CHAPTER 3 ELECTRICAL SPECIFICATIONS
		171 to 187	Modification of 4.1 30-pin products to 4.10 100-pin products
3.00	Feb 07, 2014	All	Addition of products with maximum 512 KB flash ROM and 48 KB RAM
		1	Modification of 1.1 Features
		2	Modification of ROM, RAM capacities and addition of note 3
		3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14
		6 to 8	Addition of part number
		15, 16	Modification of 1.3.6 48-pin products
		17	Modification of 1.3.7 52-pin products
		18, 19	Modification of 1.3.8 64-pin products
		20	Modification of 1.3.9 80-pin products
		21, 22	Modification of 1.3.10 100-pin products
		35, 37, 39, 41, 43, 45, 47	Modification of operating ambient temperature in 1.6 Outline of Functions
		42, 43	Addition of table of 48-pin, 52-pin, 64-pin products (code flash memory 384 KB to 512 KB)
		46, 47	Addition of table of 80-pin, 100-pin products (code flash memory 384 KB to 512 KB)
		65 to 68	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		118	Modification of 2.7 Data Memory Retention Characteristics
		137 to 140	Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products
		180	Modification of 3.7 Data Memory Retention Characteristics
		189, 190	Addition and modification of 4.6 48-pin products
		191	Modification of 4.7 52-pin products
		193 to 195	Addition and modification of 4.8 64-pin products
		198, 199	Addition and modification of 4.9 80-pin products
		201, 202	Addition and modification of 4.10 100-pin products
3.20	Jan 05, 2015	2	Deletion of R5F104JK and R5F104JL from the list of ROM and RAM capacities and modification of note
		6	Deletion of ordering part numbers of R5F104JK and R5F104JL from 52-pin plastic LQFP package in 1.2 Ordering Information
		6 to 8	Deletion of note 2 in 1.2 Ordering Information
		17	Deletion of note 2 in 1.3.7 52-pin products
		36, 39, 42, 45, 48, 50, 52	Modification of description in 1.6 Outline of Functions
		46, 48	Deletion of description of 52-pin in 1.6 Outline of Functions
		47	Modification of note of 1.6 Outline of Functions
		62, 64, 66, 68, 70, 72	Modification of specifications in 2.3.2 Supply current characteristics

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# RL78/G14 Datasheet

Davi	Dete	Description	
Rev.	Date	Page	Summary
3.20	Jan 05, 2015	135, 137, 139, 141, 143, 145	Modification of specifications in 3.3.2 Supply current characteristics
		197	Modification of part number in 4.7 52-pin products
3.30	Aug 12, 2016	143, 145	Addition of maximum values in (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products of 3.3.2 Supply current characteristics
3.31	Feb 14, 2020	3	Addition of packaging specifications in Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14
		4 to 15	Addition of ordering part numbers and RENESAS codes in Table 1 - 1 List of Ordering Part Numbers
		195, 196, 198 to 201, 203, 205 to 207, 209 to 212, 214, 215, 217	Modification of the titles of the subchapters and deletion of product names in Chapter 4
		197	Addition of figure in 4.2 32-pin Package
		202	Addition of figure in 4.5 44-pin Package
		204	Modification of figure in 4.6 48-pin Package
		208	Modification of figure in 4.8 64-pin Package
		213	Modification of figure in 4.9 80-pin Package
		216	Modification of figure in 4.10 100-pin Package
3.32	Oct 31, 2020	3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14
		4 to 7	Addition of title and modification of description in Table 1 - 1 List of Ordering Part Numbers
		193	Addition of figure in 4.4 40-pin Package
		199	Addition of figure in 4.6 48-pin Package
3.40	Apr 15, 2022	All	The module name for 3-wire SPI was changed to simplified SPI
		All	The module name for CSI was changed to simplified SPI
		All	"Wait" was modified to "clock stretch"
		1	Modification of descriptions of Serial interfaces in 1.1 Features
		1	Addition of Note 1.1 Features
		4 to 7	Modification of description in Table 1-1 List of Ordering Part Numbers (1/4) to (4/4)
		17	Modification of Caution 2 in 1.3.8 64-pin products
		18	Modification of Caution 2 in 1.3.8 64-pin products
		19	Modification of Caution 2 in 1.3.9 80-pin products
		20	Modification of Caution 2 in 1.3.10 100-pin products
		21	Modification of Caution 2 in 1.3.10 100-pin products
		35	Modification of description of Data transfer controller (DTC) in 1.6 Outline of Functions [30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 16 KB to 64 KB)]
		42	Modification of description of Timer in 1.6 Outline of Functions [44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 96 KB to 256 KB)]

REVISION HISTORY RL78/G14 Datasheet
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Day	Data		Description
Rev.	Date	Page	Summary
3.40	Apr 15, 2022	55	Modification of Output current, low in Absolute Maximum Ratings in 2.1 Absolute Maximum Ratings
		61	Modification of Input leakage current, high and low in table ( $T_A$ = -40 to +85°C, 1.6 V $\leq$ EV <sub>DD0</sub> = EV <sub>DD1</sub> $\leq$ V <sub>DD</sub> $\leq$ 5.5 V, Vss = EV <sub>SS0</sub> = EV <sub>SS1</sub> = 0 V) (5/5) in 2.3.1 Pin characteristics
		63	Modification of Note 1 in (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 $\leq$ VDD $\leq$ 5.5 V, Vss = EVSS0 = 0 V) (1/2)
		65	Modification of Note 1 in (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products ( $T_A = -40$ to $+85^{\circ}$ C, $1.6$ V $\leq$ EV <sub>DD0</sub> $\leq$ V <sub>DD</sub> $\leq$ 5.5 V, Vss = EV <sub>SS0</sub> = 0 V) (2/2)
		124	Modification of Figure in 2.10 Timing of Entry to Flash Memory Programming Modes
		128	Modification of Output current, low in Absolute Maximum Ratings of 3.1 Absolute Maximum Ratings
		134	Modification of Input leakage current, high and low in table ( $T_A = -40 \text{ to } +105^{\circ}\text{C}$ , $2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$ , $V_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V}$ ) (5/5) of 3.3.1 Pin characteristics
		136	Modification of Note 1 in (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V}) (1/2)$
		138	Modification of Note 1 in (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V})$ (2/2)
		187	Modification of Figure in 3.10 Timing of Entry to Flash Memory Programming Modes
		192	Addition of figure in 4.2 32-pin Package
		198	Addition of figure in 4.5 44-pin Package
		201	Addition of figure in 4.6 48-pin Package
		205	Addition of figure in 4.7 52-pin Package
		207, 210	Addition of figure in 4.8 64-pin Package
		215	Addition of figure in 4.9 80-pin Package
		219	Addition of figure in 4.10 100-pin Package
3.50	May 31, 2023	4	Table 1 - 1 List of Ordering Part Numbers (1/4) was modified.
		63	2.3.2 Supply current characteristics, (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products (1/2): Notes 1 and 4 were modified.
		65	2.3.2 Supply current characteristics, (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products (2/2): Notes 1 and 5 was modified, and Note 6 was deleted.
		67	2.3.2 Supply current characteristics, (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2): Notes 1 and 4 were modified.
		69	2.3.2 Supply current characteristics, (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2): Notes 1 and 5 were modified, and Note 6 was deleted.
		71	2.3.2 Supply current characteristics, (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products (1/2): Notes 1 and 4 were modified.
		73	2.3.2 Supply current characteristics, (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products (2/2): Notes 1 and 5 were modified, and Note 6 were deleted.
		136	3.3.2 Supply current characteristics, (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products (1/2): Notes 1 and 4 were modified.
		138	3.3.2 Supply current characteristics, (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products (2/2): Notes 1 and 5 were modified, and Note 6 were deleted.

REVISION HISTORY	RL78/G14 Datasheet
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Rev. Date -		Description		
		Page	Summary	
3.50	May 31, 2023	140	3.3.2 Supply current characteristics, (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2): Notes 1 and 4 were modified.	
		142	3.3.2 Supply current characteristics, (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2): Notes 1 and 5 were modified, and Note 6 were deleted.	
		144	3.3.2 Supply current characteristics, (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products (1/2): Notes 1 and 4 were modified.	
		146	3.3.2 Supply current characteristics, (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products (2/2): Notes 1 and 5 were modified, and Note 6 were deleted.	
		191	4.2 32-pin Package: Figure was added.	
		208	4.8 64-pin Package: Figure was modified.	
3.60	Mar 29, 2024	3	Modification of figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14	
		4	Modification of table in Table 1 - 1 List of Ordering Part Numbers (1/4)	
		5	Modification of table in Table 1 - 1 List of Ordering Part Numbers (2/4)	
		6	Modification of table in Table 1 - 1 List of Ordering Part Numbers (3/4)	
		7	Modification of table in Table 1 - 1 List of Ordering Part Numbers (4/4)	
		197	Addition of figure in 4.4 40-pin Package	
		206	Addition of figure in 4.6 48-pin Package	

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# General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

#### 1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

#### 2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

#### 3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

#### 4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

#### 5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

#### 6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between  $V_{IL}$  (Max.) and  $V_{IH}$  (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between  $V_{IL}$  (Max.) and  $V_{IH}$  (Min.).

## 7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

#### 8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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(Rev.5.0-1 October 2020)

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